



**SINGLEEVENTEFFECTS
TESTREPORT**

PartType:	A3PE3000L
PartDescription:	ProASIC3LFlashBasedFPGA
PartManufacturer:	ACTEL
TestFacility	RADEF, Jyväskylä, Finland
TestDate	June2010&November2010
TestFacility	PIF, PSI, Villigen, Switzerland
TestDate	March2011
Issue	03
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DOCUMENTATIONCHANGENOTICE

Issue	Date	Page	Changeltem
01	01/10/2010	All	Draftissue
02	11/05/2011	All	AddedRADEFNovember2010andPSIMarch2011 campaigndata
03	23/08/2011	63	ModifiedtheSRAMheavyioncross-sectionplotand Weibullparametersvalues
		68	Addedsamplesstatusaftertheheavyionandthe samplesstatusafteralltestsinthe CONFIGURATION FLASH,CHARGE PUMP&INSYSTEMPROGRAMMING paragraph.
		89	ModifiedtheSRAMconditionsandSEUtables

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RESULTSUMMARY

The A3PE3000L flash FPGA from the ProASIC3L family from ACTEL manufacturer was SEE characterized at the following facilities under ESA ESTEC contract number 22327/09/NL/SFE:

- ✓ RADEF, University of Jyväskylä, Jyväskylä, Finland in June and November 2010.
- ✓ PIF, PSI, Villigen, Switzerland in March 2011.

SEE mitigation methods applied on the same die were also characterized and their SEE sensitivities evaluated. 2 test vehicles (TV) were designed and tested. The first TV implemented 14 shift registers, one clock conditioning circuit with phase-locked loop and 100 % of the SRAM and UFROM memories. The second TV implemented SEU and SET mitigation on 6 shift registers. All shift registers of both TVs were made of 1024 registers made of D core flip-flop with clear and enable active high.

Device description:

Part type:	A3PE3000L
Part family:	ProASIC3L
Manufacturer:	ACTEL
Package:	PQ208
Date code:	0922
Used samples:	Serialized from SN1 to SN24.
Package marking:	QHR8G
Die dimensions:	10.8x10.8mm

SEL:

No SEL was observed up to a LET of 55 MeV.cm²/mg, a cumulated fluence of 1E7 p/cm², a temperature up to 125°Celsius and a bias voltage of 1.65 Volts for the core voltage and 3.6 Volts for the input/output voltage.

SEFI:

One SEFI was detected and recorded during the campaign at RADEF on November 2010 on the RUN112 with an effective LET of 55 MeV.cm²/mg. The device was configured with the TV2 and all shift registers were tested with a working frequency of 2 MHz. From the iteration N°257 (a fluence of 3.69E5 p/cm²) up to the end of the run (a fluence of 5E5 p/cm²) all the data from the device were read at the low state ("0"). The device did not recover from the SEFI state by itself. The recovery took place after a power cycle of the device allowing the next run with the exact same condition to be performed without any more SEFI detected.

SEU:

The flash (configuration and user) was not seen sensitive to SEE up to a LET of 55 MeV.cm²/mg. It remained intact. However the programming part of the flash was stated sensitive to SEU, SHE and to the cumulated dose deposited by the cumulated fluence.

Concerning the shift registers:

- ✓ The reference and standard shift register (TV1 - SR1) SEU cross-section is characterized with an asymptotic cross-section below 3E-7 cm² per bit and a LET threshold below 1.8 MeV.cm²/mg. An extremely light influence of the working frequency can be seen on the SEU cross-section. Most errors are SBUs where almost 2/3 is due to clear transition. Some MBUs largely made of arbitrary numbers of consecutive reset bits (clear bit) were counted as well. A reference Weibull curve plotted on the Figure 1 was estimated from the measured points and added to all SEU cross-sectional area per bit for comparison purpose.
- ✓ The channel implementing combinational cells on the enable signal path (TV1 - SR2) results in an SEU cross-sectional area per bit similar to the reference. The frequency does not appear to influence the SEU cross-section or so lightly that it is not visible on the cross-section curve. Most errors are SBUs with more than half due to clear transition. MBUs are made of errors with the same signatures than the reference channel. However another signature shows un-shifted quartets caused by a SET on the enable signal caught at the active edge of the clock: data are held from shifting. Very few SETs on the enable signal were caught that way.
- ✓ The channel implementing combinational cells on the reset signal path (TV1 - SR3) results in a SEU

- cross-sectional area per bit characterized with an LET threshold around $1.8 \text{ MeV} \cdot \text{cm}^2/\text{mg}$. This SEU cross-section is almost 80% of SEUs are SBUs and 70% of those are due to clear transition. There is a high count of MBUs compared to the reference channel and almost all of those are due to arbitrary numbers of reset bits.
- ✓ The channel implementing combinational cells in-between each register (TV1 - SR4) results in a SEU cross-sectional area per bit similar to the reference. A very light influence of the working frequency can be seen on the SEU cross-section. Most SEUs are SBUs and 2/3 of those are due to clear transition. Comparing SEU cross-section and errors signatures, this channel seems very similar to the reference one.
 - ✓ The channels implementing the DDR I/O registers (TV1 - SR5 to 8) and the channels implementing LVDS buffers (TV1 - SR9 and 10) show a SEU cross-sectional area per bit very similar to the reference. SEE signatures are also like the reference ones.
 - ✓ The channels clocked by the PLL output clock (TV1 - SR11 to 14) have a SEU cross-sectional area per bit identical to the reference. Most SEUs are SBUs with more than half due to clear transition. MBUs are largely attended to reset bits and flipped bits: it was not seen a total flip or stuck bit of the PLL output clock.
 - ✓ The channel implementing sequential cell triplication (TV2 - SR1) results in a SEU cross-sectional area per bit characterized with an asymptotic cross-section below $2 \times 10^{-9} \text{ cm}^2$. There is a large difference (around 2 decades) on its SEU cross-section and the reference one. It is based on a poor statistic attended to the small number of errors. More than 70% of SEUs are SBUs and all of those are due to clear transition. The high percentage of MBUs (almost 30%) compared to the reference channel is made of arbitrary numbers of reset bits. The sequential cell triplication SEU mitigation decreases the total amount of SEU and changes the SBU vs. MBU ratio. All events appearing on the channel only as asynchronous global (or local) reset signal should be considered between all registers induced all recorded SEUs without any available correction from the voter.
 - ✓ The channel implementing sequential cell triplication and I/O bank triplication (TV2 - SR2) has a SEU cross-sectional area per bit characterized with an asymptotic cross-section below $2 \times 10^{-7} \text{ cm}^2$ and a LET threshold below $10 \text{ MeV} \cdot \text{cm}^2/\text{mg}$, lower than the reference but still higher than the channel implementing only sequential cell triplication. This result seems unrealistic compared to the other channels implementing only the sequential cell triplication (TV2 - SR1). Because both channels use the same sequential cell triplication as SEU mitigation, a smaller (or in the worst case an equivalent) cross-section was expected on the SR2 channel. No explanation has been found yet to explain the result on this channel.
 - ✓ The channel implementing the SET filtering method with a delay of 2 ns (TV2 - SR3) has a SEU cross-sectional area per bit similar to the reference. Its SEEs signatures are also very like the reference channel.
 - ✓ The channel implementing sequential cell triplication, I/O block triplication and SET filtering with a delay of 3 ns (TV2 - SR4) did not show any event up to a LET of $55 \text{ MeV} \cdot \text{cm}^2/\text{mg}$ and a cumulated fluence of $2 \times 10^6 \text{ p/cm}^2$.
 - ✓ The channel implementing sequential cell triplication, I/O block triplication and logic duplication (TV2 - SR5) did not show any event up to a LET of $55 \text{ MeV} \cdot \text{cm}^2/\text{mg}$ and a cumulated fluence of $2 \times 10^6 \text{ p/cm}^2$.
 - ✓ The channel made of full TMR mitigation (TV2 - SR6 cleared). Based on an extremely poor statistic this channel look close to the result of the channel implementing only sequential cell triplication (TV2 - SR1).
 - ✓ All the channels of the TV1, expected the channels clocked with the PLL output clock were tested to proton. They all have the same proton SEU cross-section per bit measured from a low sensitivity (with a low number of errors) below $1 \times 10^{-13} \text{ cm}^2$ at 23 MeV. The reference channel proton SEU cross-section is plotted on the Figure 2.

The SRAM heavy ion SEU cross-sectional area per bit is characterized with an asymptotic cross-section around $4 \times 10^{-8} \text{ cm}^2$ per bit and a LET threshold below $1.8 \text{ MeV} \cdot \text{cm}^2/\text{mg}$. The SRAM proton SEU cross-sectional area per bit is characterized with an asymptotic cross-section below $1 \times 10^{-13} \text{ cm}^2$ and an energy threshold below 23.5 MeV . All SEEs are upsets with a very large majority of SBUs very well balanced on bit position, on set/clear transitions and on RAM block position.

The PLL output clock never stopped. However the PLL lock signal is sensitive to PLL lock signal SEFI and to SET. It can be seen that the frequency influences those sensitivities. Because the PLL was set on a static mode to a nominal frequency of 200 MHz, increasing the gap between the nominal frequency and the working frequency increased those sensitivities. In nominal condition no any PLL lock signal SEFI was recorded on the PLL lock signal while its SET cross-sectional area based on a poor statistic attended to the small number of errors is characterized with an asymptotic cross-section below $1 \times 10^{-5} \text{ cm}^2$ and a LET threshold around $1.8 \text{ MeV} \cdot \text{cm}^2/\text{mg}$.

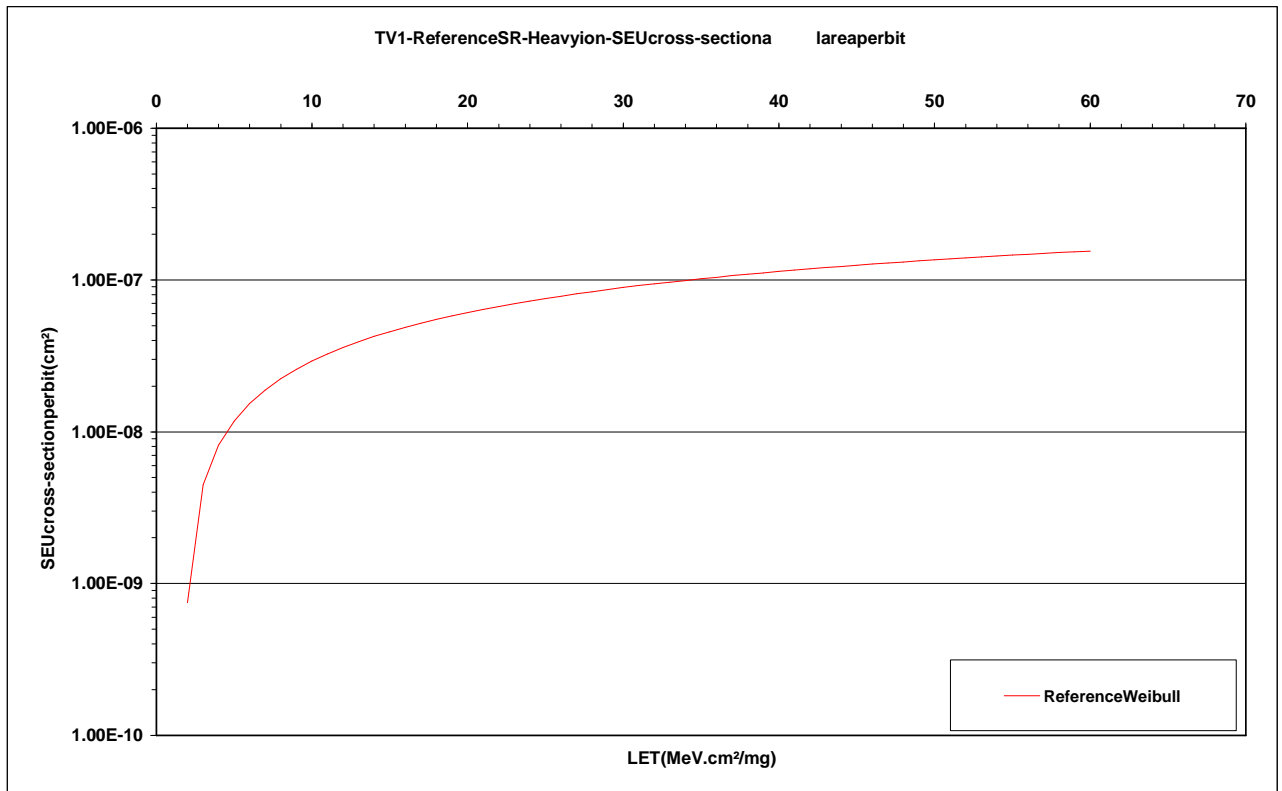


Figure1:TV1-ReferenceSR-Heavyion-SEUcross-section alareaperbit

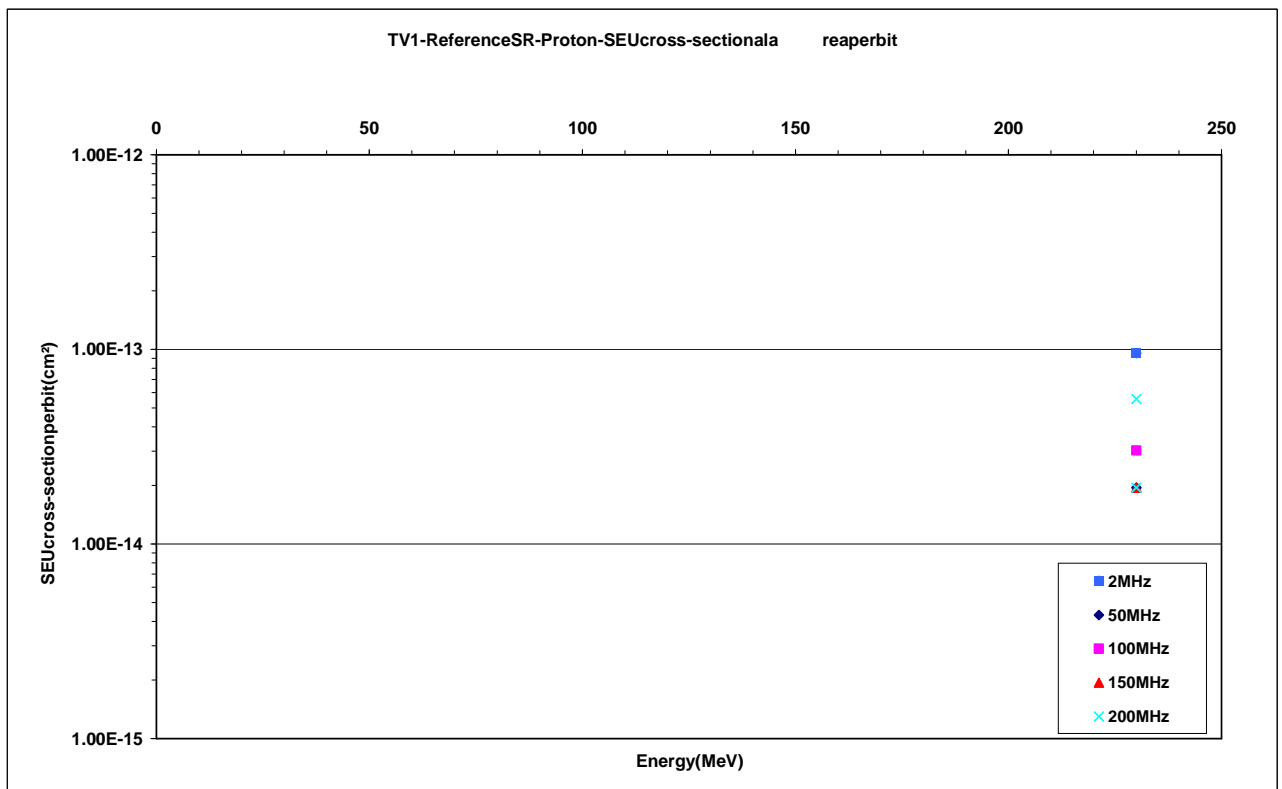


Figure2:TV1-ReferenceSR-Proton-SEUcross-section alareaperbit

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1 Introduction

ACTEL ProASIC3 flash FPGA family offers the unique combination of re-programmability and non-volatility in a high density programmable logic product. At the start of the project, the family was the only one that covered the 1 Million gates capacity requirements for space applications. Preliminary radiation test RD-1 and RD-2 results were promising. For those reasons, the ProASIC3 family was very attractive for space applications.

The objective of this study is to fully characterize the radiation sensitivity of the ProASIC3 FPGA, by performing heavy ions, proton and total ionization dose tests.

This report presents the results of Single Event Effect characterization program carried out on the device referred A3PE3000L from the ACTEL ProASIC3L Flash Based FPGA family. The Single Event Effects were characterized using:

- ✓ Heavy ions accelerator at RADEF, University of Jyväskylä, Department of Physics, Jyväskylä, Finland in June 2010 and November 2010.
- ✓ Proton accelerator at PIF, Paul Scherrer Institut (PSI), Villigen, Switzerland in March 2011.

This work was performed for ESA ESTEC under the contract number 22327/09/NL/SFE.

2 Applicable and Reference Documents

2.1 Applicable Documents

AD-1	Statement Of Work, Radiation Testing of Candidate Microelectronics Parts for Space Applications - Frame Contract, Reference TEC-QCA/CP/SOW/2008-1 Issue: 1, Revision C, 26.06.2008
AD-2	Statement Of Work, Radiation Testing of Candidate Microelectronics Parts for Space Applications - Call-Off Order 1, Reference TEC-QCA/CP/SOW/2008-2-COO1 Issue: 1, Revision C, 26.06.2008
AD-3	Hirex Engineering Proposal, Radiation Characterization of ACTEL ProASIC3L family, reference HRX/PRO/2427, Issue 1, September 15 th , 2009
AD-4	ProASIC3L low power flash FPGAs Datasheet v1.3, February 2009
AD-5	Hirex Engineering A3PE3000L design report reference HRX/SEE/0286

2.2 Reference Documents

RD-1.	S. Rezgui & al., "New Reprogrammable and Non-Volatile Radiation Tolerant FPGA: RTA3P," presented at RADECS 2007, Deauville, France, September 2007
RD-2.	S. Rezgui & al., "New Methodologies for SET Characterization and Mitigation in Flash-Based FPGAs," IEEE Trans. Nuc. Sci., vol, 54, n°6, pp. 2512-2524, Dec. 2007
RD-3.	ECSS Q60-02, "Space Product Assurance, ASIC and FPGA development," July 2007
RD-4.	Proton Irradiation Facility at the PROSCAN project of the Paul Scherrer Institute PIF facility at PSI, Ulrike Grossner, Wojtek Hajdas, Ken Egli, Roger Brun, and Reno Harboe-Sorensen, RADECS 2009.

3 DEVICE INFORMATION

3.1 Devicedescription

The tested device is the A3PE3000L. It is the biggest device by the number of gates from the ProASIC3L FPGA family from ACTEL: It includes 3 Million gates. This device is a commercial device manufactured with a 0.13 μm CMOS flash technology packaged in a PQFP 208 pins. The Radiation-Tolerant (RT) family uses the same designs and processes. So the RT3PE3000LR radiation-Tolerant device uses the same silicon as the commercial device A3PE3000L. The Table 1 summarizes the description of the device.

Parttype	A3PE3000L
PartFamily	ProASIC3L
Manufacturer	ACTEL
Package	PQ208
Datecode	0922
Packagemarking	QHR8G
Diedimensions	10.8x10.8mm
Usedsamples	Serialized from Serial Number (SN) 1 to 24

Table 1: Devicedescription

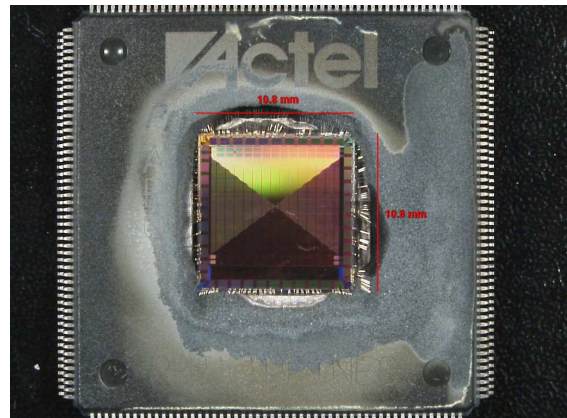
3.2 DeviceProcurement

40 samples of A3PE3000L packaged in a PQFP 208 pins were delivered at HIREX. 18 samples (serialized from SN 1 to SN 18) were dedicated to heavy ion testing and were delivered. 6 samples (serialized from SN 19 to SN 24) were reserved for proton testing and were left untouched. The left over samples were reserved for Total Ionization Dose (TID) testing.

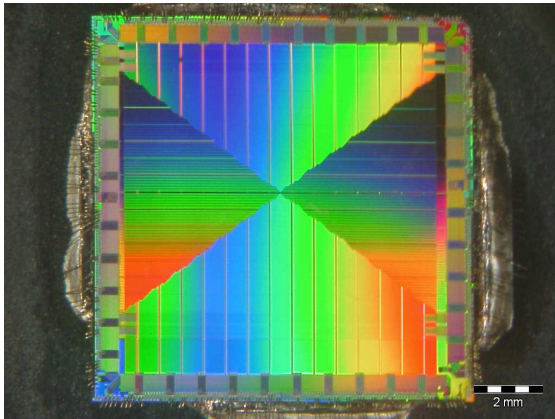
3.3 Deviceidentification



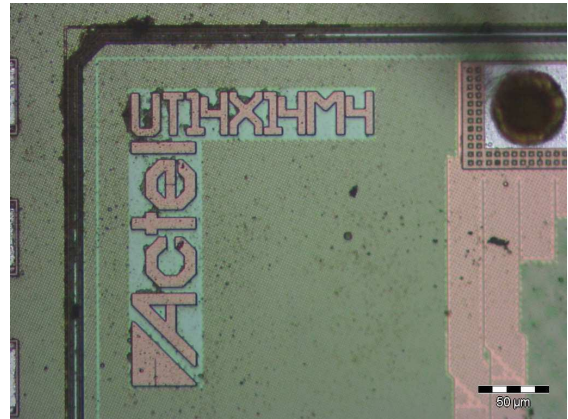
Packagemarking



Diedimensions



Full die view



Die marking

Figure3: Device identification

3.4 Sample identification

The device identification code (IDCODE) is 3E74E1CF. All samples are from the same reference (same device) and share the same IDCODE. However each sample is stamped with its own Flash Serial Number (FSN). The FSN of fused samples are provided in the following Table 2.

Serial Number (SN)	Flash Serial Number (FSN)
1	00f5dd483c70
2	00f5dd4c1c64
3	00f5dd484064
4	00f5dd483870
5	00f5dd4c2468
6	00f5dd4c1c70
7	00f5dd480c70
8	00f5dd48286c
9	00f5dd4c2c78
10	00f5dd48206c
11	00f5dd4c405c
12	00f5dd4c304c
13	00f5dd4c2884
14	00f5dd4c2860
15	00f5dd4c3078
16	00f5dd4c1874
17	00f5dd4c4074
18	00f5dd4c3478
19	00f5dd4c487c
20	00f5dd4c2478
21	00f5dd481c64
22	00f5dd4c4078
23	00f5dd481470
24	00f5dd4c2078

Table 2: Sample identification

A visual identification was materialized on each DU incised. The SN and FSN correspondance was verified

at all time.

4 RADEFTESTFACILITY

2 Heavy ions test campaign were performed at the cyclotron accelerator at the University of Jyväskylä, Finland in June and November 2010 under HIREX Engineering responsibility.

The facility includes a special beam line dedicated to irradiation studies of semiconductor components and devices. It consists of a vacuum chamber including component movement apparatus and the necessary diagnostic equipment required for the beam quality and intensity analysis.

The cyclotron is a versatile, sector-focused accelerator of beams from hydrogen to xenon equipped with three external ion sources: two electron cyclotron resonance (ECR) ion sources designed for high-charge state heavy ions, and a multicusp ion source for intense beams of protons. The ECR's are especially valuable in the study of single event effects (SEE) in semiconductor devices. For heavy ions, the maximum energy attainable can be determined using the formula

$$130Q^2/M,$$

Where Q is the ion charge state and M is the mass in Atomic Mass Units.

4.1 Beam quality control

For measuring beam uniformity at low intensity, a CsI(Tl) scintillator with a PIN-type photodiode readout is fixed in the mounting fixture. The uniformity is measured automatically before component irradiation and the results can be plotted immediately for more detailed analysis.

A set of four collimated PIN-CsI(Tl) detectors is located in front of the beam entrance. The detectors are operated with step motors and are located at 90 degrees with respect to each other. During the irradiation and uniformity scan they are set to the outer edge of the beam in order to monitor the stability of the beam homogeneity and flux.

Two beam wobblers and/or a 0.5 microns diffusion Gold foil can be used to achieve good beam homogeneity. The foil is placed 3 mm in front of the chamber. The wobbler-coils vibrate the beam horizontally and vertically, the proper sweeping are being attained with the adjustable coil-currents.

4.2 Dosimetry

The flux and intensity dosimeter system contains a Faraday cup, several collimators, a scintillation counter and four PIN-CsI(Tl) detectors. Three collimators of different size and shape are placed 25 cm in front of the device under test. They can be used to limit the beam amount to the active area to be studied.

At low fluxes a plastic scintillator with a photomultiplier tube is used as an absolute particle counter. It is located behind the vacuum chamber and is used before their irradiation to normalize the counter rates of the four PIN-CsI(Tl) detectors.

4.3 Used ions

The RADEF used ions are listed in the following table.

Ions specie	Energy (MeV)	LET Meas. @ Surface (MeV.cm ² /mg)	Range(Si) (µm)
¹⁵ N ⁺⁴	139	1.87	202
²⁰ Ne ⁺⁶	186	3.68	146
⁴⁰ Ar ⁺¹²	372	10.08	118
⁵⁶ Fe ⁺¹⁵	523	18.84	97
⁸² Kr ⁺²²	768	30.44	94
¹³¹ Xe ⁺³⁵	1217	54.95	89

Table 3: RADEF, used ions and features

5 PIFTESTFACILITY

Proton tests were performed at the Proton Irradiation Facility (PIF) at Paul Scherrer Institut (PSI), Villigen, Switzerland in March 2011 under HIREX Engineering responsibility.

A description of PIF test facility can be found in RD-4. As shown in Figure 4, proton beam from COMET cyclotron is delivered to the experimental PIF cave with an input energy that can be varied from few MeV up to 250 MeV. Then in PIF room, local copper degrader can be inserted into the beam to obtain the different user energies.

In March 2011, 230 MeV input beam's energy was selected and calibrated. The corresponding calibration result is shown in Figure 5.

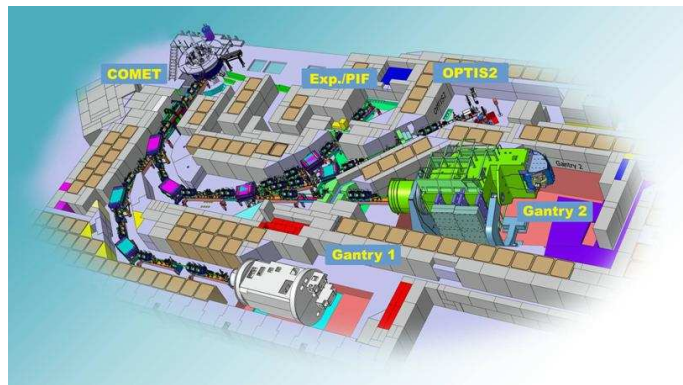


Figure 4: Proscan facility

	Energy [MeV]	Degr. [mm]	Plastic [cnt/s]	IC-target [cnt/s]	IC-degr [cnt/s]	Target(1) Fac. 20nA [p/cnt/cm2]	Degr(2) Fac. 20nA [p/cnt/cm2]	Target(1) Fac. 200nA	Degr(2) Fac. 200nA	Target(1) Fac. 2 uA	Degr(2) Fac. 2 uA	PL6 distance 5.0 cm to collim collim 20 mm diam 1 sec test
Pos 1	230	0.0	265698	724	288	6143.5	15548.5					
1	230	0.0	265662	721	286	6168.3	15656.4					
			4.5	3.20	3.2	6.16E+03	1.56E+04	6.16E+04	1.56E+05	6.16E+05	1.56E+06	
Pos 1	200	11.5	235645	752	289	5244.8	13741.6					
2	200	11.5	234835	747	289	5262.0	13694.3					
			4.5	3.20	3.2	5.25E+03	1.37E+04	5.25E+04	1.37E+05	5.25E+05	1.37E+06	
Pos 1	151.2	28.0	151773	824	288	3081.7	8881.6					
3	151.2	28.0	151410	824	289	3074.3	8829.3					
			4.5	3.20	3.2	3.08E+03	8.86E+03	3.08E+04	8.86E+04	3.08E+05	8.86E+05	
Pos 1	101.4	41.4	90201	1015	291	1485.7	5223.3					
4	101.4	41.4	88679	1008	289	1470.8	5171.1					
			4.5	3.20	3.2	1.48E+03	5.20E+03	1.48E+04	5.20E+04	1.48E+05	5.20E+05	
Pos 1	75.3	47.0	62202	1223	291	849.8	3601.9					
5	75.3	47.0	61877	1212	288	853.1	3620.8					
			4.5	3.20	3.2	8.51E+02	3.61E+03	8.51E+03	3.61E+04	8.51E+04	3.61E+05	
Pos 1	50.9	50.9	46004	1536	292	500.2	2654.6					
5	50.9	50.9	45969	1536	291	499.8	2661.8					
			4.5	3.20	3.2	5.00E+02	2.66E+03	5.00E+03	2.66E+04	5.00E+04	2.66E+05	
Pos 1	23.5	54.0	20311	2829	286	119.8	1196.8					
5	23.5	54.0	19743	2885	287	114.2	1159.2					
			4.5	3.20	3.2	1.17E+02	1.18E+03	1.17E+03	1.18E+04	1.17E+04	1.18E+05	

Figure 5: Calibration results - input energy 230 MeV proton

6 STATEMENT OF WORK-REQUIREMENTS

The Statement of Work (SOW) requirements were defined in AD-1 and AD-2. Here follows the bolded parts:

- ✓ Perform heavy ion, proton and total ionization dose tests on an A3PE3000L device.
- ✓ Evaluate the sensitivities of SEL, SEU, SET, SEFI and SEGR.
- ✓ Check configuration flash after each irradiation steps and additional runs should be performed while the device is in configuration process.
- ✓ Perform tests at room temperature. Further tests performed at 80 °C to evaluate the parts to the SEL sensitivity while power supplies are raised to a higher level than the nominal one.
- ✓ Use static0, static1, checkerboard and checkerboard complemented patterns.
- ✓ Shift registers clock frequency set to 2, 50, 100 and 200 MHz.
- ✓ Perform tests in dynamic condition.
- ✓ All errors should be detected, time stamped, recorded and reported with the relevant information like word address, expected value, word in error, error signature, etc.

To do such characterization, the project included the design of 2 Test Vehicles (TVs).

6.1 TEST VEHICLE DESIGN REQUIREMENTS

Two test vehicle designs were required. The aim of the first test vehicle was to characterize the different elements of the FPGA while the second test vehicle was to implement SEE mitigation. RD-1, RD-2 and RD-3 were applicable.

The first test vehicle was to be made of shift register chains with or without layers of combinational logic (inverters) between the flip-flops as shown in Figure 6 and the combinational logic made of 8 levels of inverters [or less depending on the timing simulation results]. It was also requested, each four registers in some chains, a separate fan-out tree with 8 inverters [or less depending on the timing simulation results] in enable or reset paths.

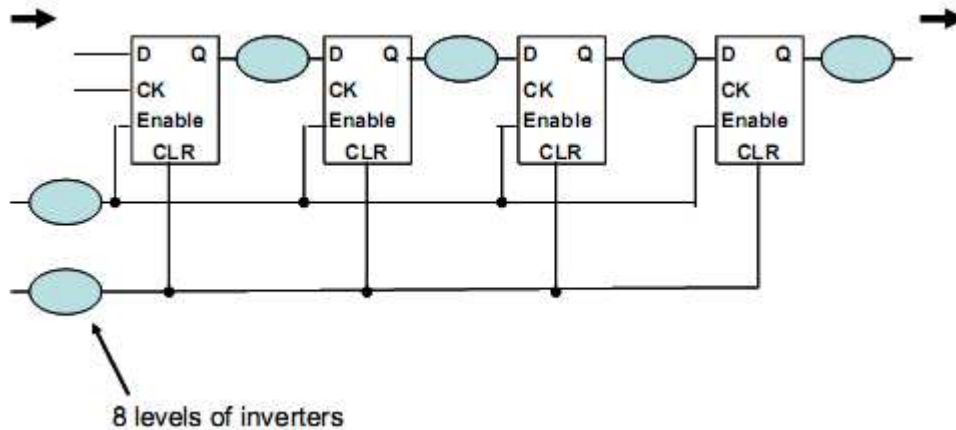


Figure 6: Basic shift register block

In addition to standard 3.3V LVCMOS I/Os, some channels were required to use LVDS differential I/Os and DDR I/Os. Finally, some channels were requested to be clocked with a 200 MHz clock generated from the FPGA internal PLL: all other channels having a common external clock inputs. Table 4 summarizes the characteristics of the different shift registers of the TV1. Each channel made of 1024 registers. The four last registers outputs of each channel were requested to be accessible externally: this allowing the test of the channel at a frequency four times slower than the channel clock frequency.

In addition it was required in the test vehicle a specific interface design to test the FPGA internal SRAM (512x9) (read and write), and flash ROM (128x8) (read only).

The second test vehicle was required to be made of shift registers with or without layers of combinational logic (inverters) between the flip-flops as the first test vehicle, plus implementing SEU and SET mitigation. Only LVCMOS/OS standard was to be used in this design.

Chain #	Clock	Logic between registers	Register enable fanout	Register CLR fanout	I/O type
1	External	no	no	no	LVC MOS 3.3V
2	External	no	yes	no	LVC MOS 3.3V
3	External	no	no	yes	LVC MOS 3.3V
4	External	yes	no	no	LVC MOS 3.3V
5	External	no	no	no	DDR 3.3V
6	External	no	no	no	DDR 3.3V
7	External	no	no	no	DDR 3.3V
8	External	no	no	no	DDR 3.3V
9	External	no	no	no	LVDS 2.5V
10	External	no	no	no	LVDS 2.5V
11	Internal, PLL 200 MHz	no	no	no	LVC MOS 3.3V
12	Internal, PLL 200 MHz	no	no	no	LVC MOS 3.3V
13	Internal, PLL 200 MHz	no	no	no	LVC MOS 3.3V
14	Internal, PLL 200 MHz	no	no	no	LVC MOS 3.3V

Table4:TV1-shift registers characteristics

7 TESTVEHICLEDESIGNS

The first phase of the project was to design two Test Vehicles (TVs). The design phase included:

- ✓ Specification
- ✓ Description
- ✓ Simulation
- ✓ Test and validation

The result of the Test Vehicle design phase is reported in AD-5.

The first TV was used to characterize the sensitivity of the device while the second was used to characterize the SE mitigation techniques. As a consequence the TV1 implemented:

- ✓ Shift Registers (SR) with different input/output configurations
- ✓ Clock Conditioning Circuit (CCC) with Phase-locked Loop (PLL)
- ✓ SRAM memory
- ✓ UFROM memory

While the second TV was fully used to implement SE mitigation techniques on shift registers.

All shift registers of both TVs were made of 1024 registers each and, if not specified otherwise, used common:

- ✓ Reset (clear)
- ✓ Clock
- ✓ Enable
- ✓ Input data

The common clock, enable and reset signals were routed on global network resources of the device. All sequential logic core (registers) were implemented by D-type flip-flop with enable and clear active high. The place and route processes of the design were left to the charge of the manufacturer's design software (not placed/routed by hand).

7.1 TV1-SHIFTREGISTERS

The Table 5 summarizes the specifications of shift register channels implemented on the TV1.

Shift Register	Clock	I/O Type	Particularity
1	External	3.3V LVCMOS	Reference
2	External	3.3V LVCMOS	Global Enable C-cell
3	External	3.3V LVCMOS	Global Reset C-cell
4	External	3.3V LVCMOS	C-cell
5	External	3.3V LVCMOS-DDR	DDR I/O
6	External	3.3V LVCMOS-DDR	DDR I/O
7	External	3.3V LVCMOS-DDR	DDR I/O
8	External	3.3V LVCMOS-DDR	DDR I/O
9	External	2.5V LVDS	LVDS I/O
10	External	2.5V LVDS	LVDS I/O
11	CCC/PLL	3.3V LVCMOS	CCC/PLL Clock
12	CCC/PLL	3.3V LVCMOS	CCC/PLL Clock
13	CCC/PLL	3.3V LVCMOS	CCC/PLL Clock
14	CCC/PLL	3.3V LVCMOS	CCC/PLL Clock

Table 5: TV1-Shift Registers specifications

The first SR is the reference. It is a standard SR as it can be seen on the Figure 7.

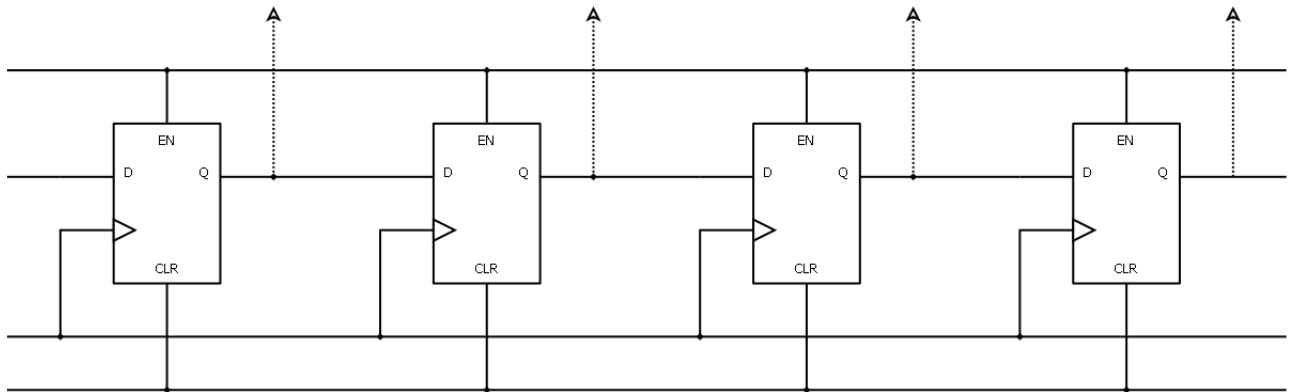


Figure7:TV1-SR1-Schematic

On the previous shift register schematic as well as for the following shift register schematics, all dotted outputs of the D flip-flops are applicable for the four last registers outputs of all shift registers because they are accessible externally.

The second shift register is identical to the reference adding combinational cells (C-Cell) on the global enable signal. Each four register stages have a separate level of 4 inverters computing a "local enable signal" from the global one. This principle is detailed on the Figure 8. To increase the maximum working frequency of this channel, the number of inverters on the enable signal was decreased from 4 to 2 in October 2010 (after the first RADEF campaign) to conform to the decision taken during the phone review meeting of October 22^{sd} 2010.

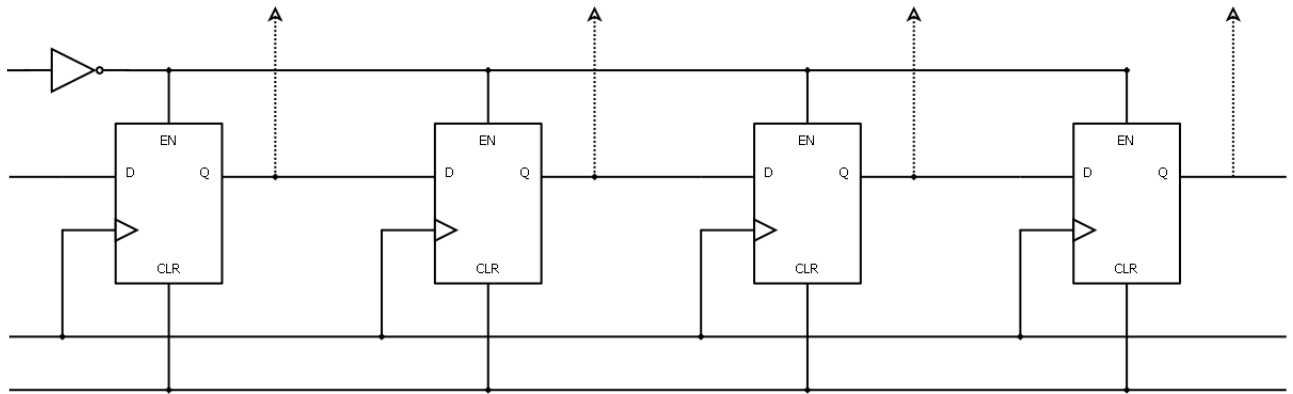


Figure8:TV1-SR2-Schematic

The third shift register is identical to the reference adding combinational cells (C-Cell) on the global reset signal. Each four register stages have a separate level of 4 inverters computing a "local reset signal" from the global one. This principle is detailed on the Figure 9. The number of inverters on the reset signal was decreased from 4 to 2 in October 2010 (after the first RADEF campaign) to conform to the decision taken during the phone review meeting of October 22^{sd} 2010.

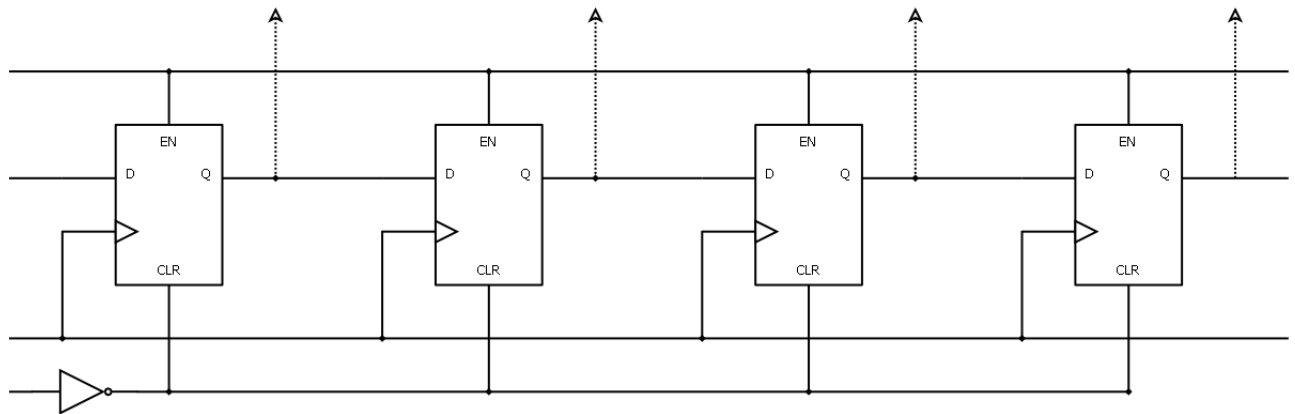


Figure9:TV1-SR3-Schematic

The fourth shift register is identical to the reference adding combinational cells (C-Cell) between each register. Each combinational path has a separate level of 4 inverters. This principle is detailed on the Figure 10. To increase the maximum working frequency of this channel, the number of inverters between each register was decrease from 4 to 2 in October 2010 (after the first RADEF campaign) to conform to the decision taken during the phone review meeting of October 22nd 2010.

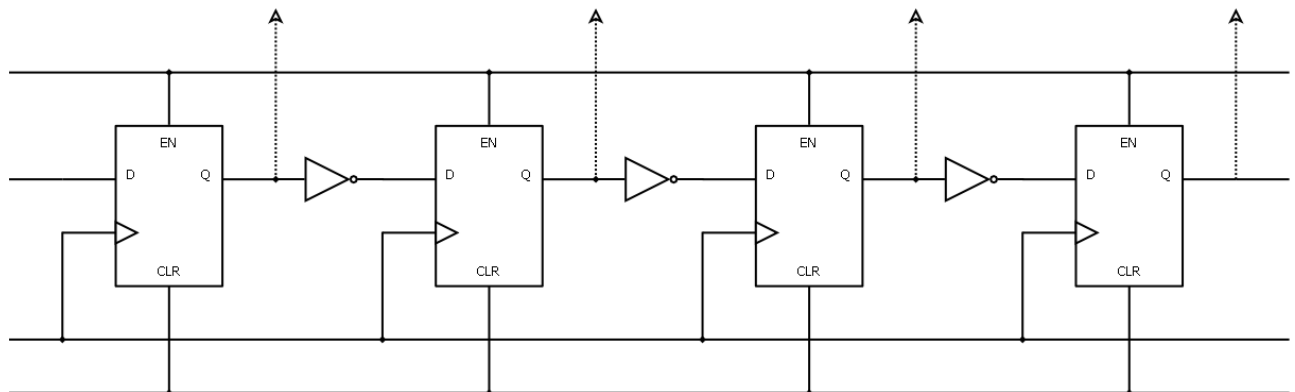


Figure10:TV1-SR4-Schematic

The shift registers from the fifth to the eighth are identical to the reference. Using 2 shift registers mounted as a pair, both pairs include a 3.3V LVCMOS Double Data Rate (DDR) input standard to drive the shift registers inputs data and also use a 3.3V LVCMOS DDR standard to drive 2 data outputs each. That principle is detailed on the Figure 11.

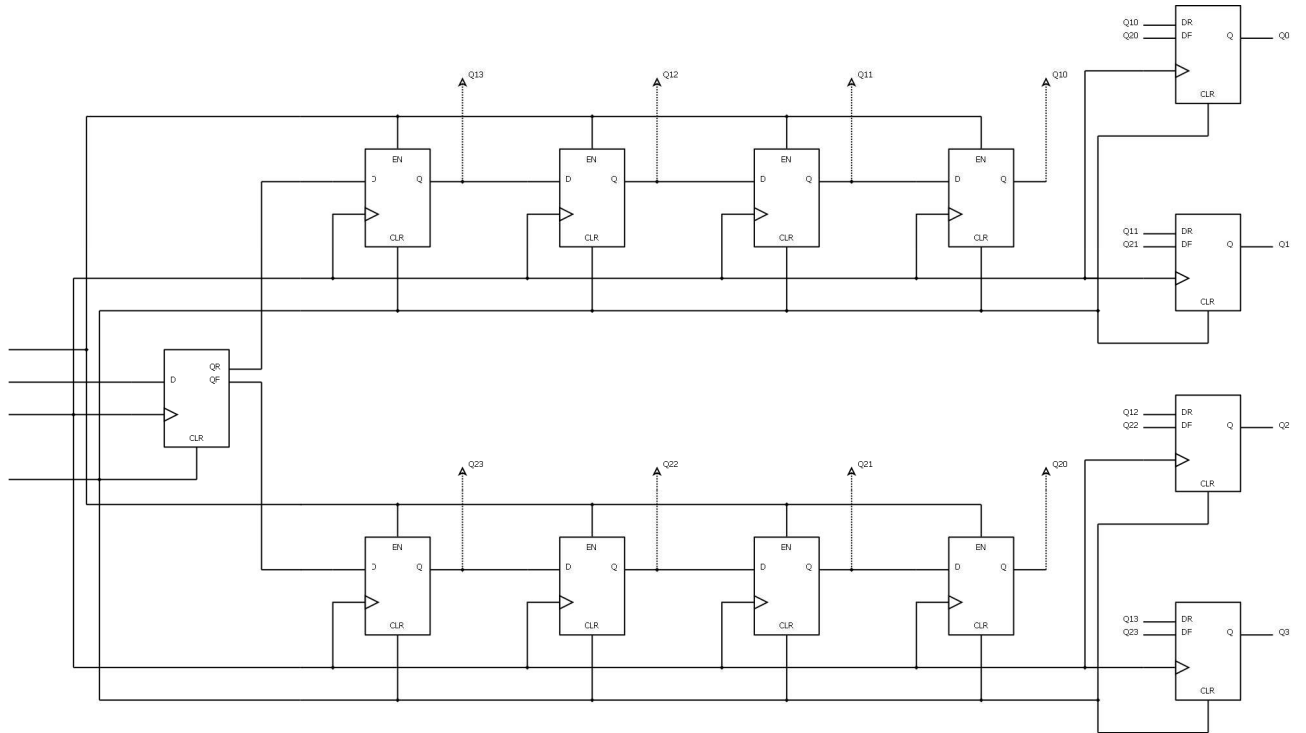


Figure11:TV1-SR5,6,7and8-Schematic

The ninth and tenth shift registers are identical to the SR1. However those channels use a 2.5 V LVDS standard as input and output standard.

o the SR1. However those channels use a 2.5 V LVDS

The 4 shift registers from the eleventh to the fourteenth are identical to the SR1. However the clock generated by the internal CCC with a PLL module from

teenth are identical to the SR1. However the clock is generated by the internal CCC with a PLL module from

Those 14 shift registers used around 30% of the FPGA

A's logic tiles and 71 inputs/output pads.

With the decrease number of inverters (2 instead of 4), the maximum working frequency of the shift registers is 200MHz.

4), the maximum working frequency of the shift registers is

7.2 TV2-SHIFTREGISTERS

The Table 6 summarizes the specifications of shift registers implemented on the TV2.6 Shift registers use 5 different SEU and SET mitigation methods.

registers implemented on the TV2.6 Shift registers use 5

Shift Register	Sequential Cell Triplexation	I/O Block Triplexation	SET Filtering	Combinational Cell Duplication	Combinational Cell Triplexation
1	✓				
2	✓	✓			
3			✓		
4	✓	✓	✓		
5	✓	✓		✓	
6	✓	✓			✓

Table6:TV2-ShiftRegisters specifications

The first SR of the TV2 is identical to the TV1 SR1 (register) triplexation and a voter at the input of Redundancy (TMR) of the sequential logic as SEU mitigation method. Only 1 data input drives the shift register while 3 data output. The same global signals (clock, reset and enable) routed on the global network are shared between the 3 lines. That principle is detailed on the Figure 12.

(the reference). However it includes sequential cell triplexation and a voter at the input of each register stage. This SR uses the Triple Modular Redundancy (TMR) of the sequential logic as SEU mitigation method. Only 1 data input drives the shift register while 3 data output. The same global signals (clock, reset and enable) routed on the global network are shared between the 3 lines. That principle is detailed on the Figure 12.

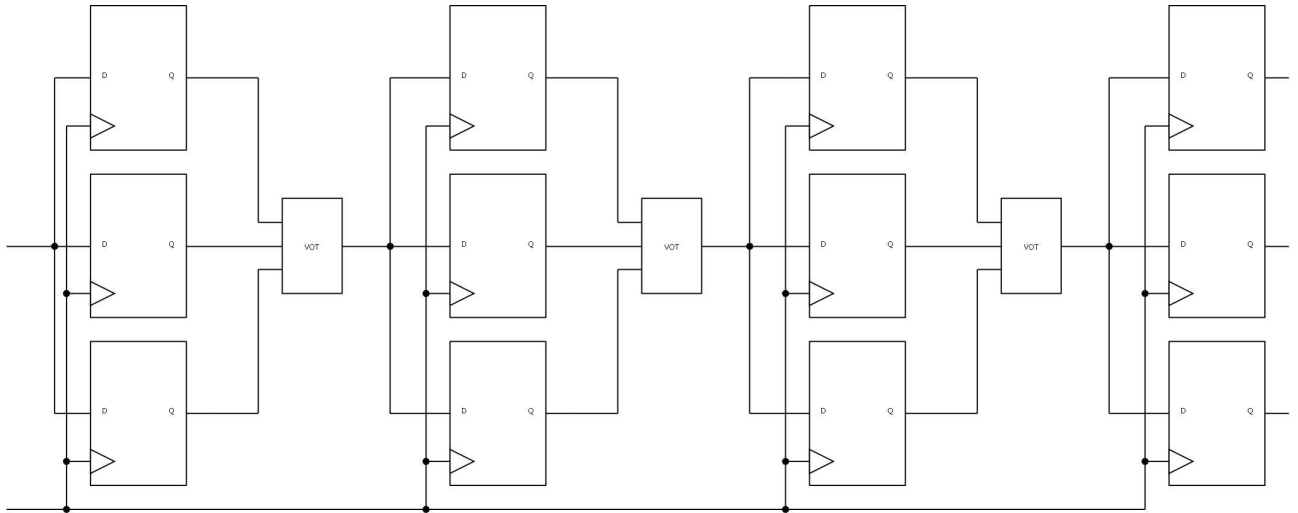


Figure12:TV2-SR1-Schematic

To ease the understanding of the schematic, on the previous figure as well as for the following ones, the previous dotted lines for the 4 data outputs of the last 4 register stages as well as the global enable and clear signals have not been drawn but still remain applicable.

The second shift register is similar to the SR1 (of the TV2) using the triplication of the sequential logic as SEU and SET mitigation. Each flip-flop input is generated using a separate voter and so 3 voters are used at each register stage. That principle is detailed on the Figure 13.

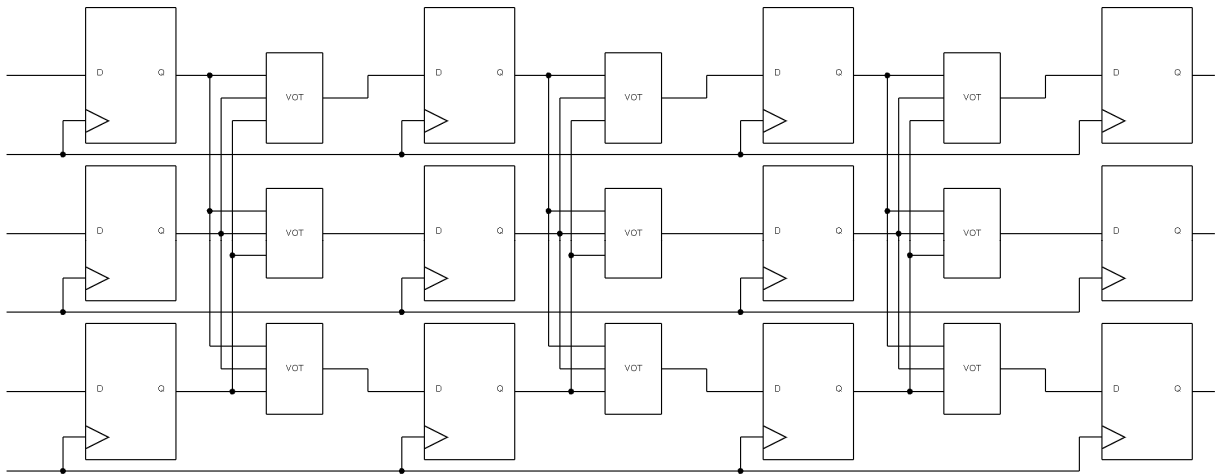


Figure13:TV2-SR2-Schematic

The third shift register is identical to the SR1 of the TV1 (the reference) plus it includes SET filtering method at the combinational logic output as SET mitigation. This method consists of voting, with a guard gate, the current state of the output of the combinational logic with its own state delayed (here with a delay around 2 ns). That principle is detailed on the Figure 14.

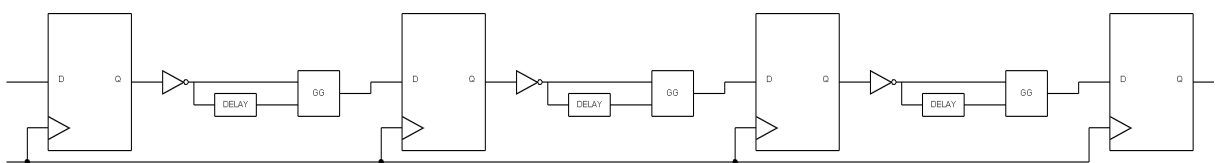


Figure14:TV2-SR3-Schematic

The fourth shift register is identical to the TV2 SR4 in addition it includes an SET filtering mitigation with a delay around 3ns. This shift register principle is detailed on the Figure 15.

R2 including sequential logic and I/O bank triplication. In that delay around 3ns. This shift register principle is detailed on the Figure 15.

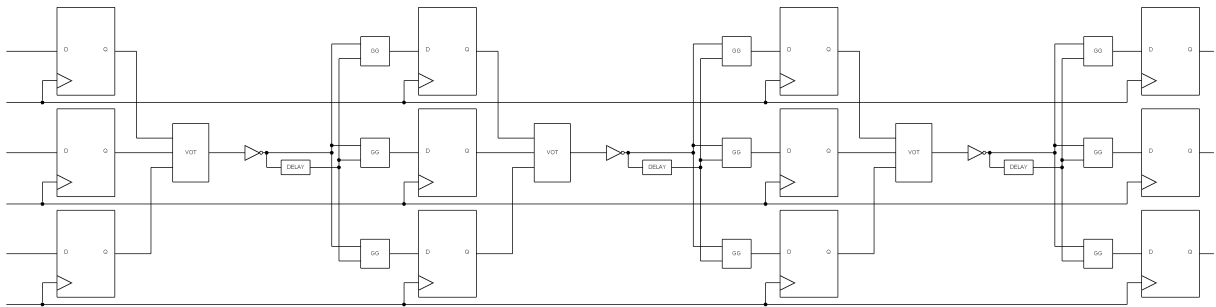


Figure15:TV2-SR4-Schematic

The fifth shift register includes sequential logic duplication as SEU and SET mitigation. That principle is detailed on the Figure 16.

triplication, IO bank triplication and combination logic duplication as SEU and SET mitigation. That principle is detailed on the Figure 16.

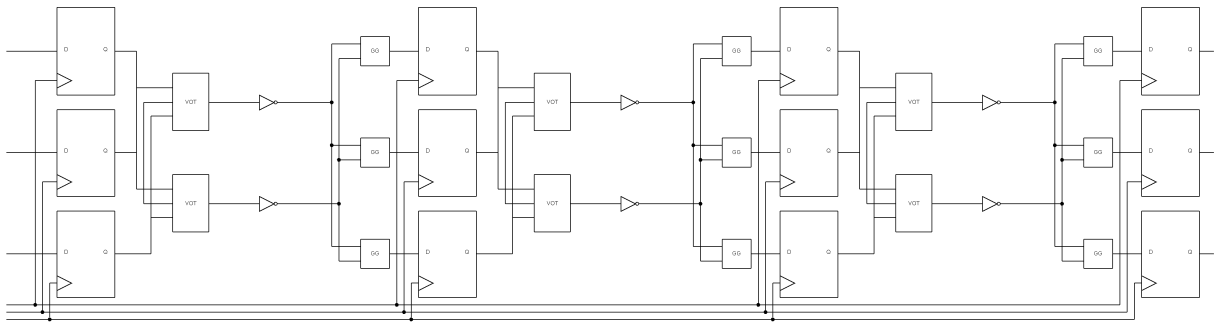


Figure16:TV2-SR5-Schematic

The sixth shift register implements the full triplication (full TMR) as SEE mitigation. That principle is detailed on the Figure 17.

triplication (full TMR) as SEE mitigation. That principle is detailed on the Figure 17.

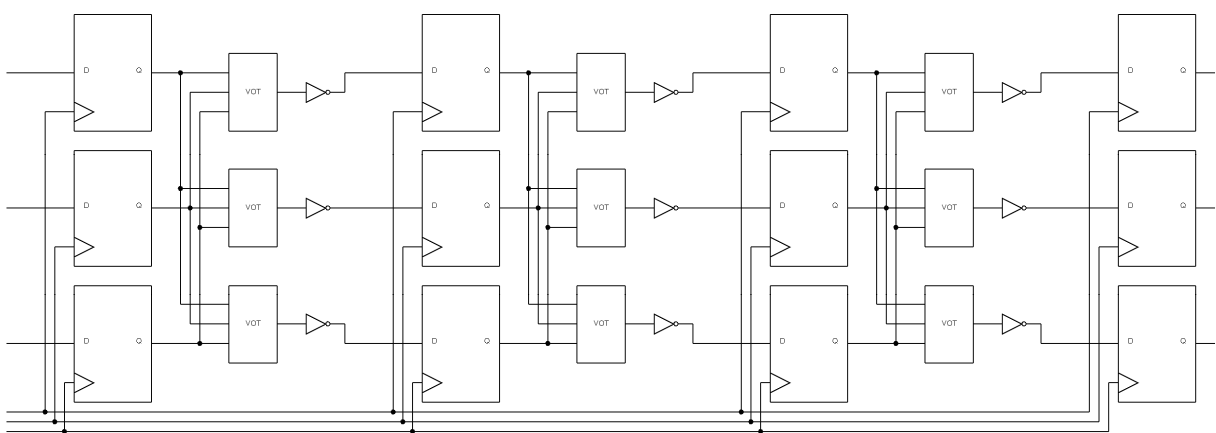


Figure17:TV2-SR6-Schematic

With 2 inverters as SET generation line (combinational path) between each register cell, 1 logic tile to generate a voter as well as a guard gate (with a combinational loop) and specified delay lines this design uses around 78% of the logic tiles and 76 inputs/outputs.

With 2 inverters as SET generation line (combinational path) between each register cell, 1 logic tile to generate a voter as well as a guard gate (with a combinational loop) and specified delay lines this design uses around 78% of the logic tiles and 76 inputs/outputs.

Time penalties induced by the combinational paths, voters, delay lines, guard gates and additional routing delays limit the maximum working frequency of the shift register to 50MHz (70MHz for some channels).

Time penalties induced by the combinational paths, voters, delay lines, guard gates and additional routing delays limit the maximum working frequency of the shift register to 50MHz (70MHz for some channels).

7.3 SRAM

100% of the device embedded SRAM is used on the TV1. The first half made of 56 blocks of 512 words of 9 bits is located on the north side of the die while the other half is located on the south. To access all memory blocks, all blocks are cascaded and the output is multiplexed. The SRAM is implemented in synchronous mode for both read/write operations. The SRAM functional block uses dedicated clock routed on one global line, control signals, address and data buses and is entirely independent of the remainder of the design.

The Flash Freeze type 1 is also implemented on the design.

7.4 UFROM

100% of the device embedded UFROM was used on the TV1. The UFROM block was made of 128 words of 8 bits configured with a checkerboard interleaved with its complement. The UFROM functional block used dedicated clock, address and data buses and was entirely independent of the remainder of the design.

7.5 CLOCK CONDITIONING CIRCUIT/PHASE-LOOKED LOOP

The TV1 included one CCC with PLL configured in a static mode set on 200MHz. The input clock signal was the global input clock while the PLL output was routed on one global line. The PLL output was used to clock 4 shift registers of the TV1. The PLL lock and power-down signals were output and input of the design.

The TV2 design did not implement the CCC with PLL blocks.

7.6 TV RESOURCES USAGE

The Table 7 summarizes the resources usage of both TVs.

	Total Number	Total Number on TV1	Total Number on TV2
Core tiles	75264	22758(30%)	58368(78%)
Core tiles used as combinational cell	-	8415(37%)	41984(72%)
Core tiles used as sequential cell	-	14343(63%)	16384(28%)
I/O	147	139(95%)	76(52%)
I/O used as differential	65	13(20%)	0(0%)
Chip Global	6	6(100%)	6(100%)
Quadrant Global	12	0(0%)	0(0%)
Local Clock	-	0	3
PLL	2	1(50%)	0(0%)
RAM (Block)	112	112(100%)	0(0%)
Low Static ICC	1	0(0%)	0(0%)
User Flash ROM (Block)	1	1(100%)	0(0%)
User JTAG	1	0(0%)	0(0%)
Flash Freeze	1	Type1	No

Table 7: TVs-Resources usage

8 TESTSET-UP AND CONDITIONS

The test system is based on a Virtex-5 FPGA (XILINX) of test board includes a DUT power supplies control independent channels. A temperature control and regulation system is added to heat the DUT whenever needed. Ambient temperature is used otherwise. The and the computer running the controlling GUI software is made using a 100 MBit/s Ethernet link. The Figure 18 displays the principle of the test system used for heavy ion tests.

It has 168 I/O including 44 LVDS channels. The controller which manages the DUT power supplies up to 24 independent channels. A temperature control and regulation system is added to heat the DUT whenever needed. Ambient temperature is used otherwise. The communication between the under vacuum test system and the computer running the controlling GUI software is made using a 100 MBit/s Ethernet link. The Figure 18 displays the principle of the test system used for heavy ion tests.

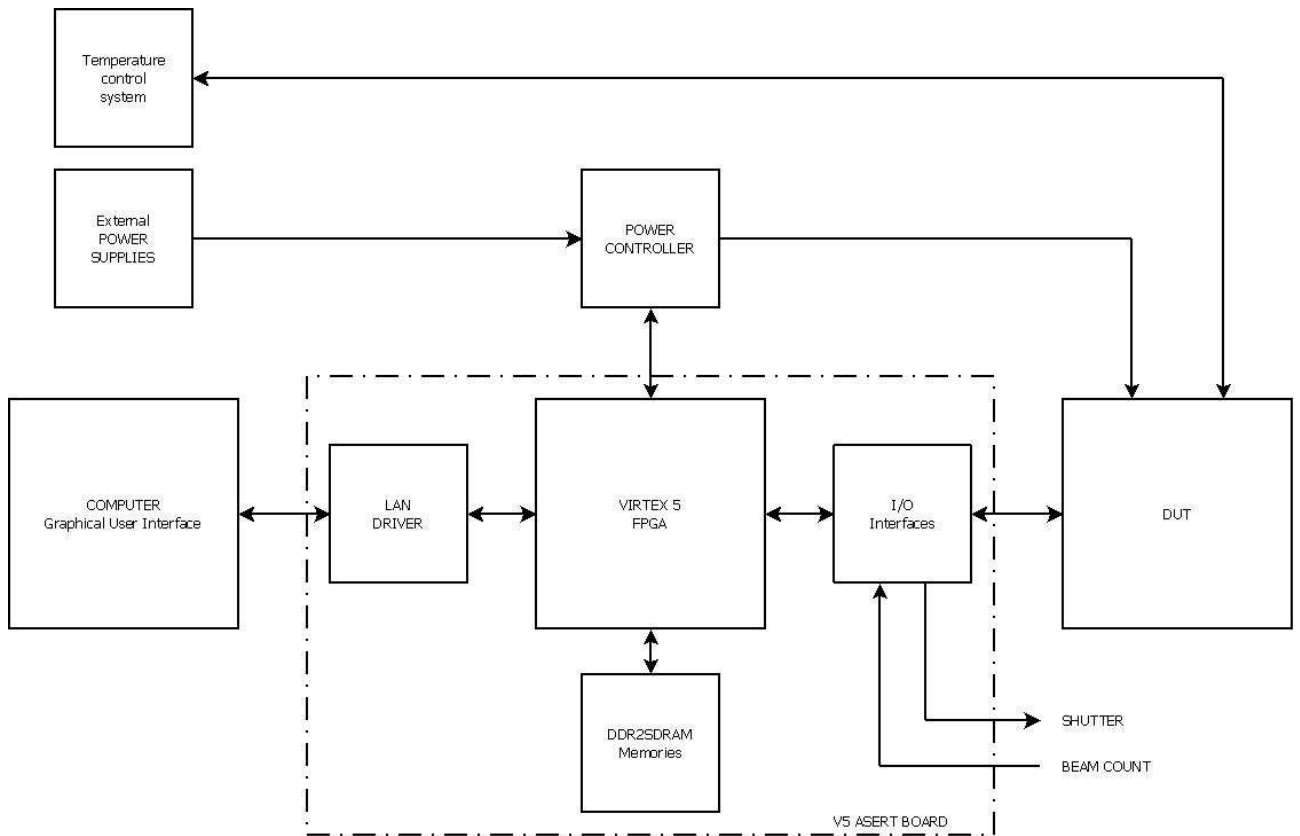
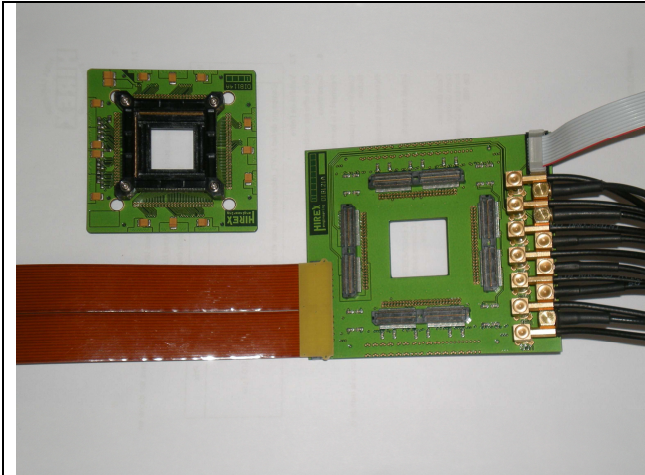


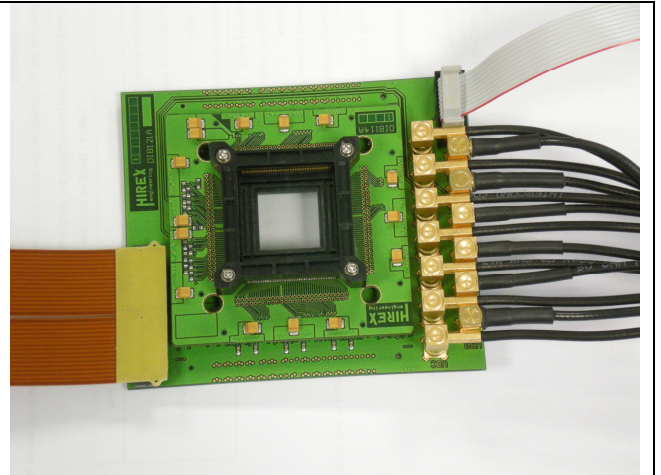
Figure 18: Heavy ion test set-up

The DUT side of the tester is composed of a set of connecting directly on the tester implementing voltage level translators, power supply connectors, LVDS connectors and the ISP connector. It received onto daughterboard received as a sample (or socket) directly and terminal resistors. All samples were soldered onto socket instead of a device. An access area was realized below the DUT footprint on both boards to allow the heating system and temperature sensor to take place in close contact to the bottom of device's package. Both test vehicles used the same hardware (also the

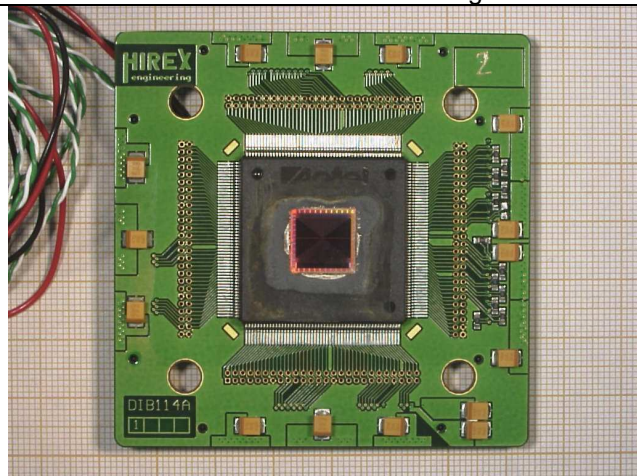
same hardware) as shown on the Figure 19. A motherboard age level translators, power supply connectors, LVDS connections system to plug the daughterboard. The lysoldered in the middle as well as decoupling capacitor on a daughter board. Two daughter boards received a sized below the DUT footprint on both boards to allow the heating system and temperature sensor to take place in close contact to the bottom of device's package. Both test vehicles used the same hardware (also the



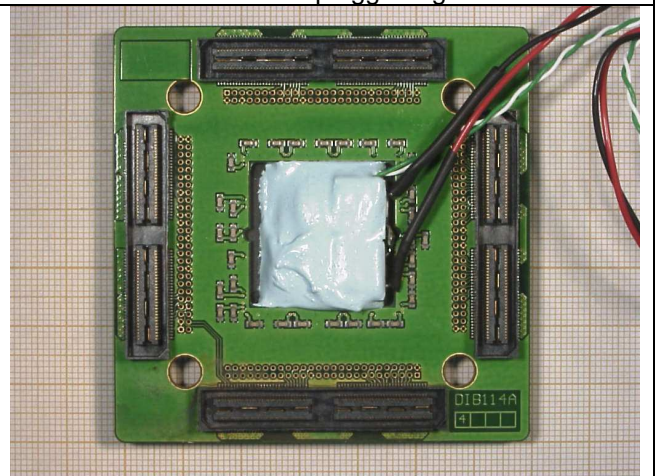
ADUTdaughterboard(heresolderedwithasocket) ontheleftandamotherboardontheright



ADUTdaughterboard(heresolderedwithasocket) andamotherboardpluggedtogether



ADUTdaughterboard(top)-SN2



ADUTdaughterboard(bottom)withheatingsystem andtemperaturesensormounted

Figure19:DUTboardset

8.1 Powersupply

The following 13 channels were defined to monitor the DUT power supplies. They were independently monitored using for each channel a set of selectable parameters (start and stop delay, current threshold, inhibit time...) and were globally controlled.

- ✓ 1 coresupply
- ✓ 8 banksupplies
- ✓ 2 PLLsupplies
- ✓ 1 chargepumpsupply
- ✓ 1 JTAGsupply

The Table 8 details the voltage range admissible for each channel previously defined.

NAME	DESCRIPTION	FUNCTIONING			PROGRAMMING		
		Min(V)	Nominal(V)	Max(V)	Min(V)	Nominal(V)	Max(V)
Vcc	Coresupplyvoltage	1.35	1.5	1.65	1.35	1.5	1.65
Vccbx	I/OBankSupplyvoltage	2.25 3.0	2.5 3.3	2.75 3.6	2.25 3.0	2.5 3.3	2.75 3.6
Vccplx	PLLsupplyvoltage	1.35	1.5	1.65	1.35	1.5	1.65
Vjtag	JTAGsupplyvoltage	0	0	0	3	3.3	3.6
Vpump	ChargePumpsupplyvoltage	0	0	0	3	3.3	3.6

Table8: Powersuppliesconditions

The device belonging to the ProASIC3L family (learning low power) is working with the core voltage (V_{cc}) down to 1.2 Volts. However the device was not properly functioning when increasing the working frequency. For this reason the core voltage was kept at 1.5V.

Unused power supplies (like JTAG and charge pump power supplies while the device is not in configuration mode), and unused I/O were kept at the reference voltage (0V).

The Table 9 summarizes the applied test conditions on the current thresholds of the DUT power supplies.

Target-Mode	Core current threshold (mA)	Bank current thresholds (mA)	PLL current thresholds (mA)	JTAG and PUMP current thresholds (mA)
TV1-Dynamic	950	600	100	NA
TV1-Static	950	250	100	NA
TV1-FlashFreeze	950	250	100	NA
TV2-Dynamic	950	600	NA	NA
Programming	950	600	100	100

Table9: Powersupplies-Currentthresholds

8.2 Shiftregisters

Thebasicshiftregisterstestsequenceusedwas:

```

Initialization
Loop
  Exposition
  Check&Fill
Endloop

```

Theinitializationstepwasneededtoinitializetheshiftregisterswithaselectedpattern.Thecheck&fillstep was made to read and verify the content of all channels while they were filled with another (or the same) pattern.

Theusedpatternswerethestandardcheckerboardandcomplementedcheckerboard,static0andstatic1. Theshiftregisterclockfrequency(selectablefromtheGUI)wassetto2,50,100,150and200MHzforthe firstTVwhileitwassetto2,37.5,50and70MHzforthesecondTV.

Dynamic tests were performed. One additional run was performed in a static mode using the Hirex shutter system.

SEFIandSEUaretreatedonapost-treatmentprocess. Thisclassificationprocessallowedthedetectionof SEFI,SBUandMBU.

8.3 SRAM

TheTV1uses100%ofthedevice'sembeddedSRAM.Itwasmadeof112blocksof512wordsof9bits.To accessallmemoryblocks,allblockswerecascadedandtheoutputsweremultiplexed.

TheSRAMfillandtheSRAMcheckalgorithms(Figure20andFigure21)werebothdesignedtohighlight differenttypesoferrors(writeerror,readerror,upset,stuckbits...)ofbasicmemorycells.Eachmemorycell onablockcanbesequentiallyorinterleavedmanestedwithdifferentcombinationsofbothalgorithms.

Tobetestedtheselectedmemoryblockhasfirsttobefilledusingthefillalgorithm.Thenthesame memory blockcanbe:

- ✓ Checkedentirelythenfilledagainentirelymakingthetestsequential.
- ✓ Checkedandfilledmemoryaddresspermemoryaddressmakingthetestinterleaved.

TheSRAMfillandcheckalgorithmsreporteachtypeoferrorherelistedontheTable10:

Error type	FILL algorithm	CHECK algorithm	Error source
No-error	Noerrorfrom1write/read	Noerrorfrom1read	NA
Type1	1errorfrom2write/read	1errorfrom2reads	Write/Readerror
Type2	NA	2errorsfrom3reads/1write	Upset
Type3	2errorsfrom4write/read	3errorsfrom4reads/2writes	Snapback
Type4	3errorsfrom4write/read	4errorsfrom4reads/2writes	Stuckbit/Bigproblem

Table10:SRAM-Errortypesdefinitions

Theusedpatternswherecheckerboardandcomplementedcheckerboard,static0andstatic1.TheSRAM clockfrequency(selectablefromtheGUI)wassetto20MHz.

Mostlydynamic tests were performed. Few additional runs were performed in a static mode using the Hirex shutter system and one additional run was performed in the flash freeze mode.

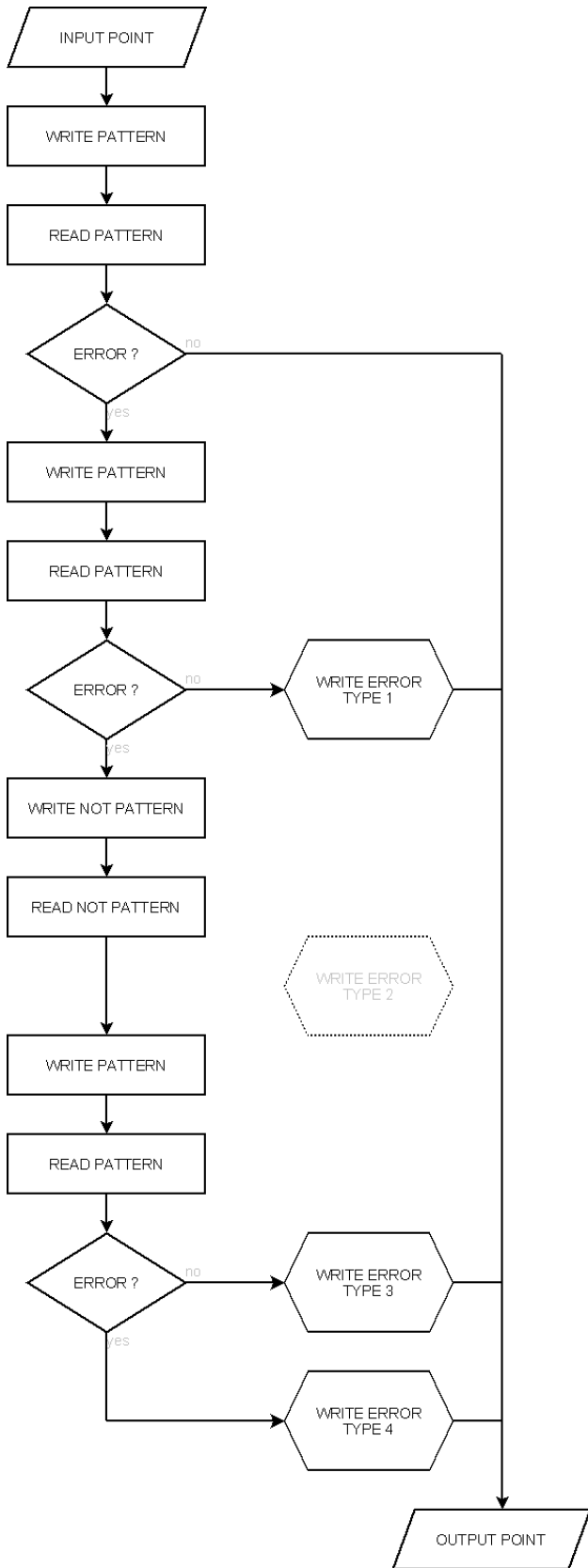


Figure20:SRAMFillAlgorithm

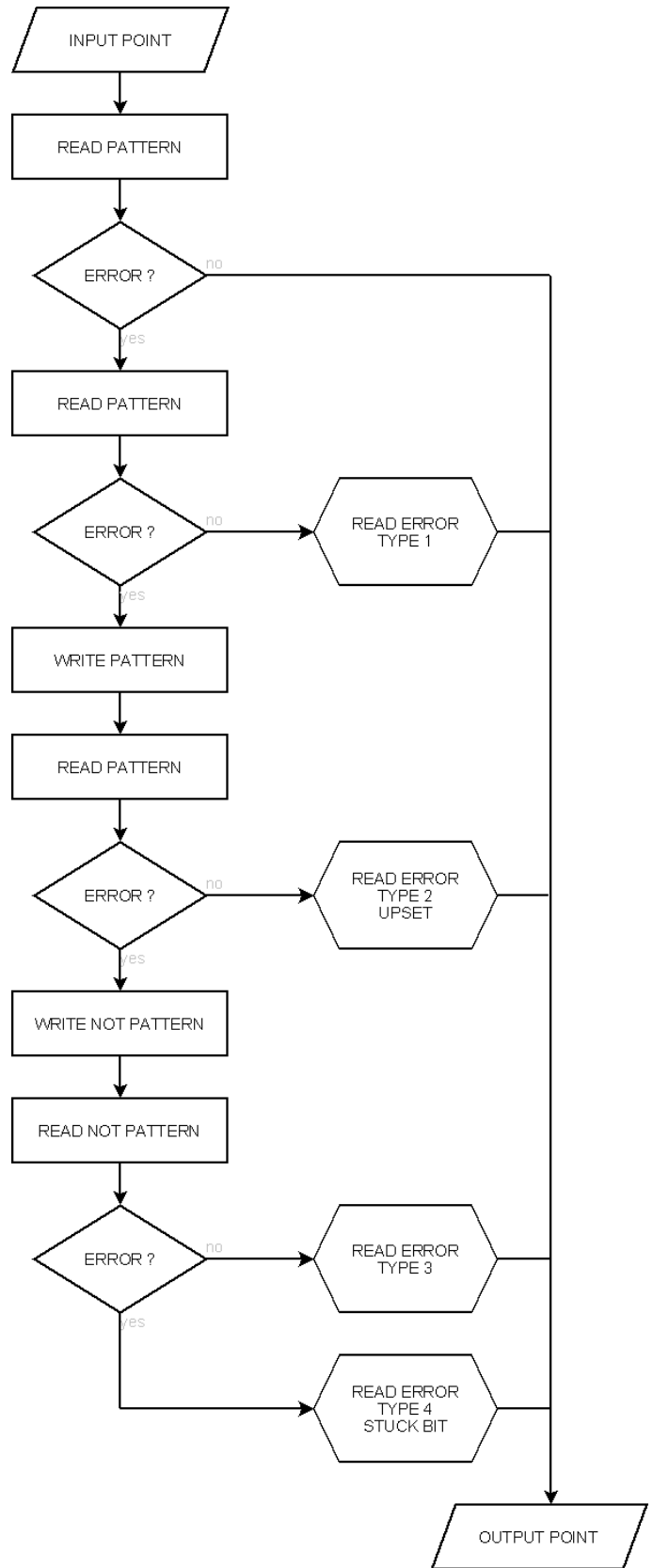


Figure21:SRAMCheckAlgorithm

8.4 **UFROM**

The TV1 uses 100% of the device's embedded UFROM memory of 128 words of 8 bits.

The UFROM algorithm detailed on the Figure 22 is based on 3 reads of each memory address sequentially. The memory address is increased to the next when the state of the current address is stated. The result of the memory content is estimated as the majority of the read results. By this way, 3 errors are defined as detailed on the Table 11:

Error type	Algorithm steps	Error source
No error	0 error from 2 reads	NA
Type 1	1 error from 3 reads	Reader error
Type 2	2 errors from 3 reads	Reader error Upset
Type 3	2 errors from 2 reads	Upset

Table 11: UFROM-Error types definitions

To fasten the test of the memory, the 3rd read is "cancelled" if the 2 previous results are similar.

For example, if 2 successive reads are realized without any error then the 3rd read is cancelled and the "No error" type is stated (reporting nothing), this increasing the speed of the test. The behavior is similar if 2 successive reads result in error cancelling the 3rd read, stating and reporting the error type 3.

The flash memory content was configured with checkerboard interleaved with checkerboard complemented patterns. The UFROM clock frequency (selectable from the GUI) was set to 10 MHz.

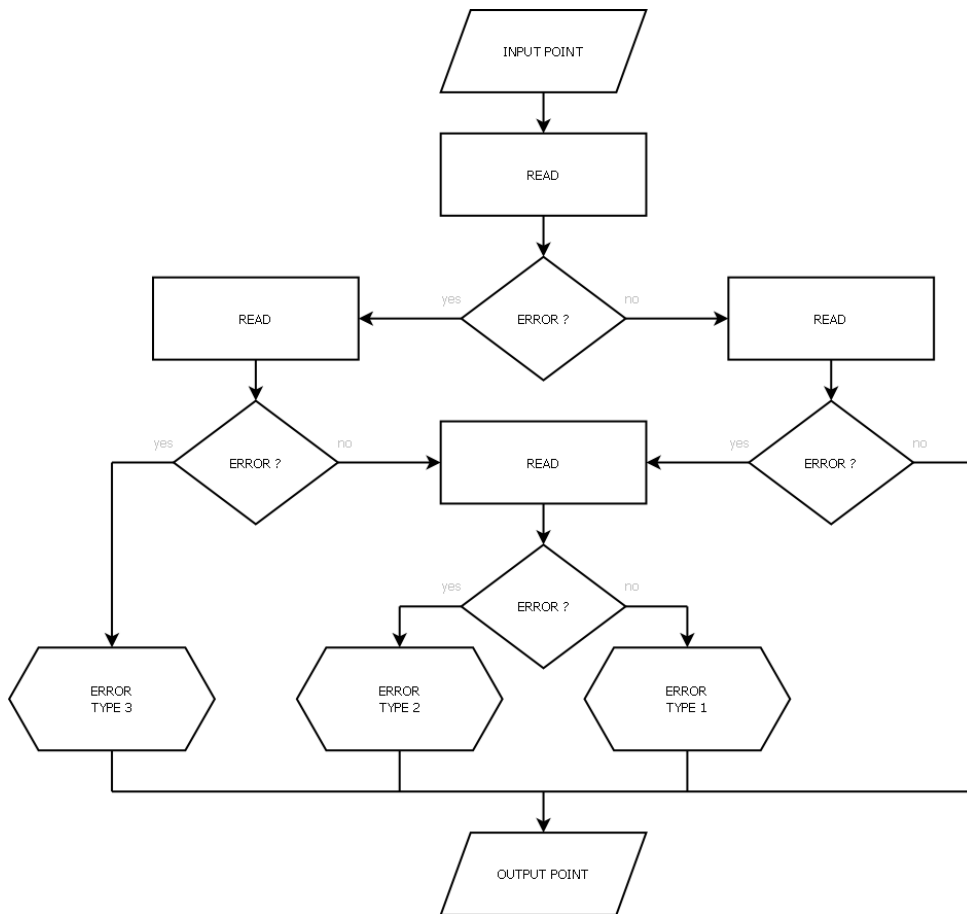


Figure 22: UFROM Check algorithm

8.5 CCC/PLL

On the TV1, one Clock Conditioning Circuit (CCC) with a Phase-Locked Loop (PLL) was configured in a static mode (single frequency) set on 200 MHz.

The SEE sensitivity of the CCC/PLL is evaluated first by interpreting clock error signature on the shift registers clocked by the CCC/PLL output. In the meantime the PLL lock signal is verified and recorded when toggling state.

The CCC/PLL input clock was the common shift register input clock. The PLL was verified functional with input clock frequency from 200 MHz (the nominal point) and down to lower than 100 MHz. The SEE sensitivity of the PLL was so characterized from 200 MHz down to 100 MHz (200 MHz being the nominal point).

8.6 Configuration Flash, charge pump and ISP

The configuration flash was tested by checking the functionality of the device during and after each exposition. Additional runs were performed while the device was running the configuration process to evaluate the SEE sensitivities of the configuration flash, charge pump and ISP. The standard configuration sequence is:

- ✓ Erase
- ✓ Program
- ✓ Verify

The erase, program and verify processes were run together and done at a time, exposed to the beam. The result of the entire configuration process was then stated by verifying the:

- ✓ Success of the operation (pass/fail)
- ✓ Design functionality
- ✓ Re-configurability of the device

The configuration process was run with ACTEL specific tools.

9 HEAVYION-TESTRESULTS

9.1 POWERSUPPLY

No SEL has been observed up to a LET of 55 MeV.cm²/mg(¹³¹Xe³⁵⁺), a cumulative fluence of 1E7 p/cm², a temperature up to 125 °C, a bias voltage of 1.65V for the core voltage and 3.6V for the input/output voltage.

The run N°159 from June 2010 campaign at RADEF was one test run performed in SEL tests condition. It was performed on the device sample SN5 configured with the TV1 exposed to Xenon ion, a total fluence of 5E6 p/cm² and a temperature of 125 °C. The chronograms of banks, PLL and core power supplies are plotted on following figures from Figure 23 to Figure 33 where no SEL appears.

It can be seen on those figures 3 plots versus time :

- ✓ The flux of the beam in black color.
- ✓ The voltage of the channel in blue color.
- ✓ The current of the channel in red color.

Remarks:

- i. The flux of the RUN159 shows 2 cuts attended to 2 stops of the beamline.
- ii. The second bank current chronogram shows large steps of current. This is due to the very short scale used (because consumption is very light on this bank). So small variations are largely spread into the full scale.
- iii. The PLLF was not used on the device but still powered.
- iv. The JTAG and charge pump voltage were kept at 0 V while tested in nominal mode (not configuring the device).
- v. The device was not tested with SEL test condition in configuration mode. So no SEL test condition was performed with the JTAG and charge pump power supplies on.

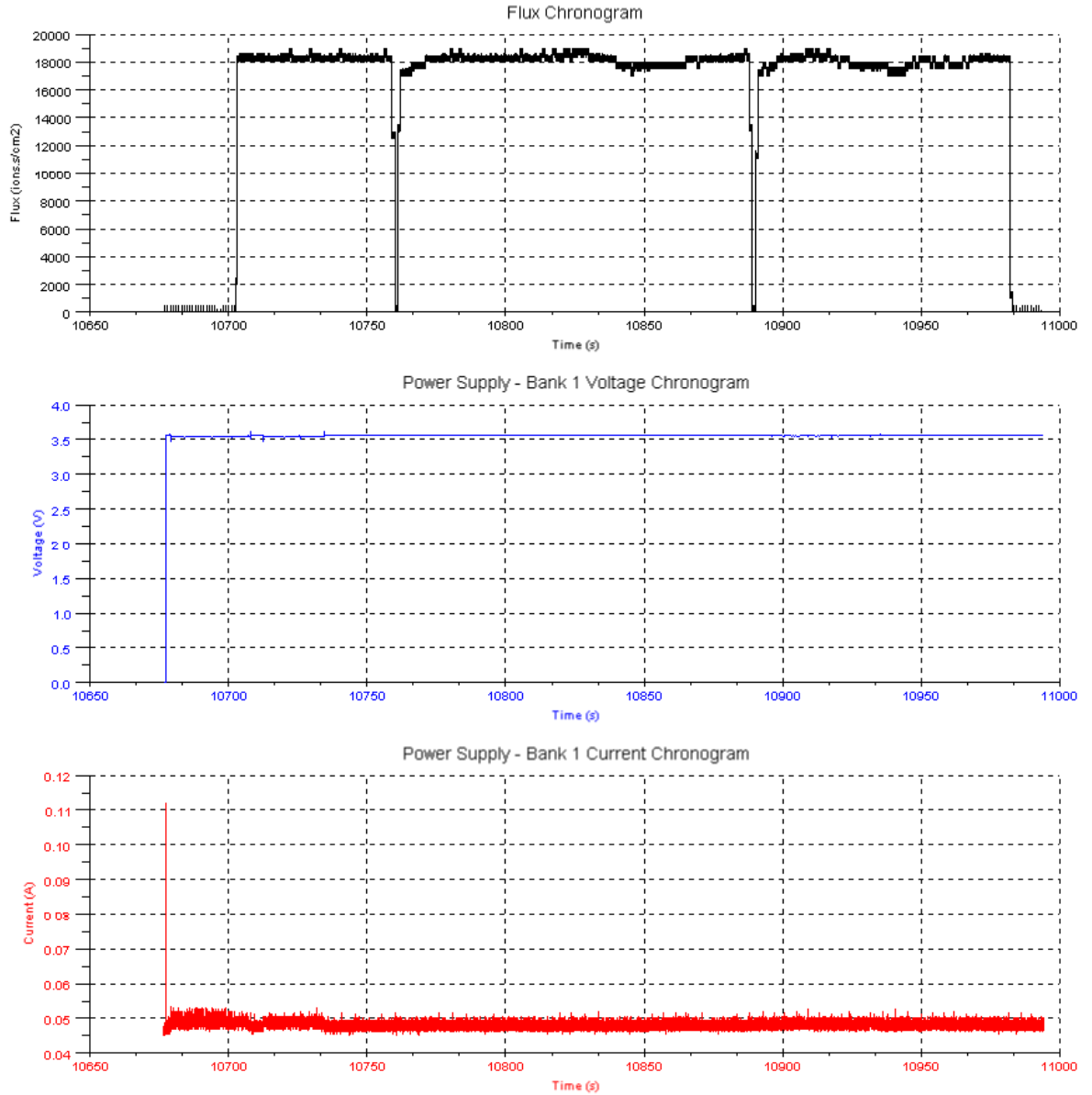


Figure23:RADEFJune2010-RUN159-Bank1power supply

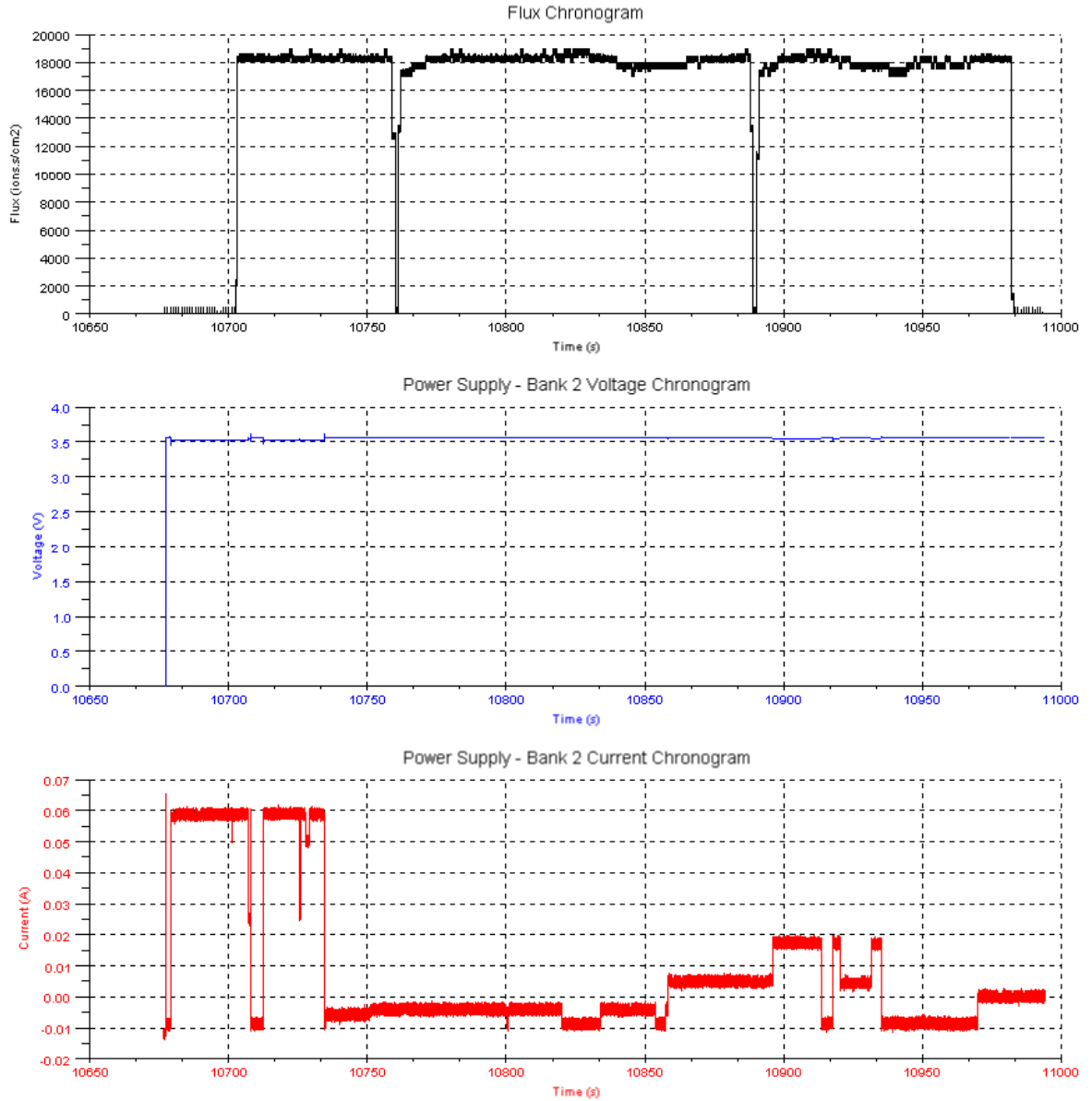


Figure24:RADEFJune2010-RUN159-Bank2power supply

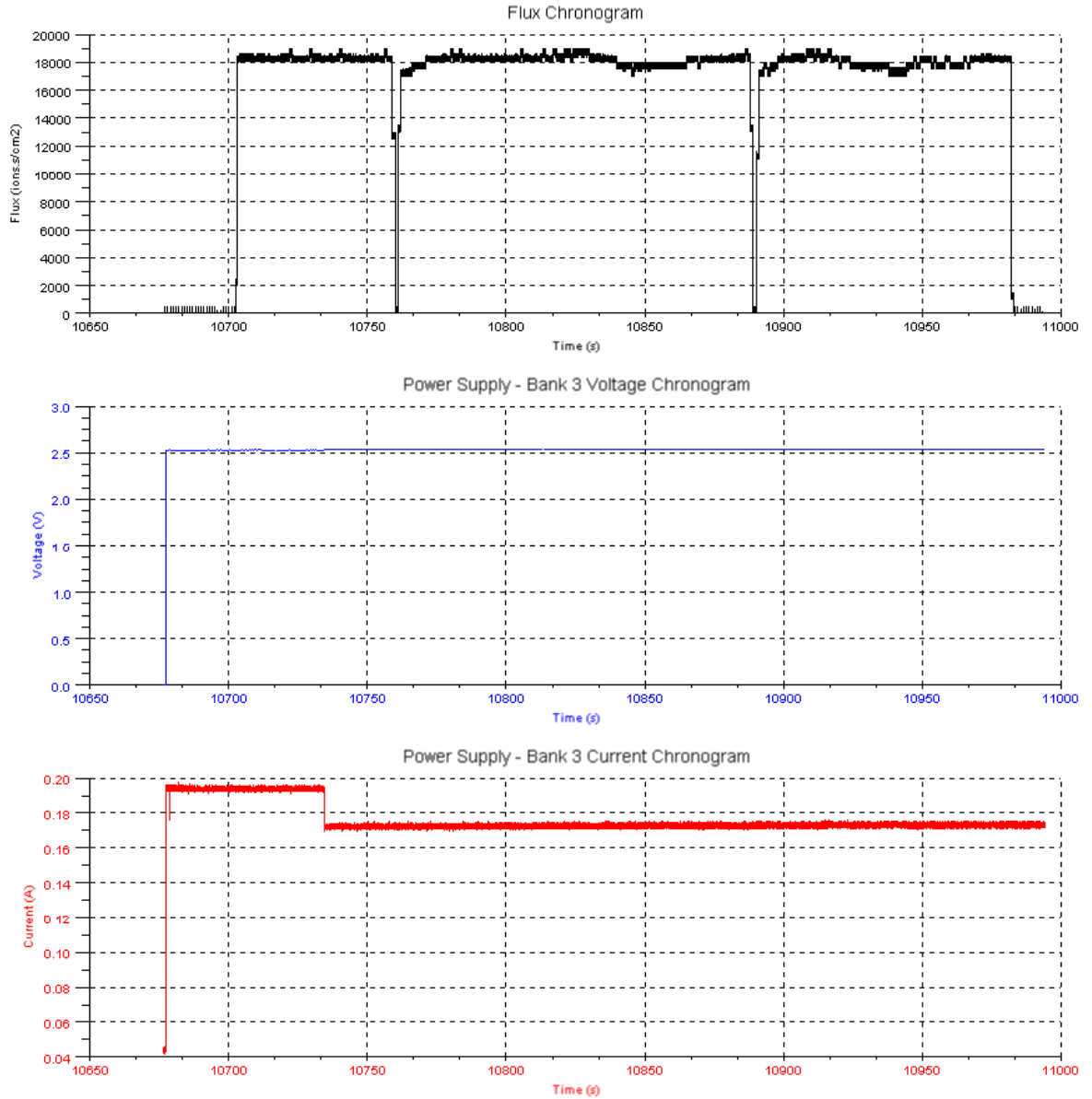


Figure25:RADEFJune2010-RUN159-Bank3power supply

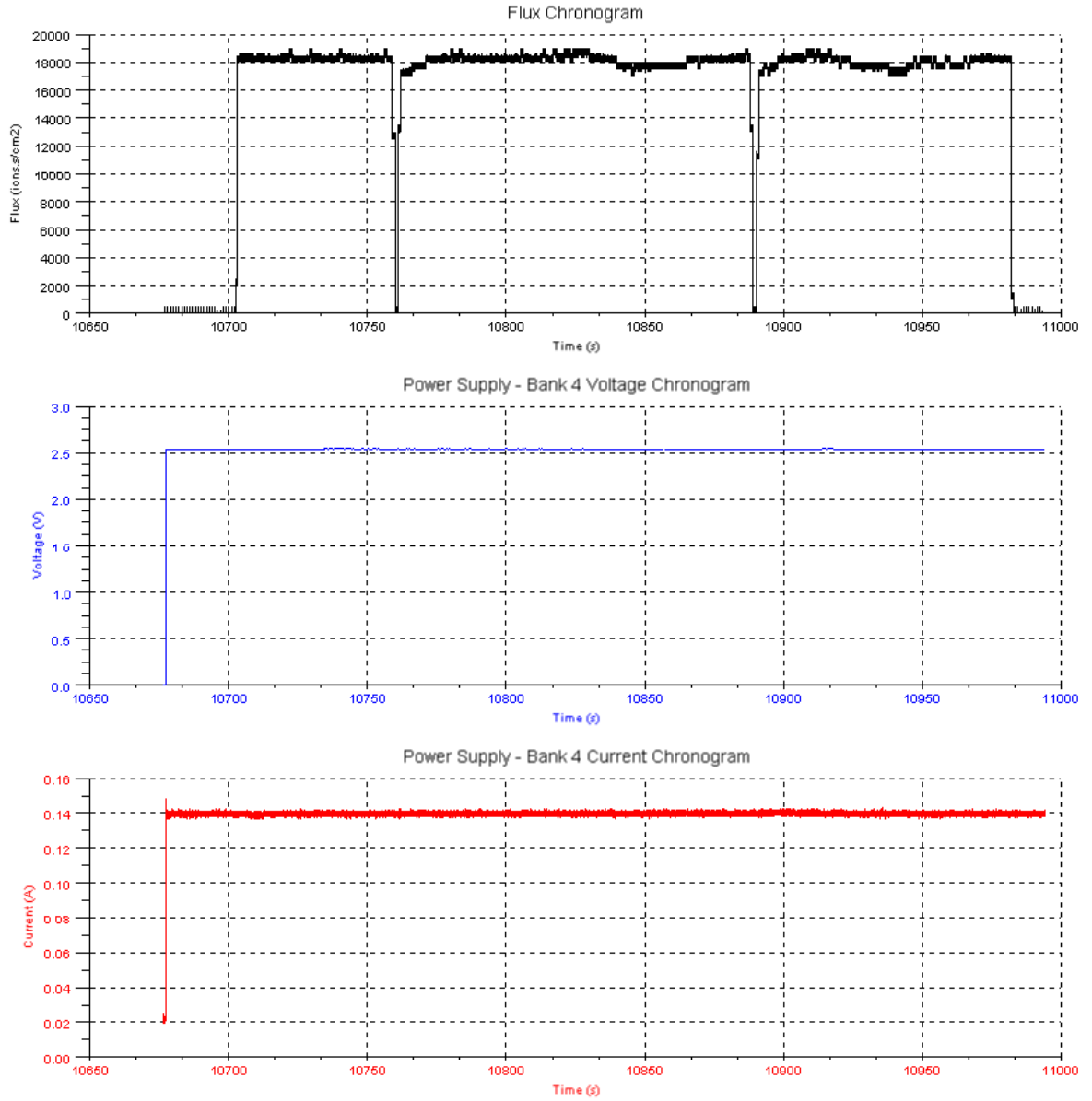


Figure26:RADEFJune2010-RUN159-Bank4power supply

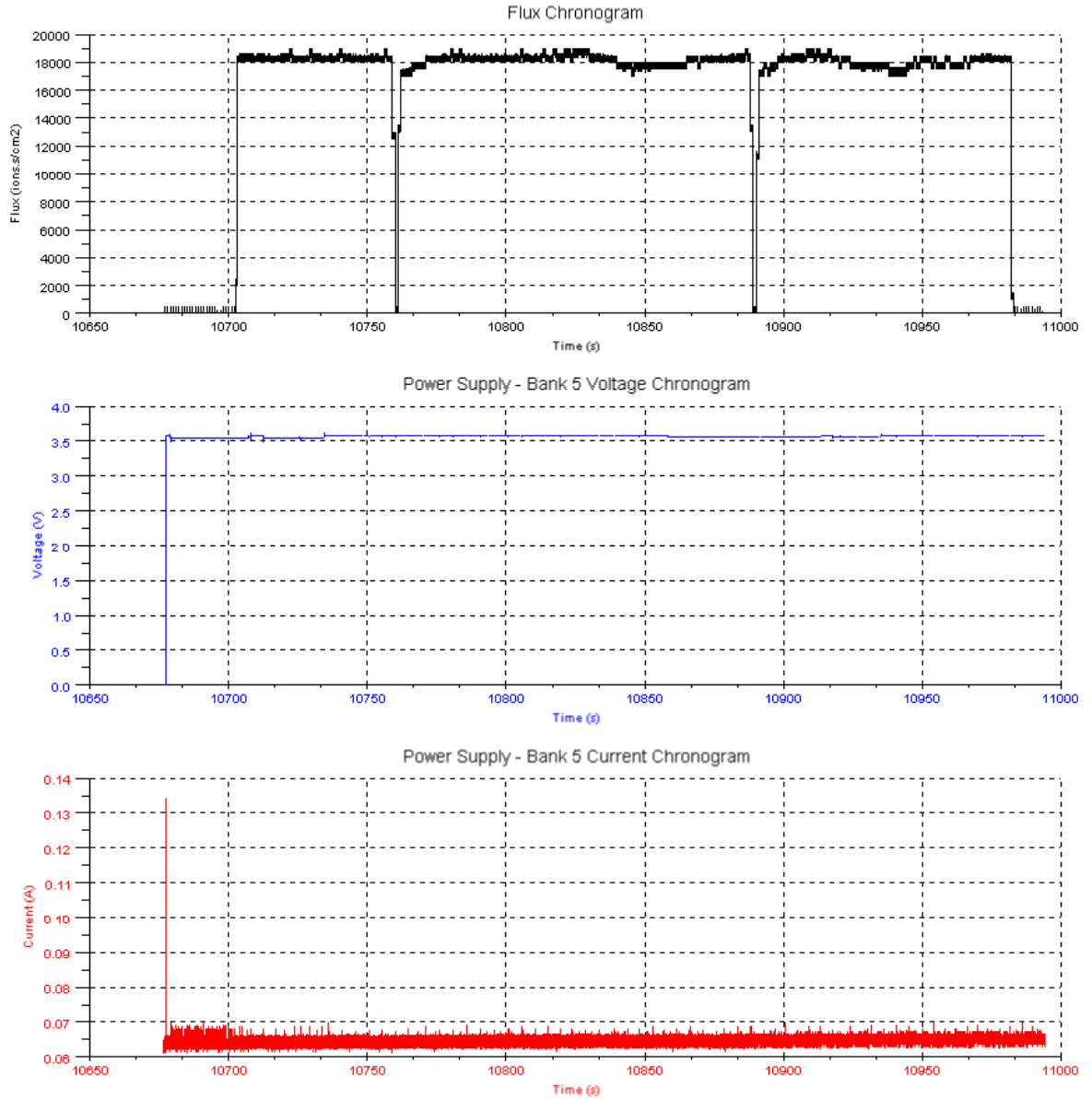


Figure27:RADEFJune2010-RUN159-Bank5power supply

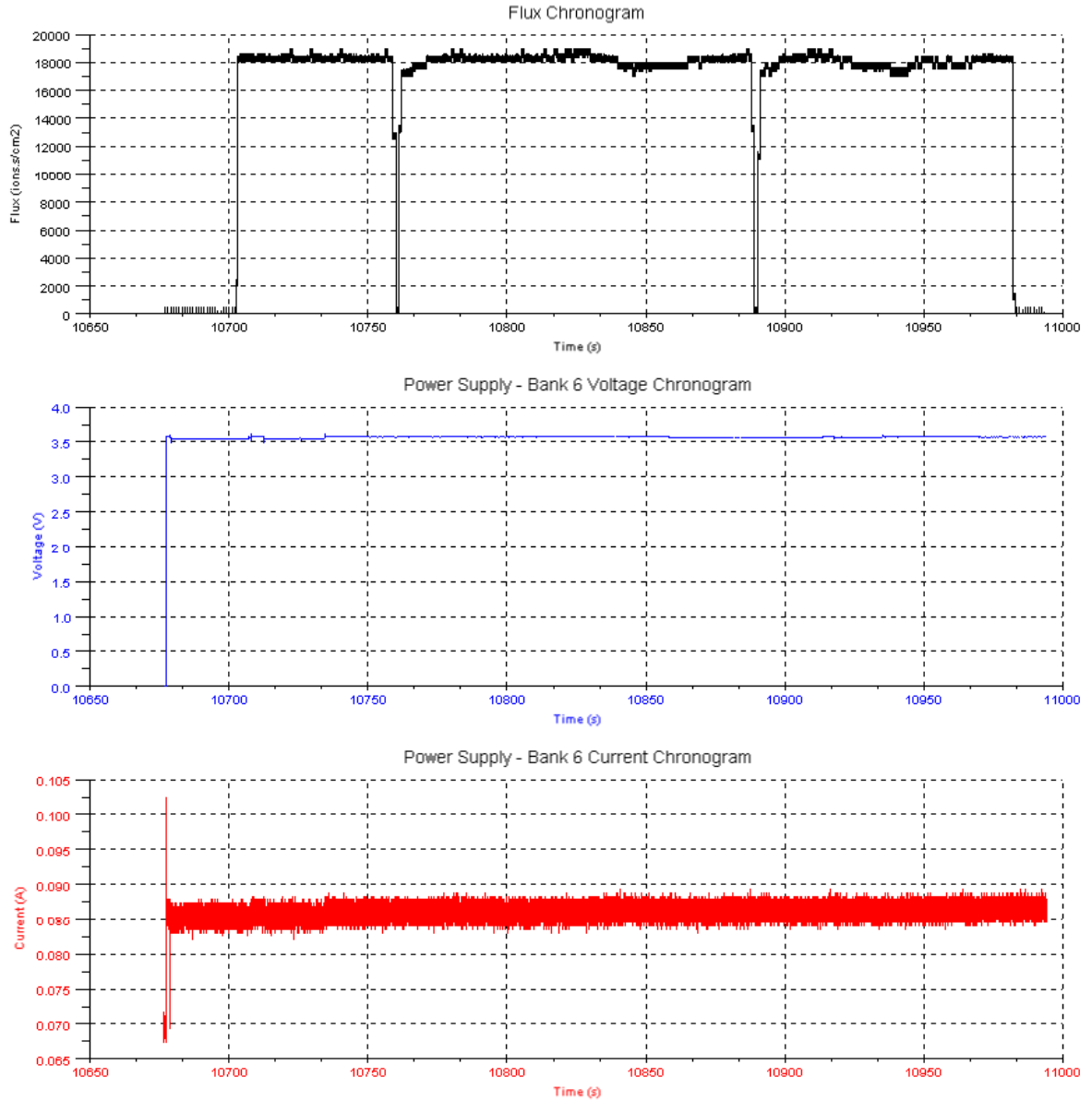


Figure28:RADEFJune2010-RUN159-Bank6power supply

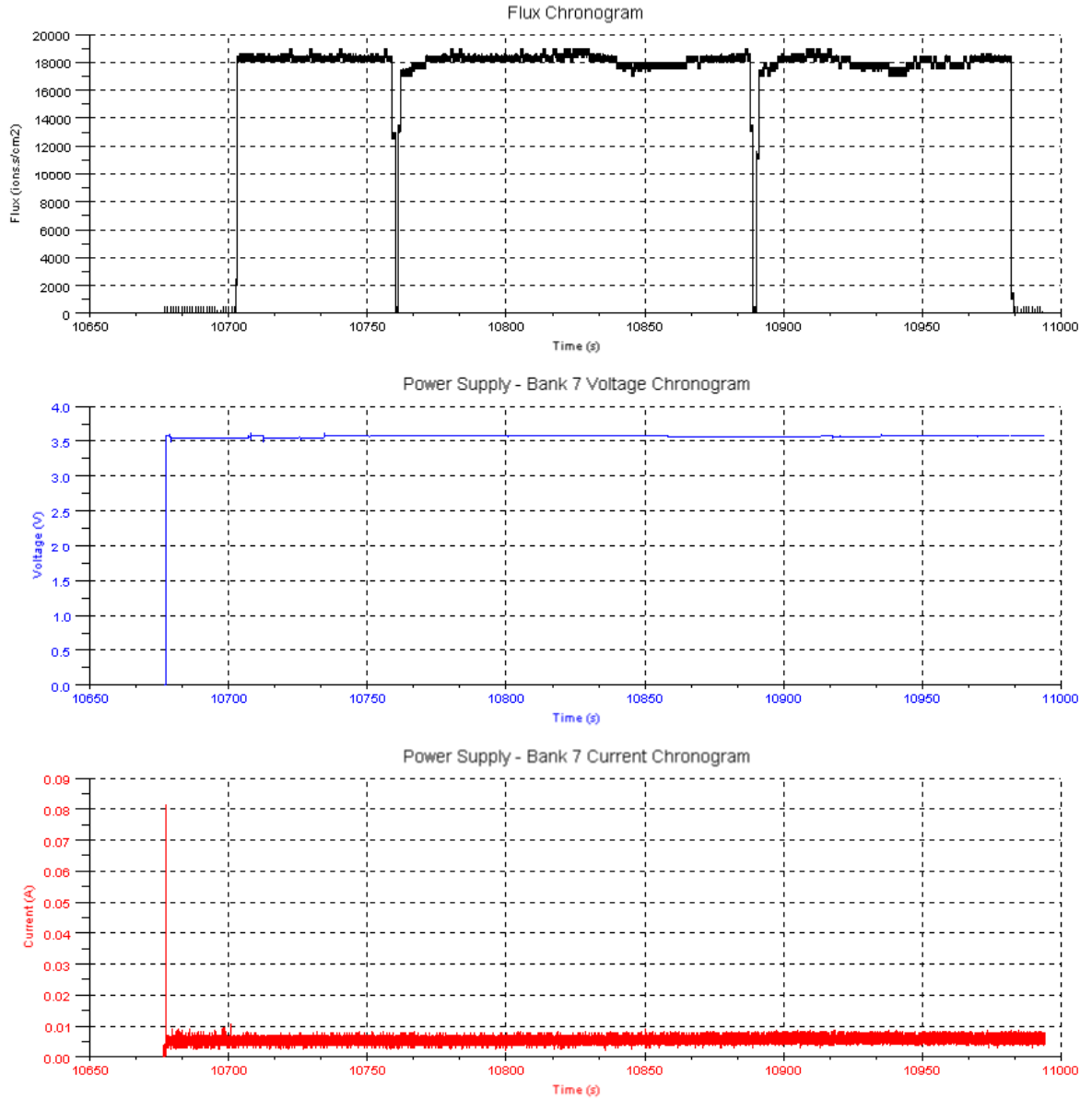


Figure29:RADEFJune2010-RUN159-Bank7power supply

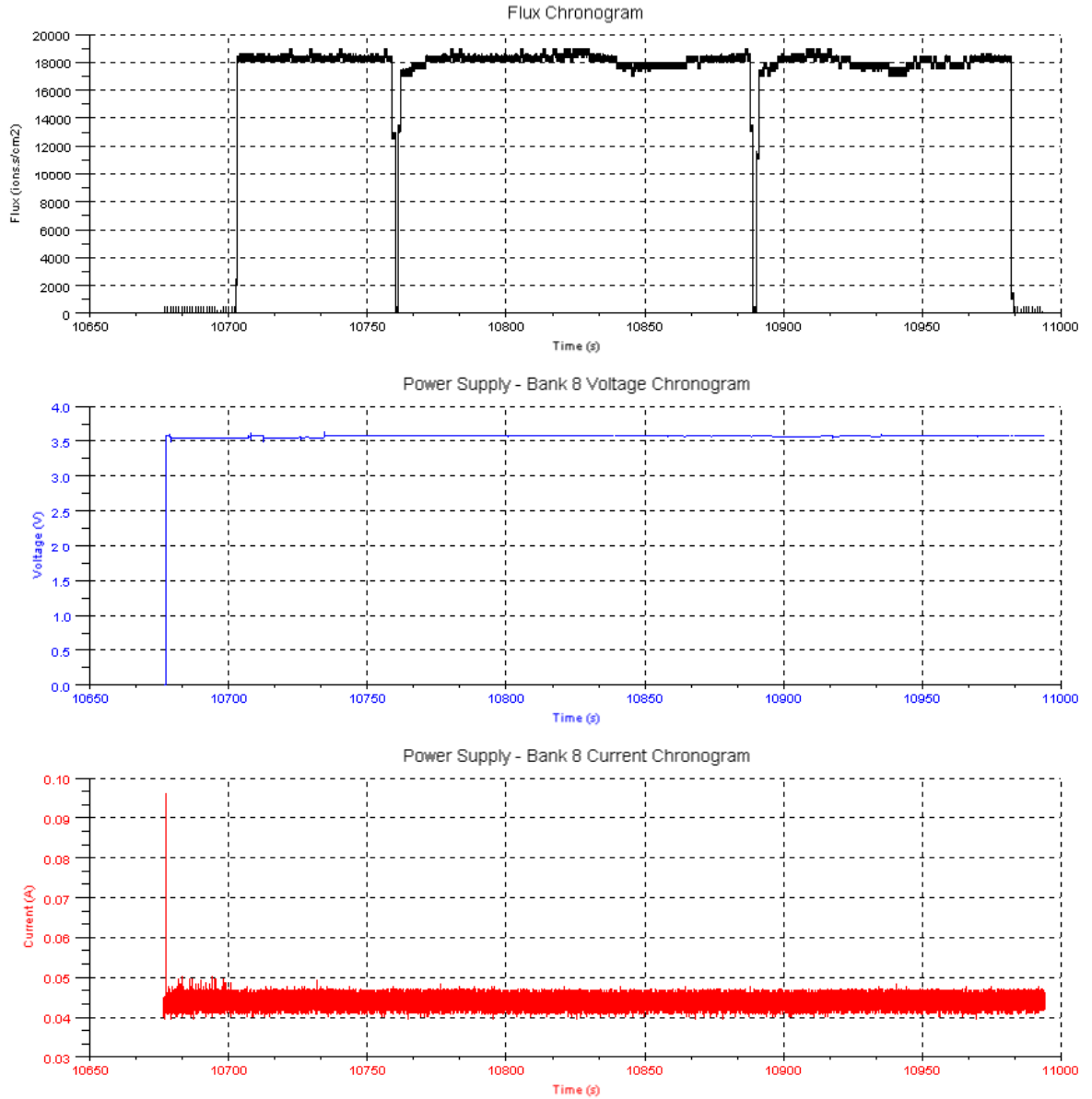


Figure30:RADEFJune2010-RUN159-Bank8power supply

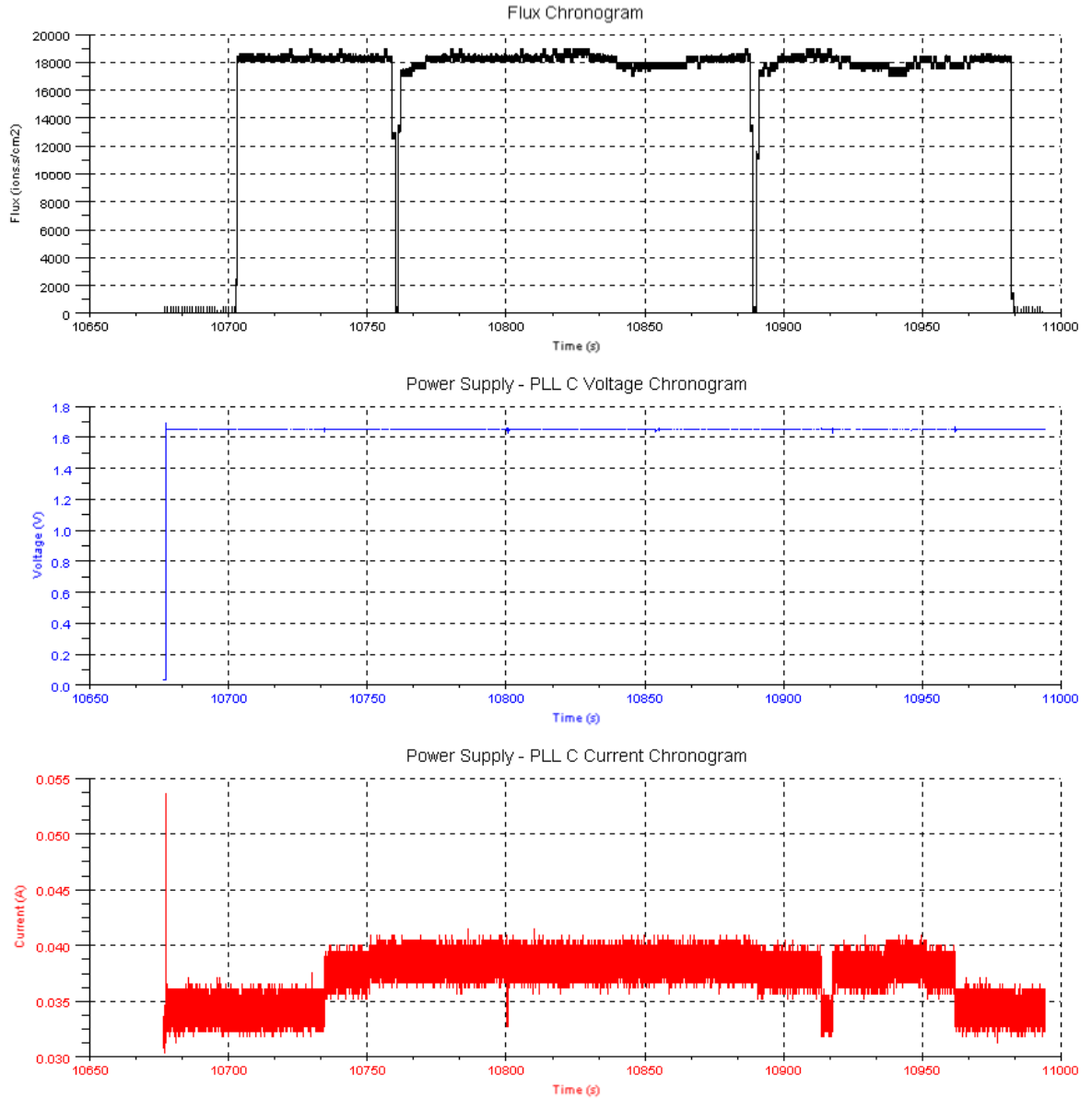


Figure31:RADEFJune2010-RUN159-PLLcpower supply

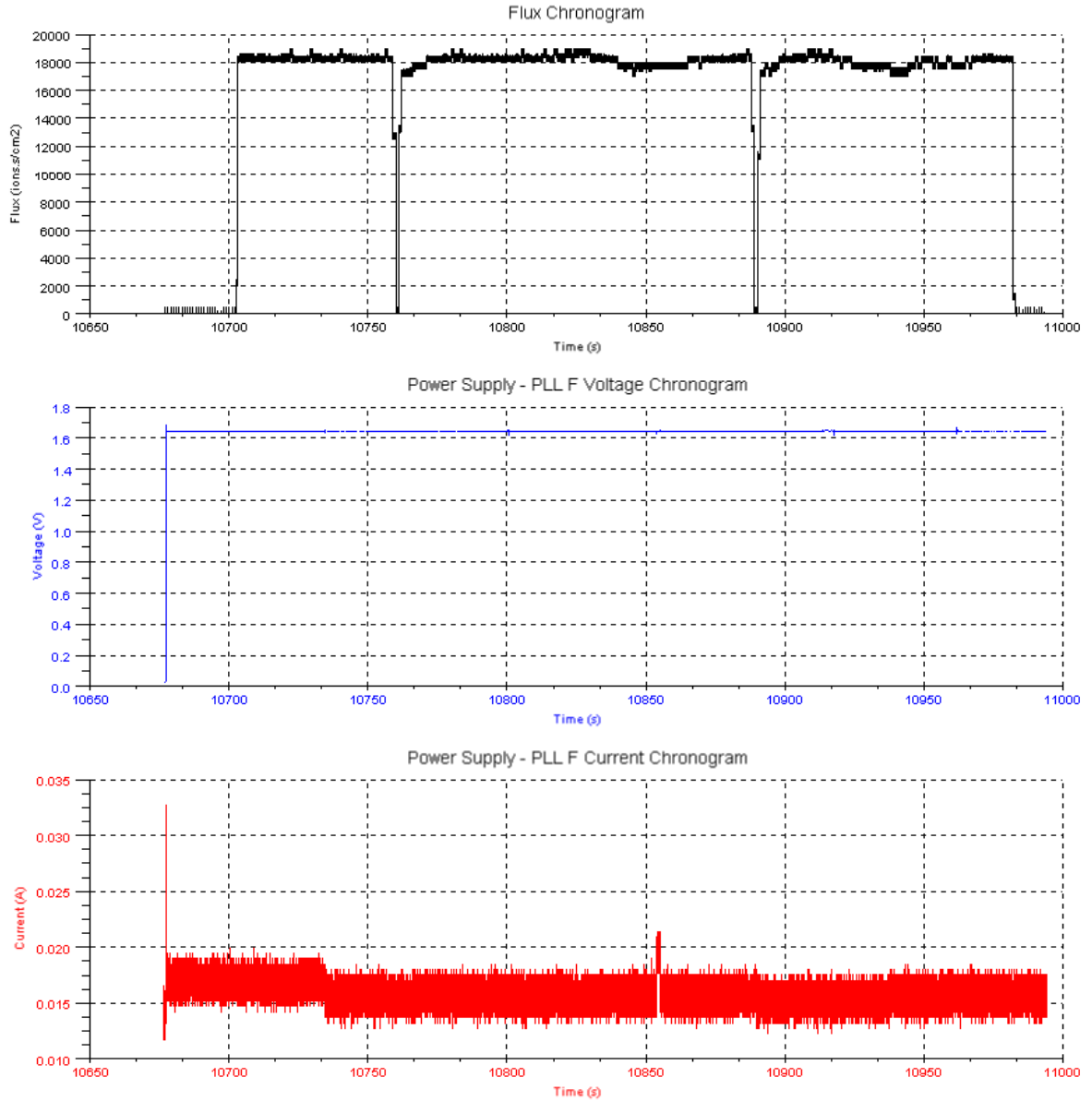


Figure32:RADEFJune2010-RUN159-PLLpower supply

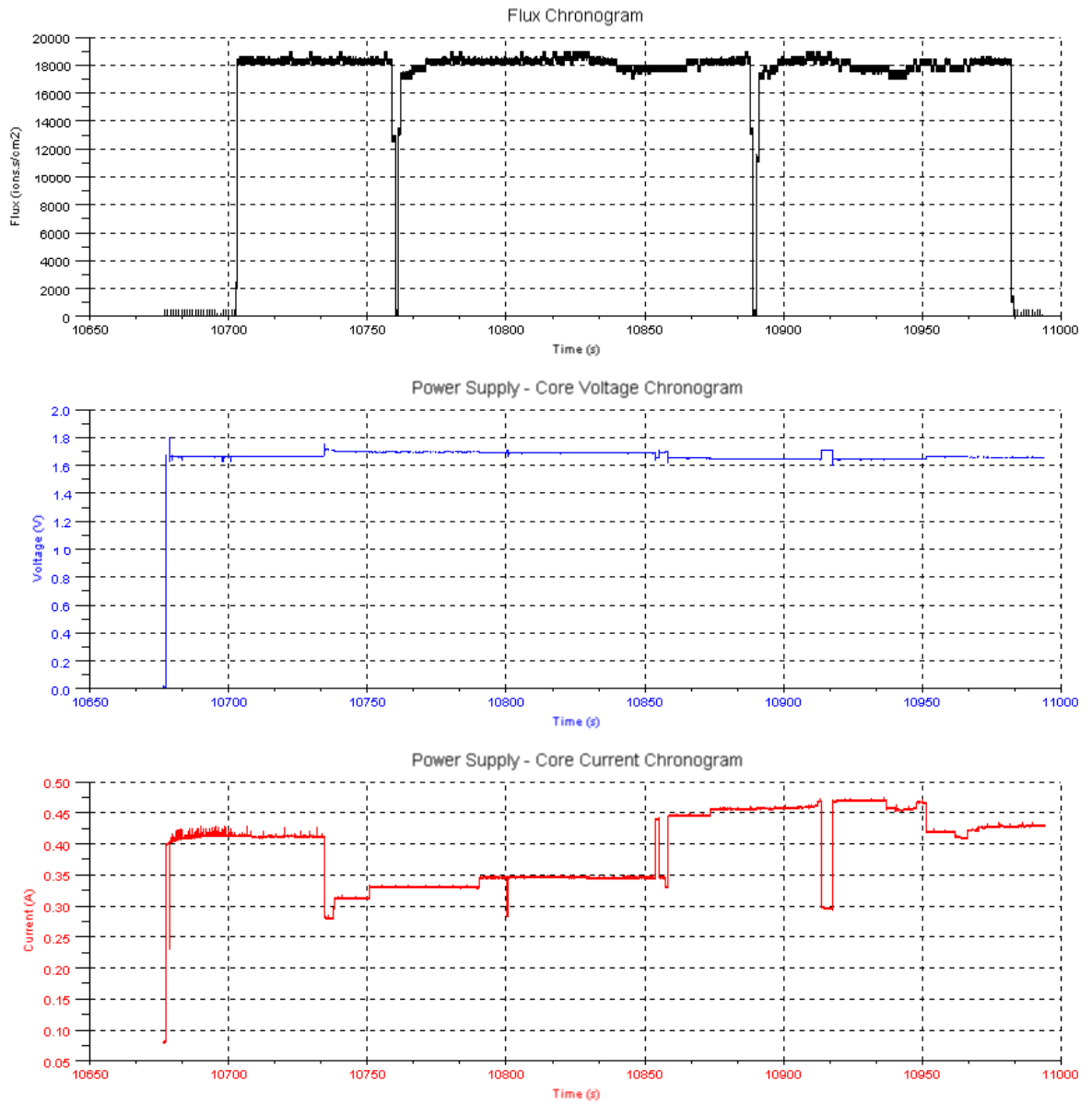


Figure33:RADEFJune2010-RUN159-Corepowers supply

9.2 TV1-SHIFTREGISTER

9.2.1 TV1-SR1

The Figure 34 displays the SEU cross-sectional area per bit of the TV1 SR1. This SEU cross-section per bit is characterized with an asymptotic cross-section (saturation cross-section) below 3E-7 cm² and a LET threshold around 1.8 MeV.cm²/mg.

On the plot, one Weibull fit curve was estimated from the points and added to the graph. The estimated Weibull fit curve is calculated from the following equation of the cumulative distribution function:

$$\sigma = CSsat(1 - e^{-(x/\lambda)^K})$$

With the following parameters values:

- K=1
- λ=80
- X₀=1.8 Mev.cm²/mg
- CSsat=3E-7 cm²

This same Weibull fit curve is then used as reference Weibull curve on all the SEU cross-sectional area plots.

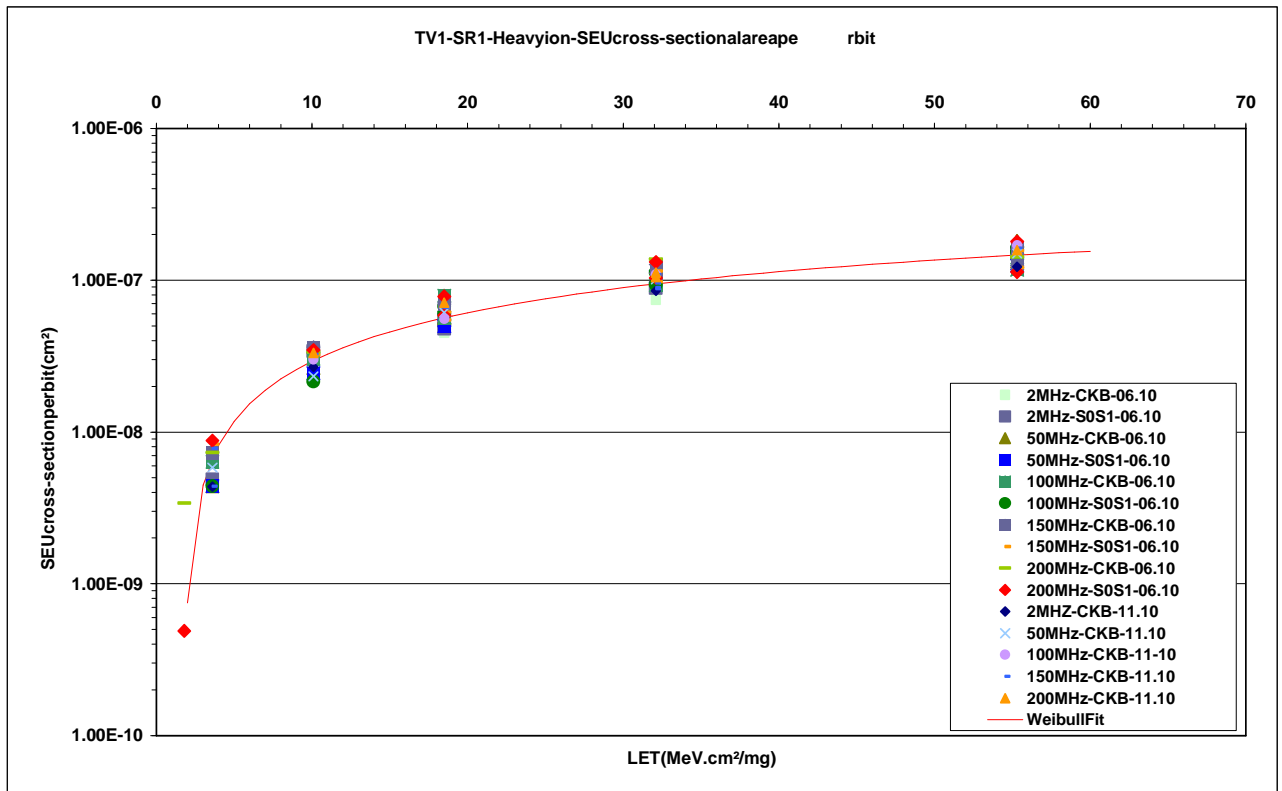


Figure 34: TV1-SR1-SEU cross-sectional area per bit

An extremely light influence of the working frequency can be seen on the SEU cross-section of the TV1 SR1 as highlighted on the Figure 35. In addition to the reference Weibull curve, 2 other Weibull curves were estimated and plotted: one fitting the 2MHz points and one fitting the 200MHz points. The 3 Weibull curves have the same parameters: K, X₀ and CSsat. The λ parameter is as in Table 12:

Weibullcurve	λ parametervalue
Weibullreference	80
Weibullfit-2MHz	100
Weibullfit-200MHz	60

Table12:TV1-SR1- λ parametervalues

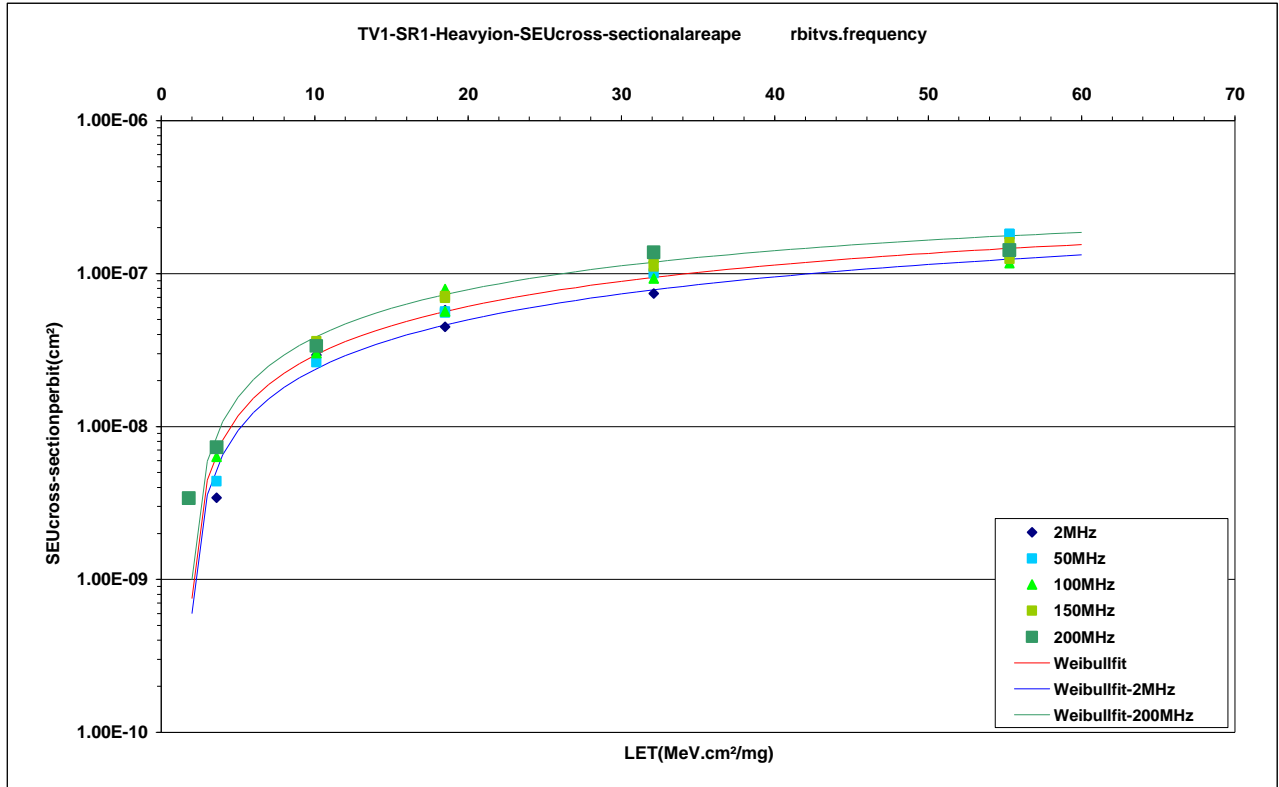


Figure35:TV1-SR1-SEUcross-sectionalareaper bitvs.frequency

The Figure 36 plots the distribution of the SEU. Most errors are SBU where almost 2/3 of those errors are due to clear transition (also called reset transition: transition from '1' to '0'). The other 1/3 is made of set transition (transition from '0' to '1'). Some MBUs can be counted as well. The MBUs are made of:

- ✓ A large majority of arbitrary numbers of consecutive reset bits which look like a local perturbation, more or less spread, on the global reset signal.
- ✓ Few 2 consecutive bits toggled: most probably due to 2 adjacent registers impacted by the same ion hit.
- ✓ Mixes of errors

This same SEU distribution plot is used as a reference for all the other SEU distribution graphs.

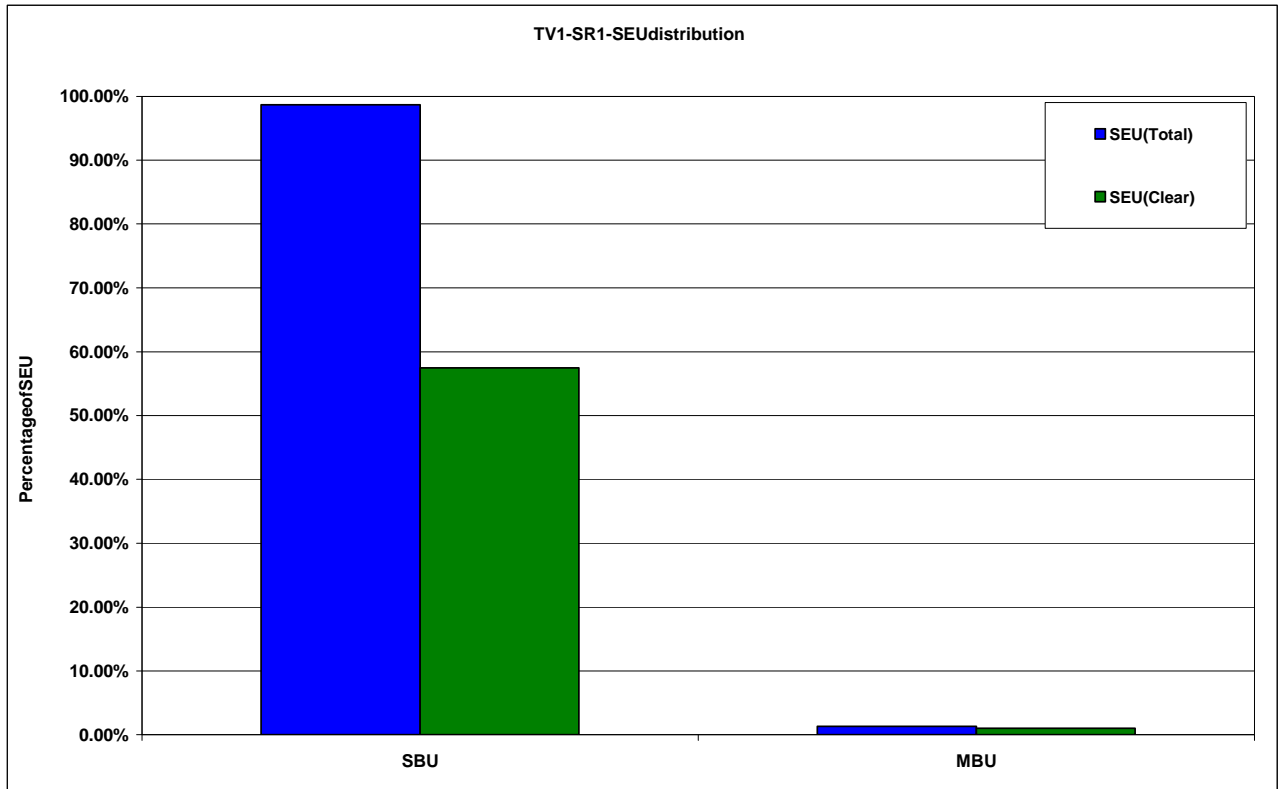


Figure36:TV1-SR1-SEUdistribution

9.2.2 TV1-SR2

TheTV1SR2channelimplementedcombinationalcells ontheglobalenablesignalpath.

TheSEUcross-sectionalareaperbitofthischanne isplottedontheFigure37.Itischaracterized withan asymptoticcross-section(saturationcross-section) below $3E-7$ cm²perbitandaLETthresholdaround 1.8 MeV.cm²/mg.Nodifferencebetweenthischanneland thereferenceisvisibleontheplotofthecross-s action: thereferenceWeibullcurvefitswellthemeasured pointsofthischannel.

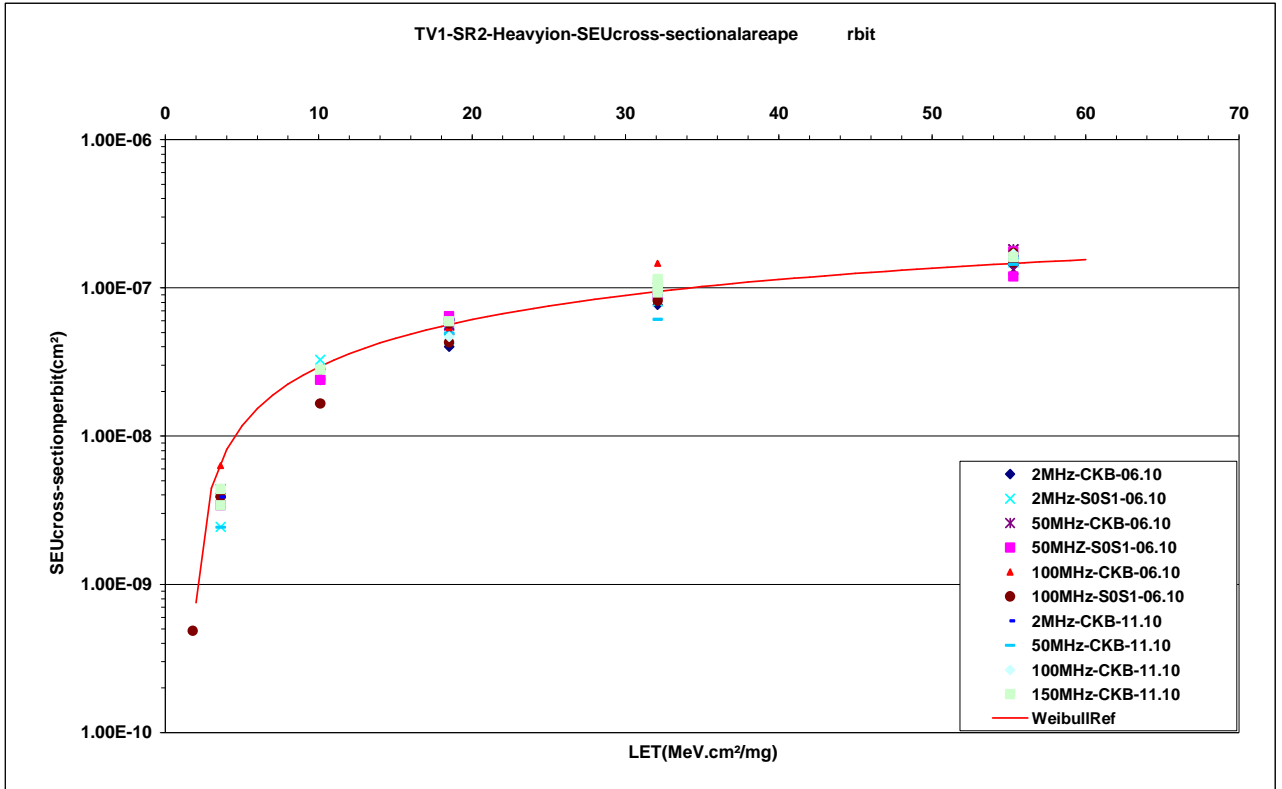


Figure37:TV1-SR2-SEUcross-sectionalareaper bit

The frequency does not appear to influence the SEU cross-section or so lightly that it is not clearly visible. The SEU cross-sectional area per bit vs. the frequency is visible on the Figure 38.

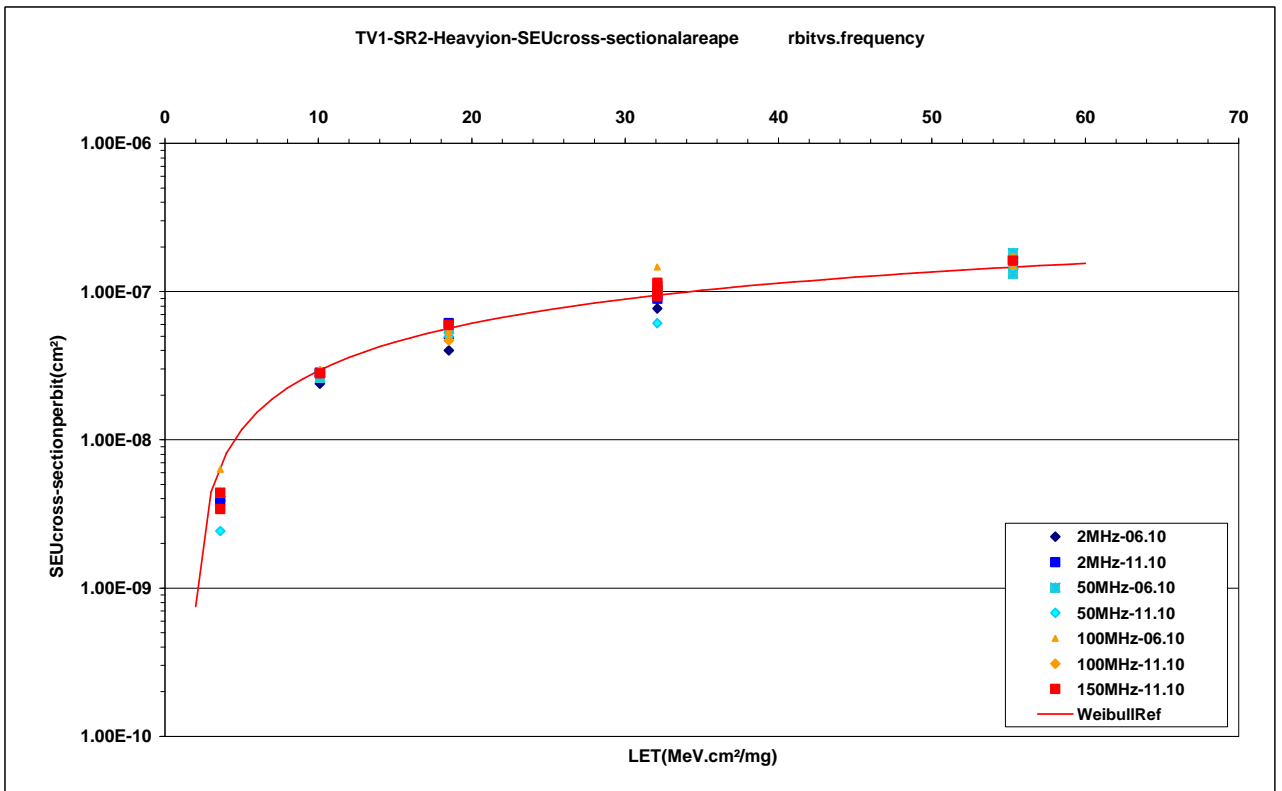


Figure38:TV1-SR2-SEUCross-sectionalareaper bitvs.frequency

The Figure39 plots the SEU distribution. Like the reference channel, most errors are SBUs with more than half of those due to clear transition. MBUs percent ages and signatures are like the reference channel. However another signature of MBU appears. This signature shows an un-shifted quartet caused by an SET on the local enables signal caught at the active edge of the clock: data are held from shifting. Very few SETs on the enables signal were caught that way.

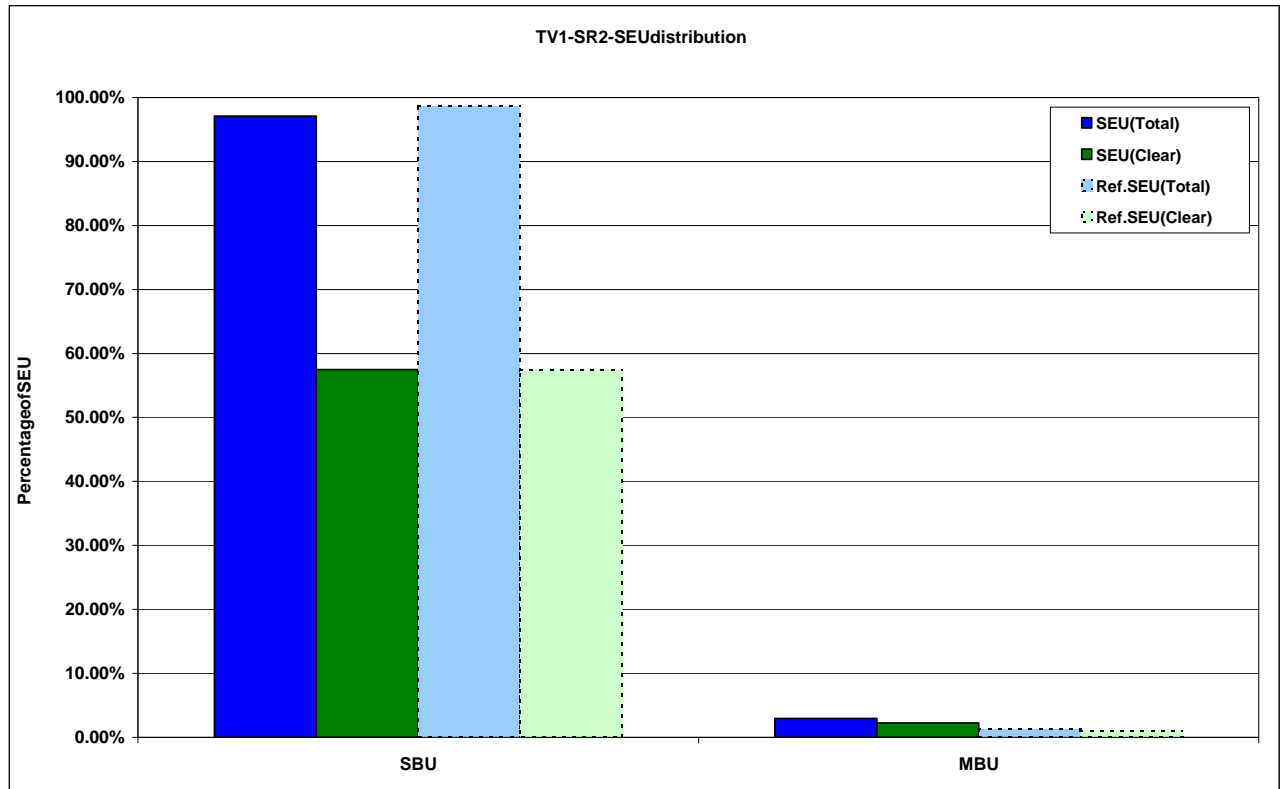


Figure39: TV1-SR2-SEU distribution

9.2.3 TV1-SR3

The TV1 SR3 channel implemented combinational cells on the global resets signal path.

The SEU cross-sectional area per bit of this channel is plotted on the Figure 40. It is characterized with an asymptotic cross-section (saturation cross-section) below 1E-6 cm² per bit and a LET threshold around 1.8 MeV.cm²/mg. This SEU cross-section is higher than the reference also added to the plot. A Weibull curve was estimated from the points and added to the graph. The TV1 SR3 Weibull fit curve has the following parameters:

- K=1
- λ=200
- Xo=1.8 MeV.cm²/mg
- CSsat=1E-6 cm²

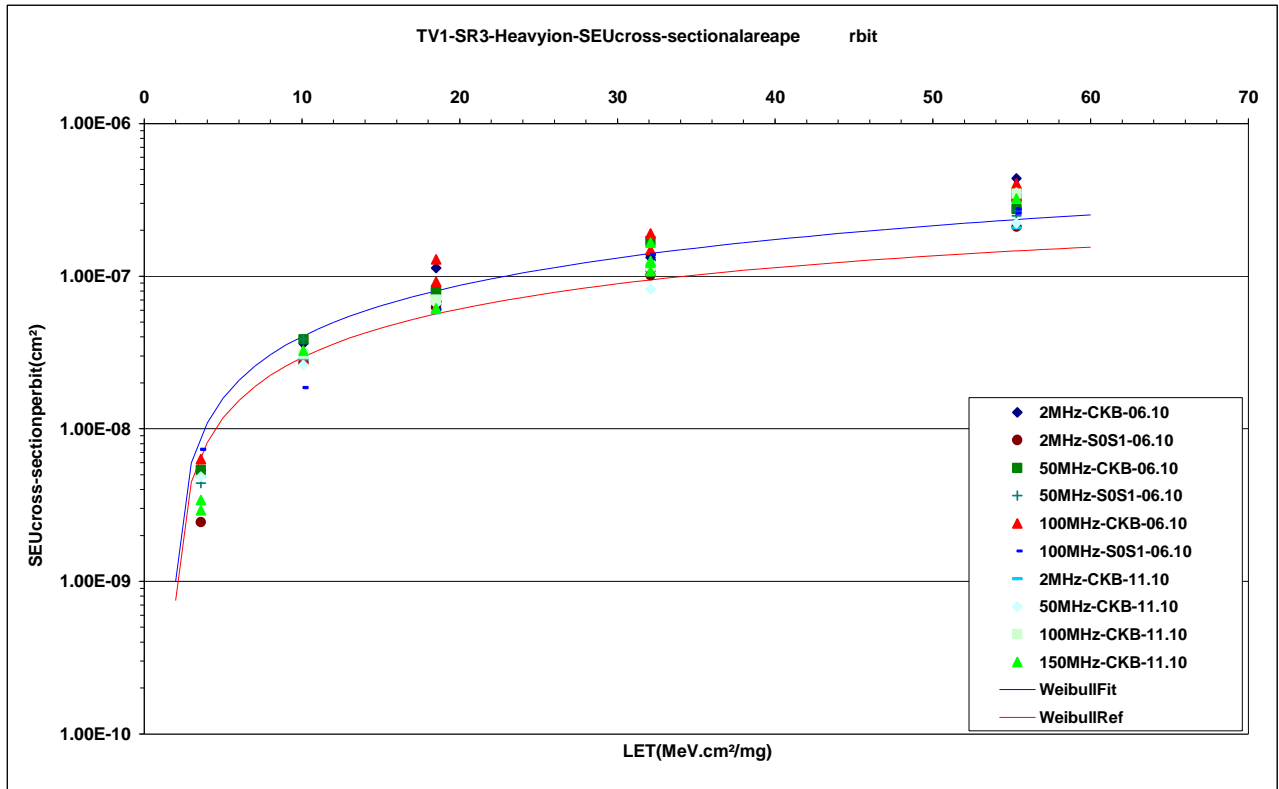


Figure40:TV1-SR3-SEUcross-sectionalareaper bit

Because the reset signal is an asynchronous signal level for a time longer or equal to the asynchronous is cleared. As a consequence SEU and SET on the global register.

each time its value steps into the bounces of the clear minimum pulse width ($T_{wclr} \approx 0.3ns$), the global (or local) reset signal longer than T_{wclr} clear

the register the

The Figure 41 plots the SEU distribution. Almost 80% of SEUs are SBUs and 70% of those are due to clear the reference channel and almost all of the MBUs are

are

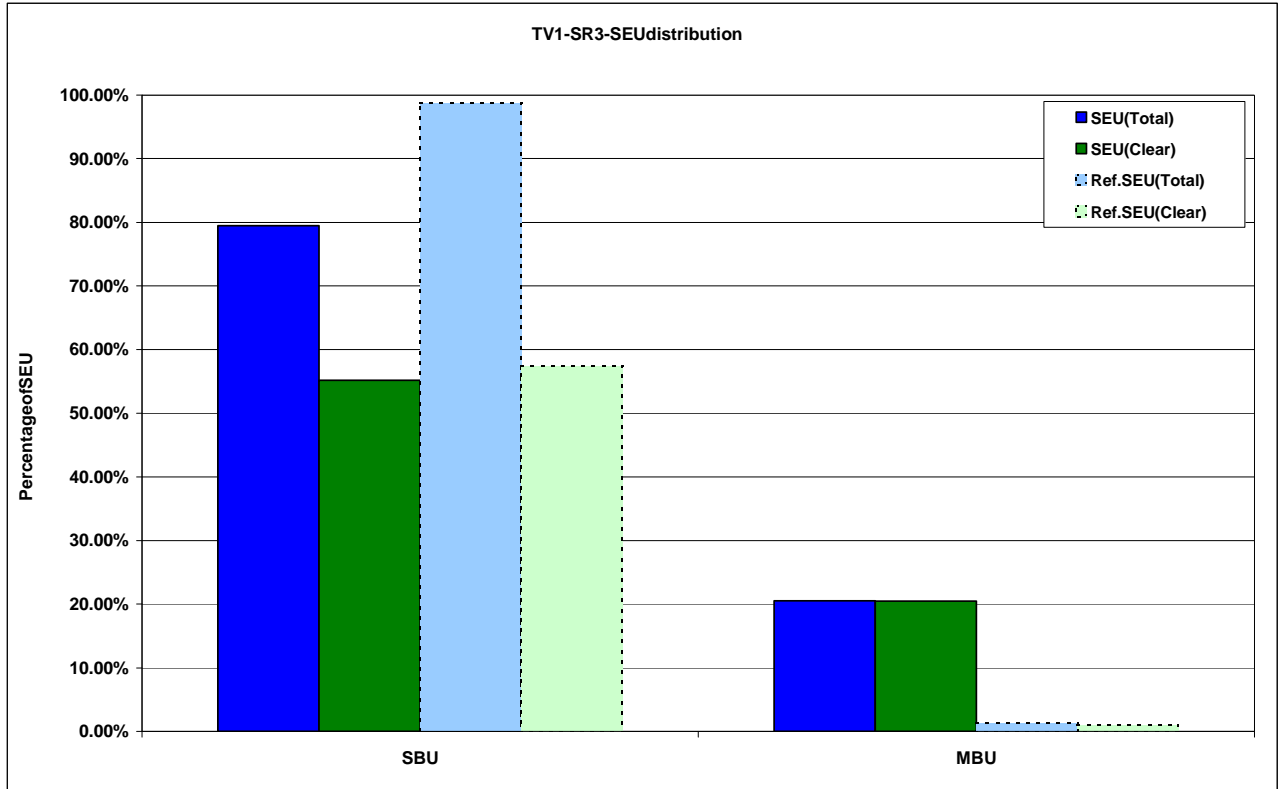


Figure41:TV1-SR3-SEUdistribution

9.2.4 TV1-SR4

TheTV1SR4channelimplementedcombinationalcells in-betweeneachregister.

TheSEUcross-sectionalareaperbitisequivalent tothereferencechannelascomparedontheFigure 42.It ischaracterizedwithanasymptoticcross-section(saturationcross-section)below3E-7cm²perbitan daLET thresholdaround1.8MeV.cm²/mg.

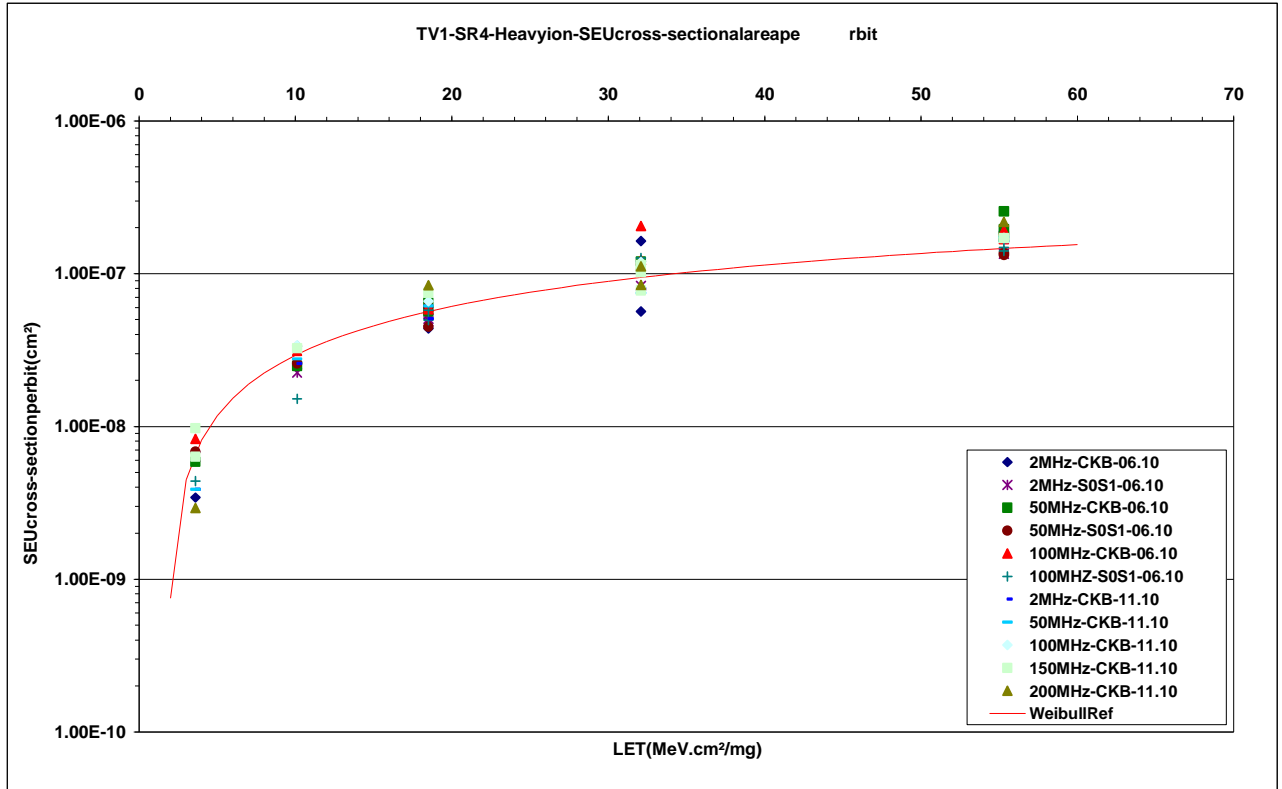


Figure42:TV1-SR4-SEUcross-sectionalareaper bit

The influence of the frequency plotted on the Figure 43 is not highly visible on the SEU cross-section. The three reference Weibull curves of the reference channel were also added to the plot for comparison purpose.

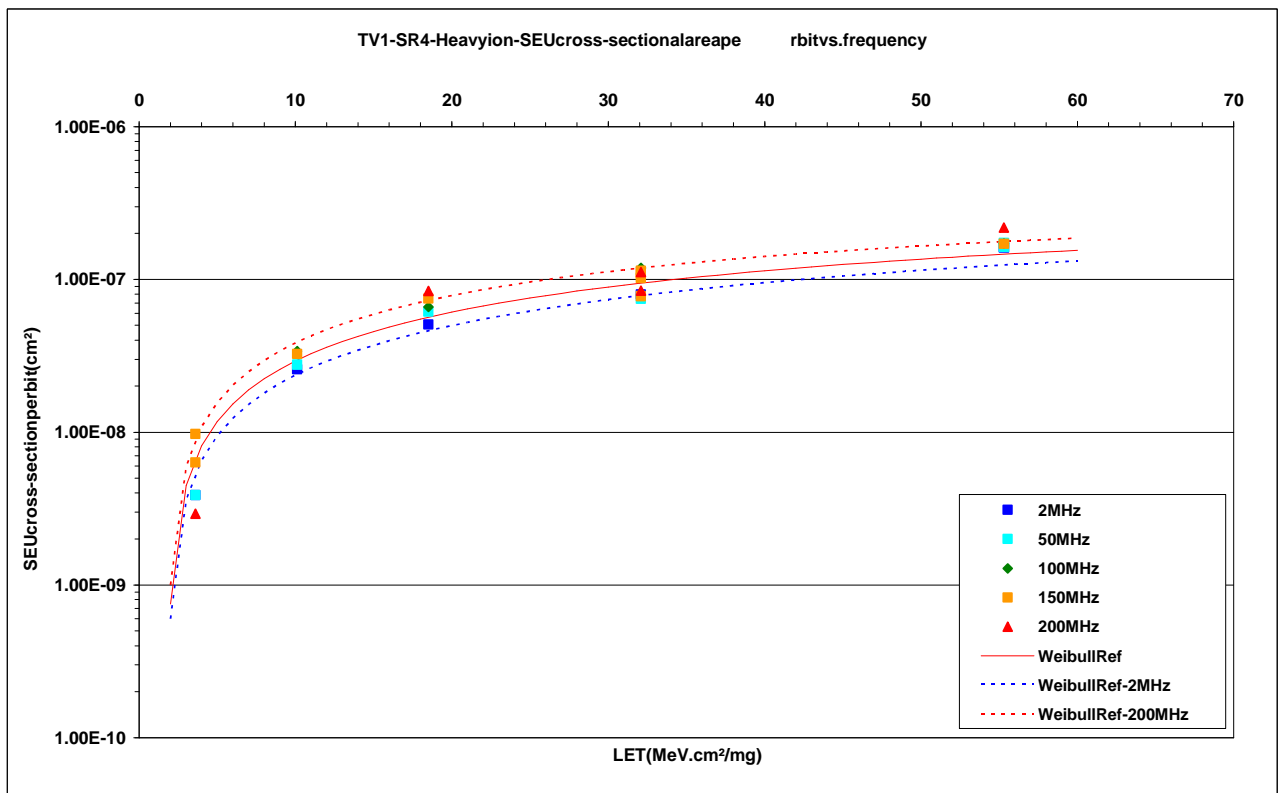


Figure43:TV1-SR4-SEUcross-sectionalareaper bitvs.frequency

The Figure 44 plots the SEU distribution. Like the reference channel, most SEUs are SBUs and 2/3 of those are due to clear transition. Comparing SEU cross-section and signatures, this channel is very similar to the reference one.

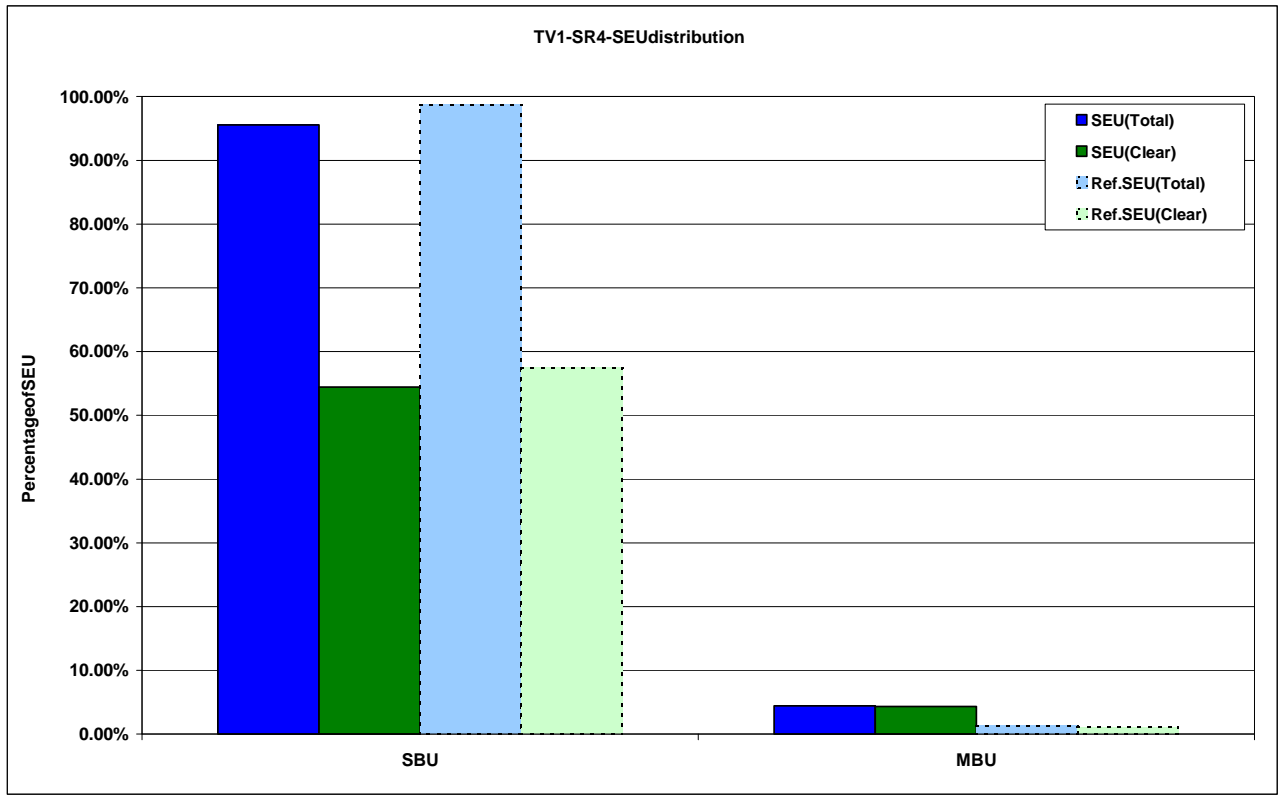


Figure 44: TV1-SR4-SEU distribution

9.2.5 TV1-SR5,6,7 and 8

The TV1 SR5, 6, 7 and 8 channels implemented Double Data Rate (DDR) registers at the input/output stages.

The SEU cross-section area per bit of those channels is very similar to the reference channel as it can be seen on the Figure 45. It is characterized with an asymptotic cross-section (saturation cross-section) below $3E-7 \text{ cm}^2/\text{per bit}$ and a LET threshold around $1.8 \text{ MeV} \cdot \text{cm}^2/\text{mg}$.

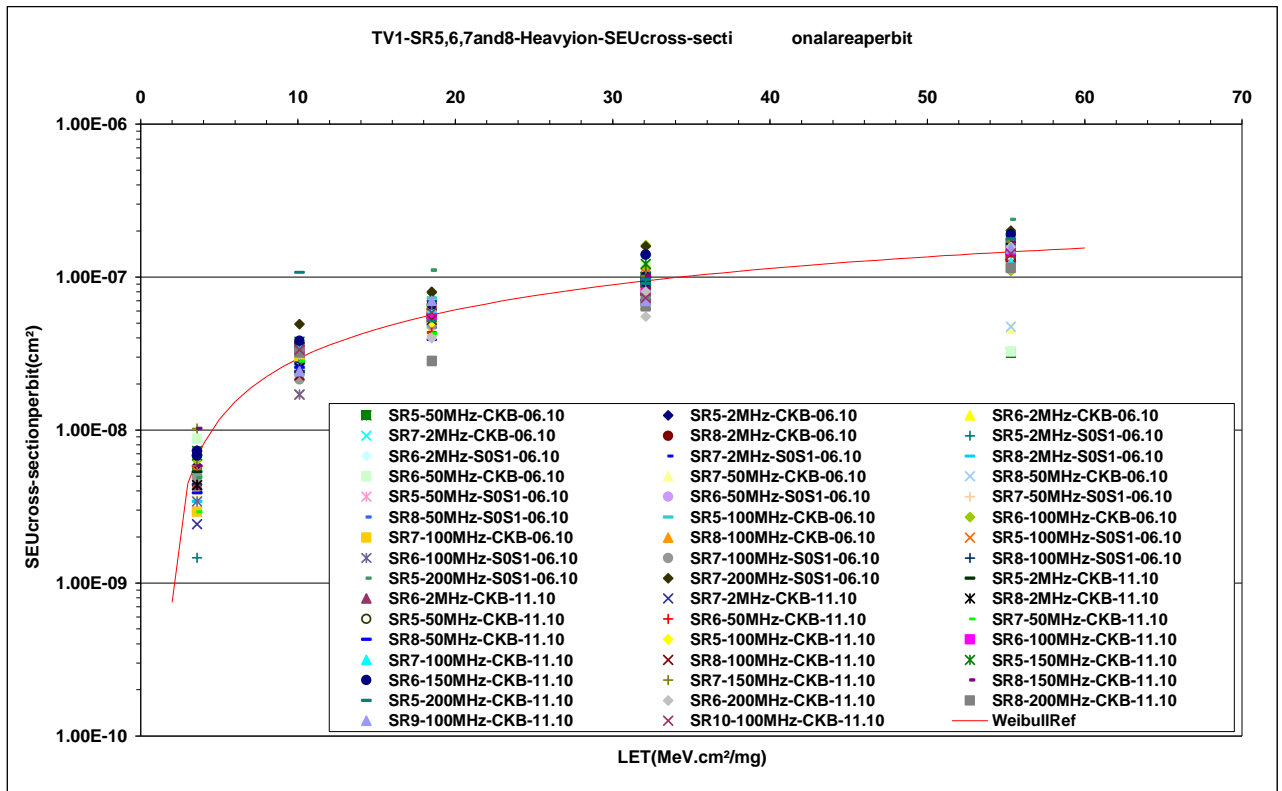


Figure45:TV1-SR5,6,7and8-SEUcross-section per bit

The Figure46 plots the SEU distribution. Like the reference channel, most SEUs are SBUs with more than the half of those due to clear transition. MBU sig

natures are very similar to the reference channel.

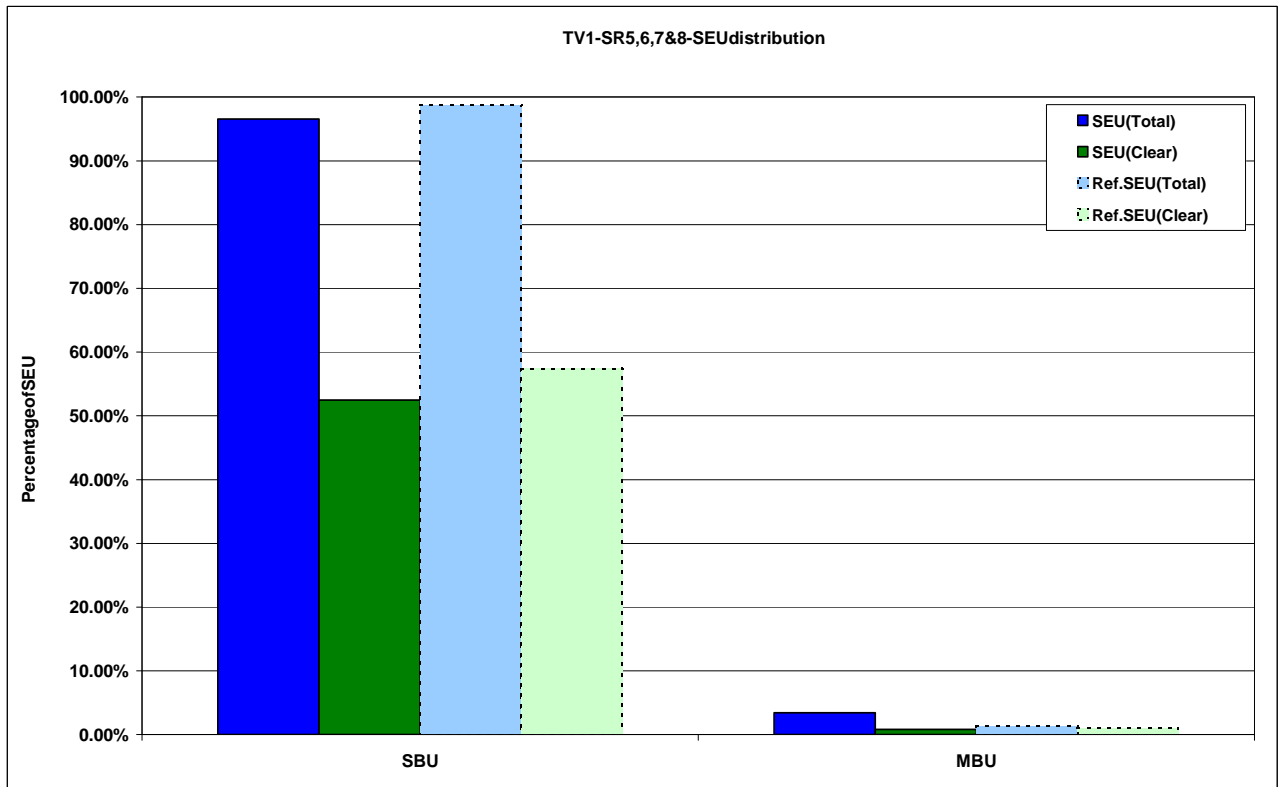


Figure46:TV1-SR5,6,7and8-SEUdistribution

9.2.6 TV1-SR9and10

TheTV1SR9and10channelsimplementedLVDSbuffer sattheinput/outputstages.

TheSEUcross-sectionalareaperbitisverysimila rtothereferencechannel.ItisplottedontheFi gure47.It ischaracterizedwithanasymptoticcross-section(saturationcross-section)below $3E-7\text{cm}^2\text{perbit}$ daLET thresholdaround $1.8\text{MeV}\cdot\text{cm}^2/\text{mg}$.

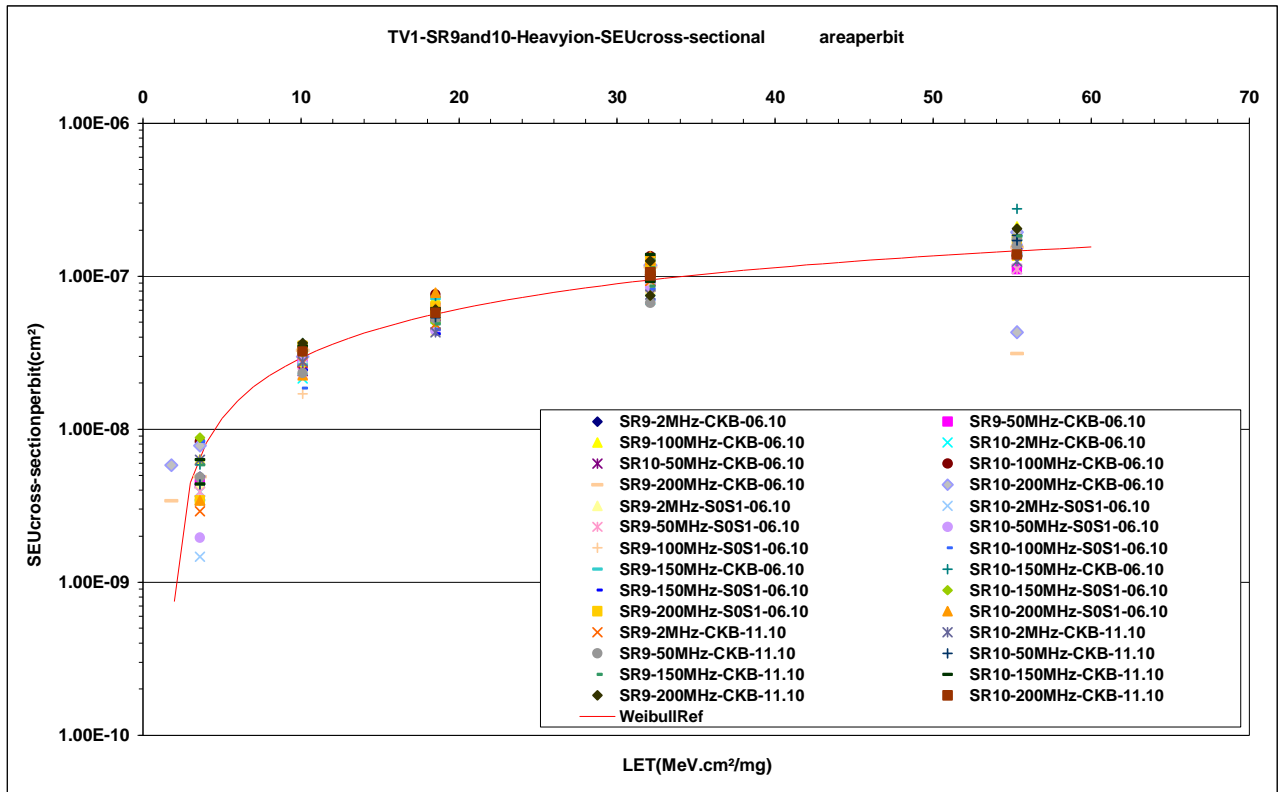


Figure47:TV1-SR9and10-SEUcross-sectional a reaperbit

TheFigure48plotstheSEUdistribution.Likethe referencechannel,mostSEUsareSBUswithmost2 /3of thoseerrorsattendedtocleartransition.Thevery fewMBUsarecomposedofthesamesignatures than the referencechannel.

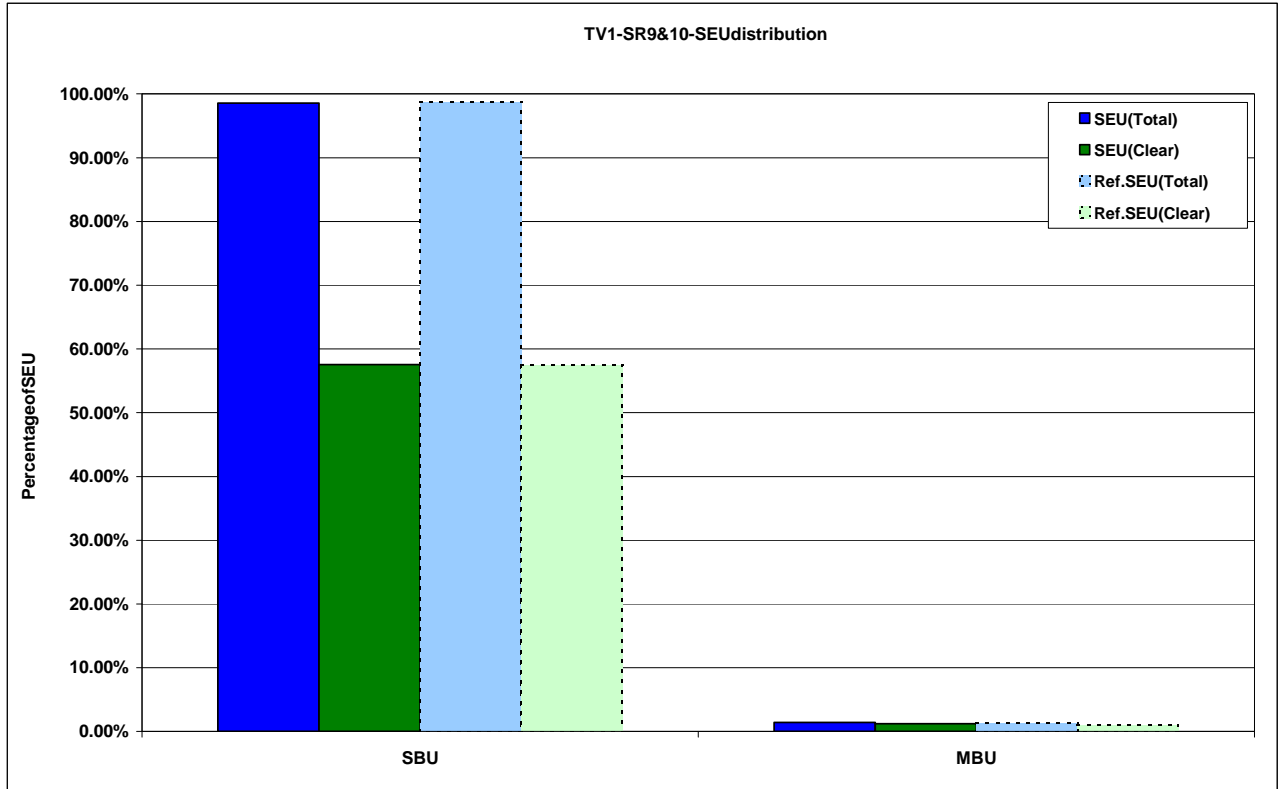


Figure48:TV1-SR9and10-SEUdistribution

9.2.7 TV1-SR11,12,13and14

TheTV1SR11,12,13and14channelswereclockedbythePLLoutputclock.

The SEU cross-sectional area per bit is similar to the reference channel. It is plotted on the Figure 49. It is characterized with an asymptotic cross-section (saturation cross-section) below $3E-7 \text{ cm}^2$ per bit and a LET threshold around $1.8 \text{ MeV} \cdot \text{cm}^2/\text{mg}$.

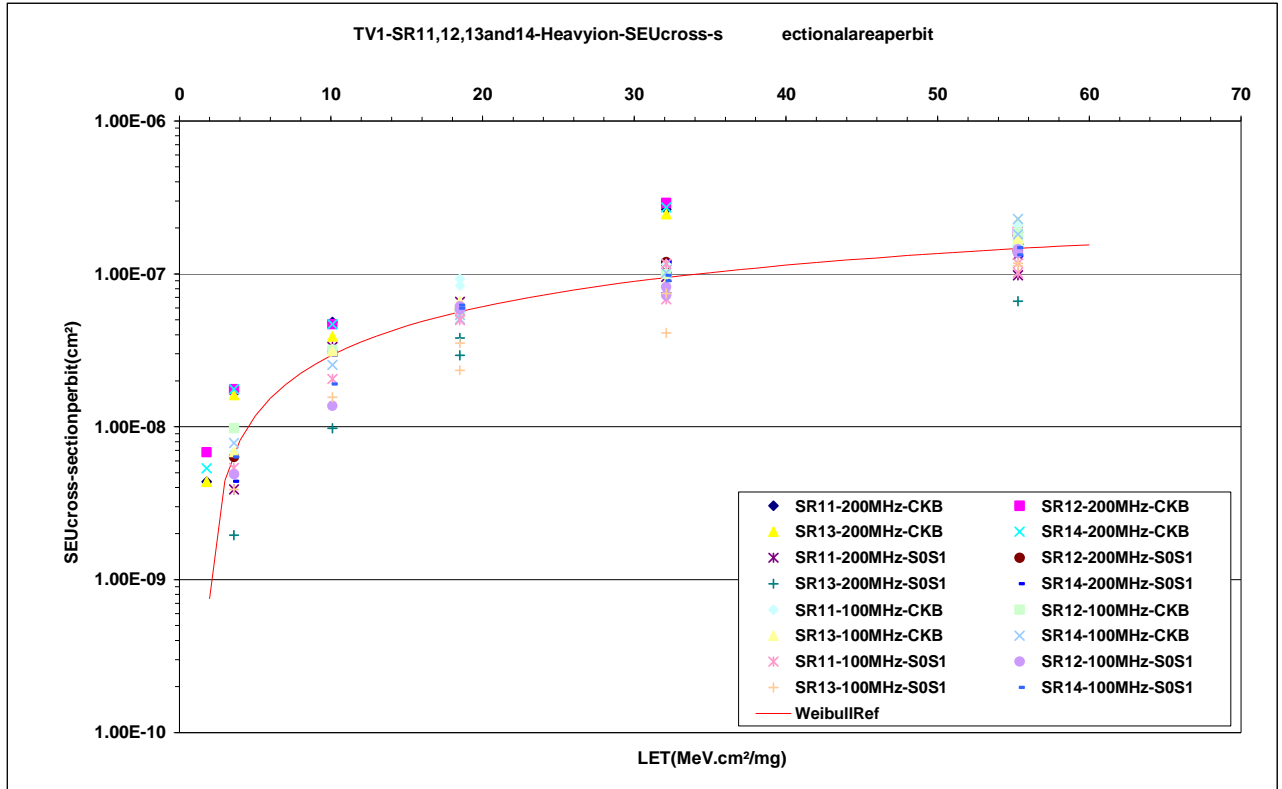


Figure49:TV1-SR11,12,13and14-SEUcross-sectionalareaperbit

The Figure50 plots the SEU distribution. Like the reference channel, most SEUs are SBUs with more than half coming from clear transition. MBU signatures are the same as the reference channel: it was not seen a total flip or stuck bit of the channel that could lead to a total or partial stop of the PLL output clock.

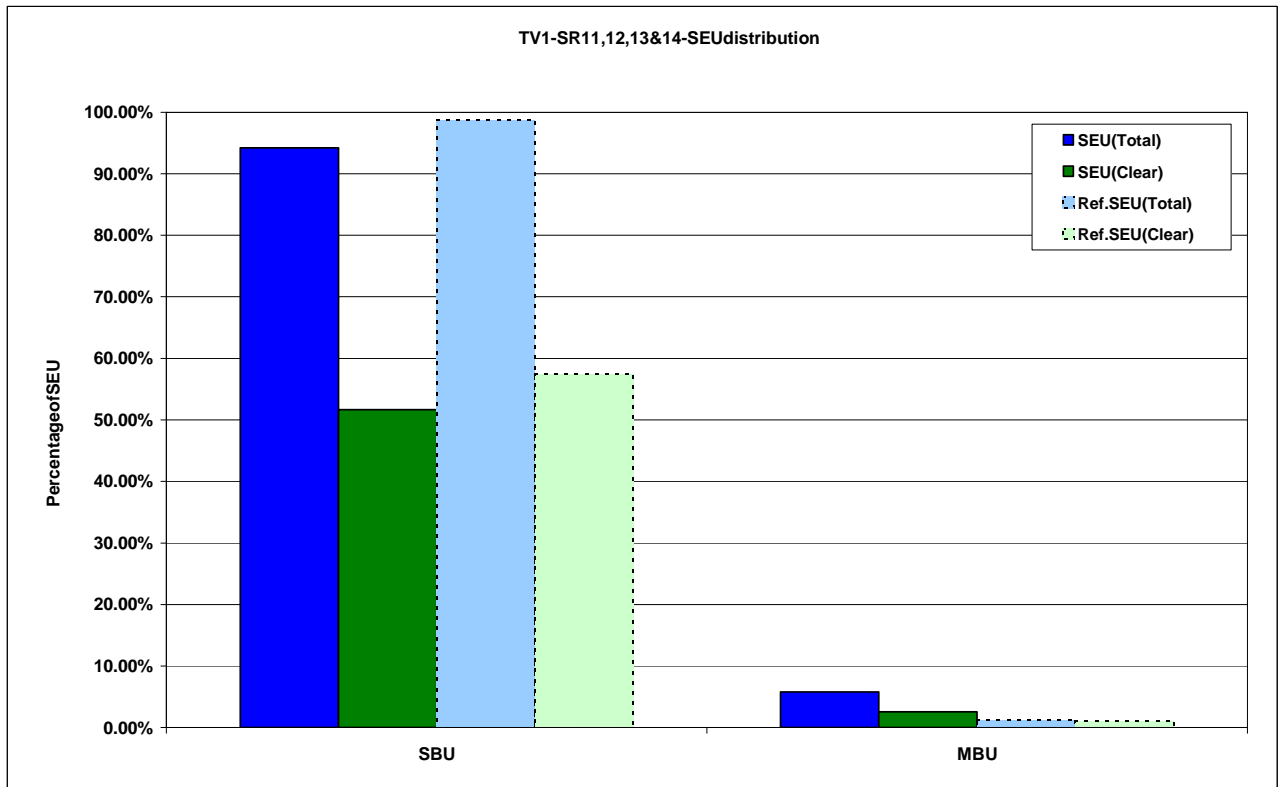


Figure50:TV1-SR11,12,13and14-SEUdistribution

9.3 TV2-SHIFTREGISTER

One SEFI was detected and recorded during the campaign at RADEF on November 2010 on the RUN112 with an effective LET of 55 MeV.cm²/mg. The device was configured with the TV2 and all shift registers were tested with a working frequency of 2 MHz. From the iteration N° 257 (a fluence of 3.69E5 p/cm²) up to the end of the run (a fluence of 5E5 p/cm²) all the data from the device were read at the low state ("0"). The device did not recover from the SEFI state by itself. The recovery took place after a power cycle of the device allowing the next run with the exact same condition to be performed without any more SEFI detected.

9.3.1 TV2-SR1

The TV2SR1 implemented sequential cell triplication as SEU mitigation.

The Figure 51 displays the SEU cross-sectional area per bit of this channel. It is based on a poor statistical distribution attended to the small number of errors. Therefore a Weibull curve was added to the graph for comparison purpose. It can be seen a large difference (around 2 decades) on both SEU cross-sections. The SEU cross-section is characterized with an asymptotic cross-section (saturation cross-section) below 2E-9 cm² per bit. The Weibull fit curve with the following parameters values was estimated from the points and added to the plot:

- K=1
- λ=80
- Xo=1.8MeV.cm²/mg
- CSsat=2E-9cm²

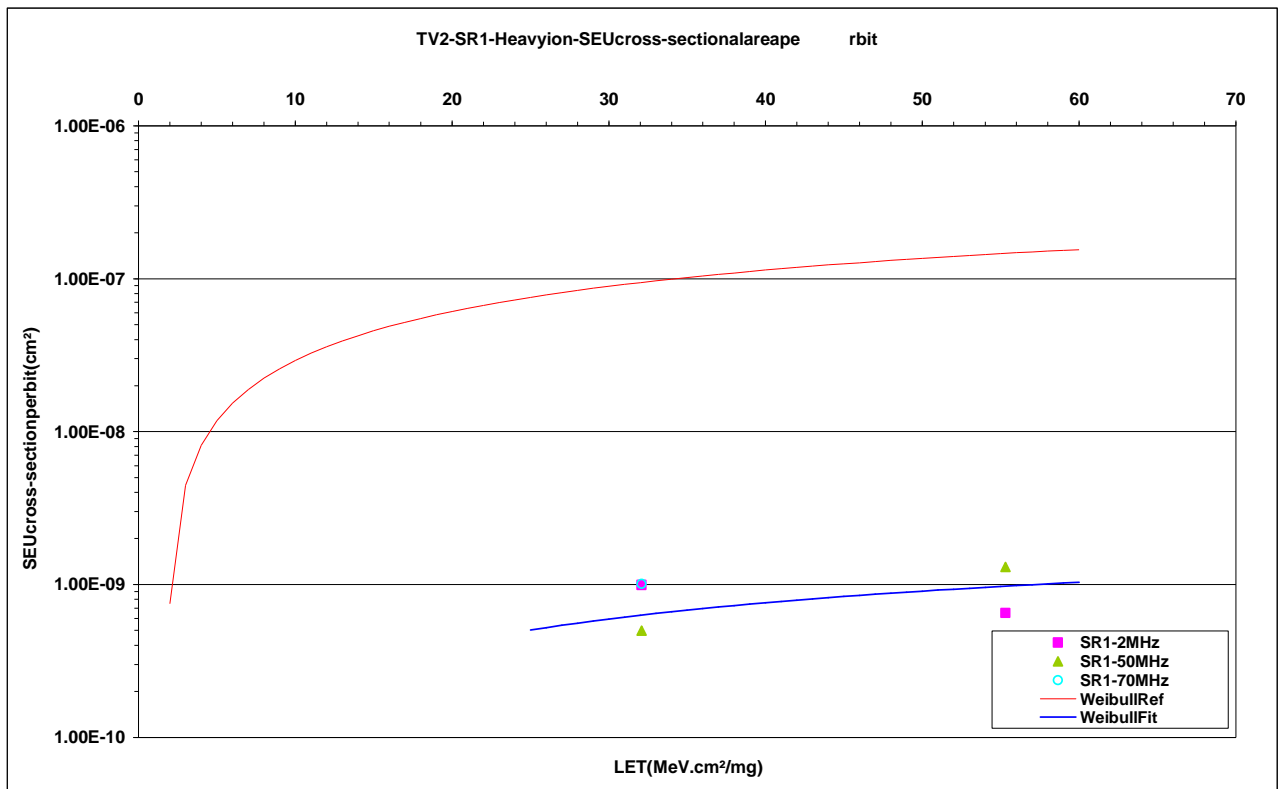


Figure 51: TV2-SR1-SEU cross-sectional area per bit

The Figure 52 plots the SEU distribution. More than 70% of SEUs are SBUs and all of those are due to clearance transition (transition from '1' to '0'). The high percentage of MBUs (almost 30%) compare to the reference channel is entirely made of arbitrary numbers of free set bits.

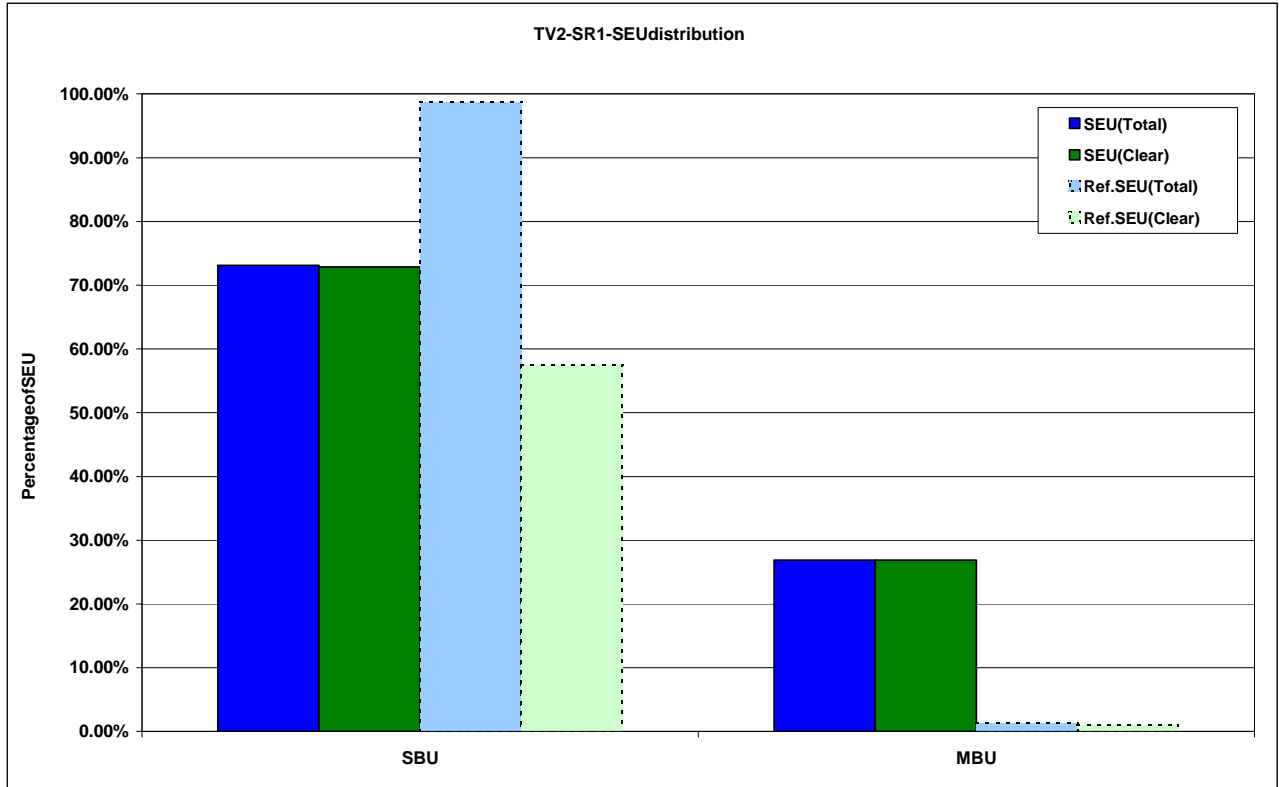


Figure52:TV2-SR1-SEUdistribution

These sequential cell triplication SEU mitigation series progressively decreases the total amount of SEU and changes the SBU vs. MBU ratio. All events appearing on the only asynchronous global (or local) reset signal shared between all registers induced all recorded SEU without any available correction from the voter.

9.3.2 TV2-SR2

The TV2SR2 implemented sequential cell and/or block triplication as SEU and SET mitigation.

The Figure 53 displays the SEU cross-sectional area added to the SEU cross-section graph for comparison per bit of this channel. The reference Weibull curve is a decade between the channel and the reference. The SEU cross-section is characterized with an asymptotic cross-section (saturation cross-section) below $2E-7 \text{ cm}^2/\text{mg}$ and a LET threshold below $10 \text{ MeV} \cdot \text{cm}^2/\text{mg}$. A Weibull fit curve was estimated from the measured points and added to the cross-section graph. The Weibull fit parameters values are:

- K=1
- $\lambda=80$
- $X_0=1.8 \text{ MeV} \cdot \text{cm}^2/\text{mg}$
- $CS_{\text{sat}}=1E-7 \text{ cm}^2$

This SEU cross-section is high compared to the SEU cross-section of the channel using only sequential cell triplication (TV2SR1). Because both channels use the same sequential cell triplication as SEU mitigation, a smaller (or in the worst case an equivalent) cross-section was expected on the SR2 channel. No explanation has been found yet to explain the result on this channel.

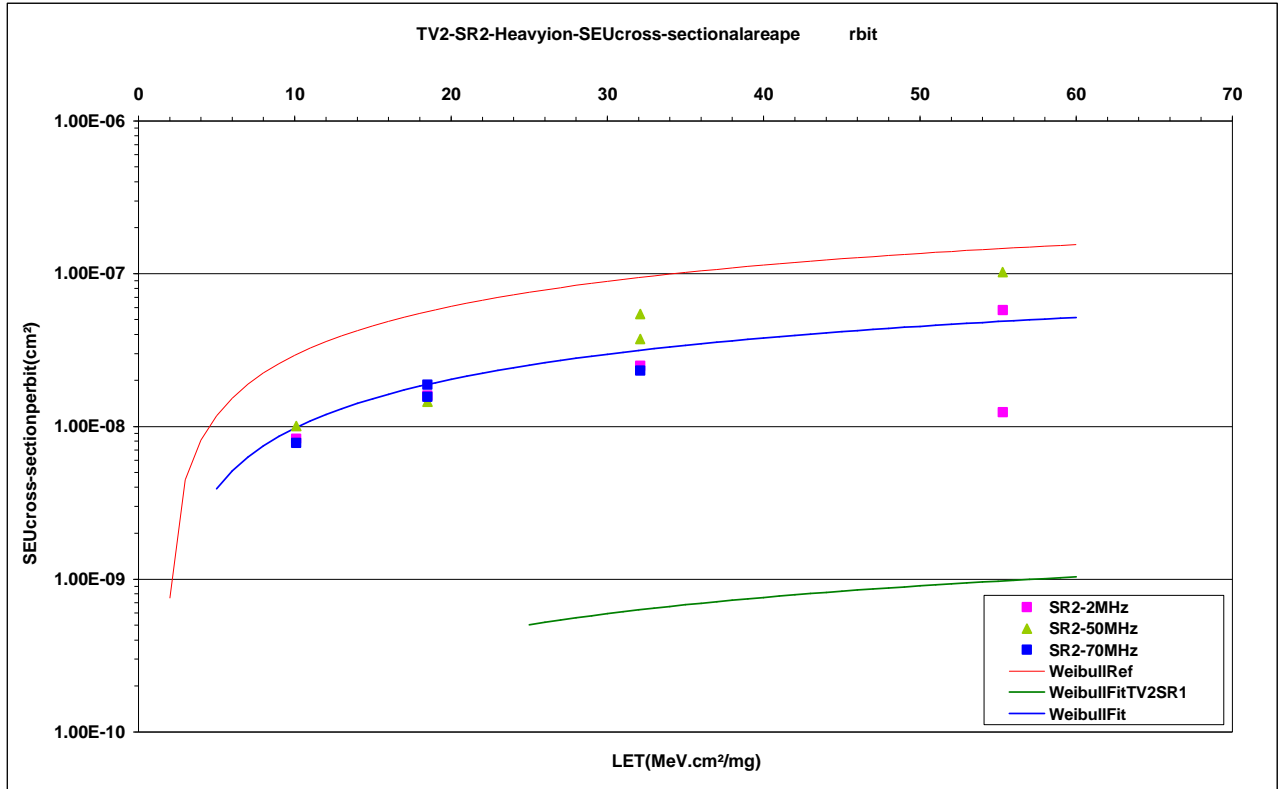


Figure53:TV2-SR2-SEUcross-sectionalareaper bit

The Figure 54 plots the SEU distribution. 87 % of SEUs are SBUs and 83 % of those are due to clear transition. The 13% of MBUs are made of arbitrary numbers of reset bits.

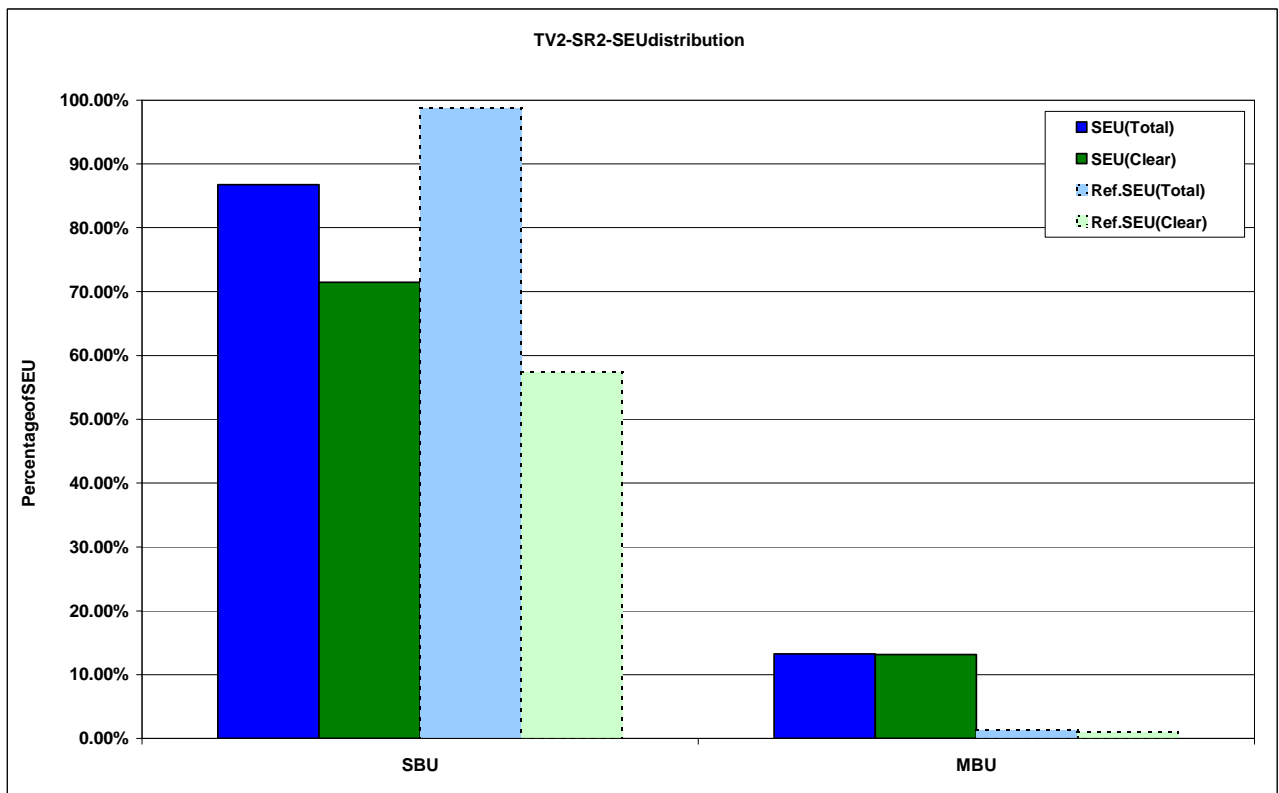


Figure54:TV2-SR2-SEUdistribution

9.3.3 TV2-SR3

The TV2SR3 implemented SET filtering with a delay of 2ns as SET mitigation.

The Figure 55 displays the SEU cross-section of this channel. It is characterized with an asymptotic cross-section (saturation cross-section) below $3E-7 \text{ cm}^2/\text{p}$ and a LET threshold around $1.8 \text{ MeV} \cdot \text{cm}^2/\text{mg}$. The reference Weibull curve was added to the graph for comparison purpose and it can be seen that the reference Weibull curve fits well the measured points of this channel.

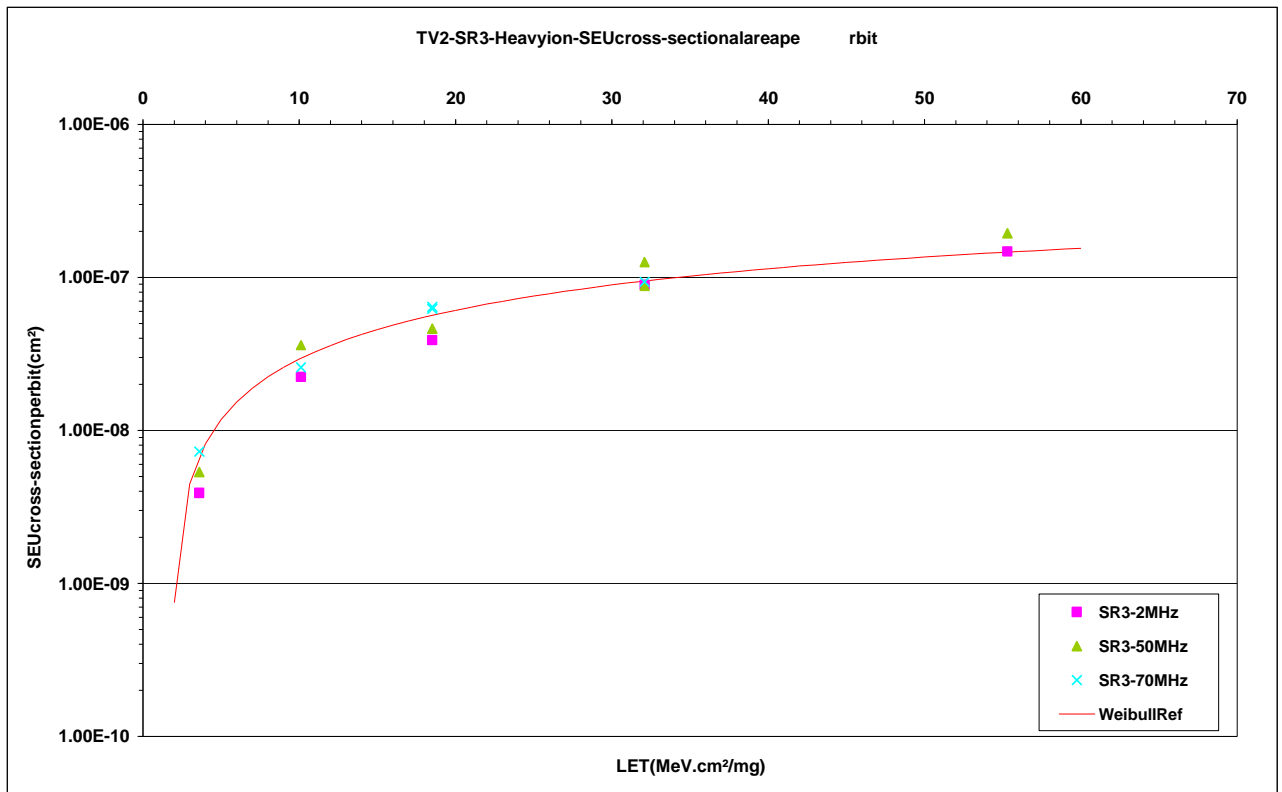


Figure 55: TV2-SR3-SEU cross-sectional area per bit

The Figure 56 plots the SEU distribution. Like the reference channel, most SEUs are SBUs with a little more than the half due to clear transition. MBUs counts and signatures are very similar to the reference.

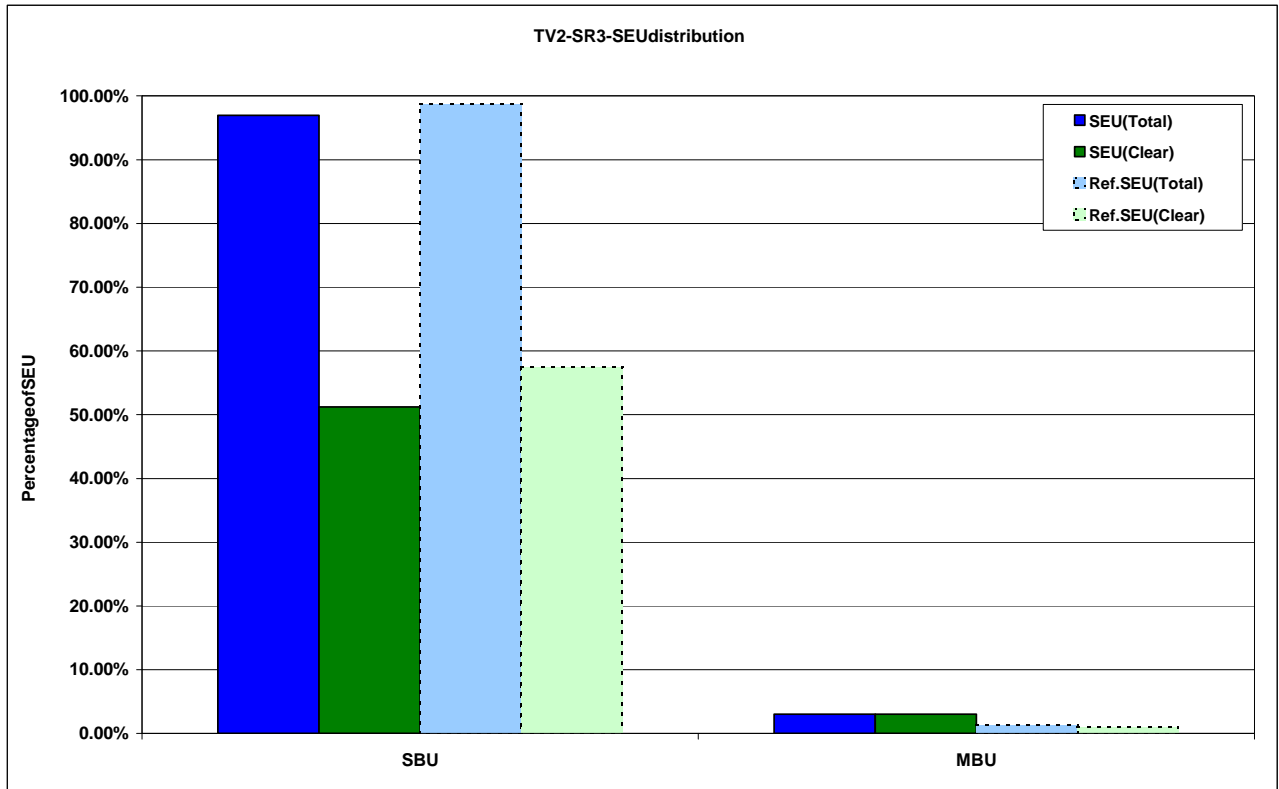


Figure56:TV2-SR3-SEUdistribution

9.3.4 TV2-SR4

TheTV2SR4implementedsequentialcelland/OblocktripllicationasSEUmitigationandSETfiltering witha delayof3nsasSETmitigation.

NoSEWasrecordedonthischanneluptoaLETof 55MeV.cm²/mgandaccumulatedfluenceof2E6p/cm².

9.3.5 TV2-SR5

TheTV2SR5implementedsequentialcelland/OblocktripllicationasSEUmitigationandlogicduplication asSETmitigation.

NoSEWasrecordedonthischanneluptoaLETof 55MeV.cm²/mgandaccumulatedfluenceof2E6p/cm².

9.3.6 TV2-SR6

TheTV2SR6implementedsequentialcelland/OblocktripllicationasSEUmitigationandcombinational cell tripllicationasSETmitigation.Thismitigationtechniqueisalsocalled[full]TripleModularRedundancy(TMR).

TheFigure57plots theSEU cross-sectionalareaper bit of this channel. It is based on an extremely poor statisticbecauseonly2SEUswererecorded. ThereferenceandtheTV2SR1Weibullcurveswereadded to thegraphforcomparisonpurpose.

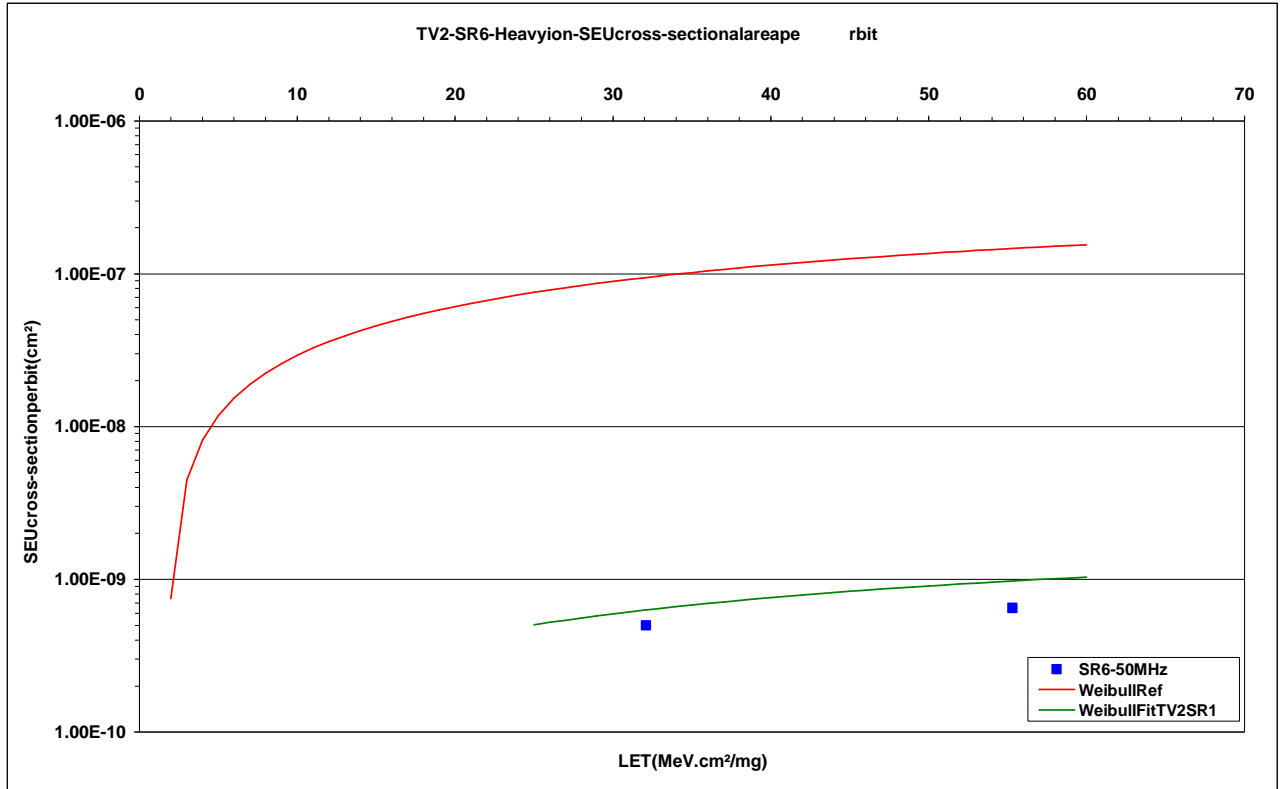


Figure57:TV2-SR6-Heavyion-SEUcross-section alareaperbit

The recorded SEUs were 2 SBUs due to clear transition.

9.4 **SRAM**

The SRAM SEU cross-sectional area per bit is plotted on the Figure 58. It is characterized with an asymptotic cross-section around $4E-8 \text{ cm}^2$ per bit and a LET threshold below $1.8 \text{ MeV.cm}^2/\text{mg}$. A Weibull fit curve was estimated from the measured points and added to the graph. The Weibull fit parameters values are:

As a remark, all test conditions (dynamic, static and Flash Freeze) fit well to the estimated SEU cross-section.

- K=1
- $\lambda=22.5$
- $X_0=0.2 \text{ MeV.cm}^2/\text{mg}$
- $C_{\text{Sat}}=4E-8 \text{ cm}^2$

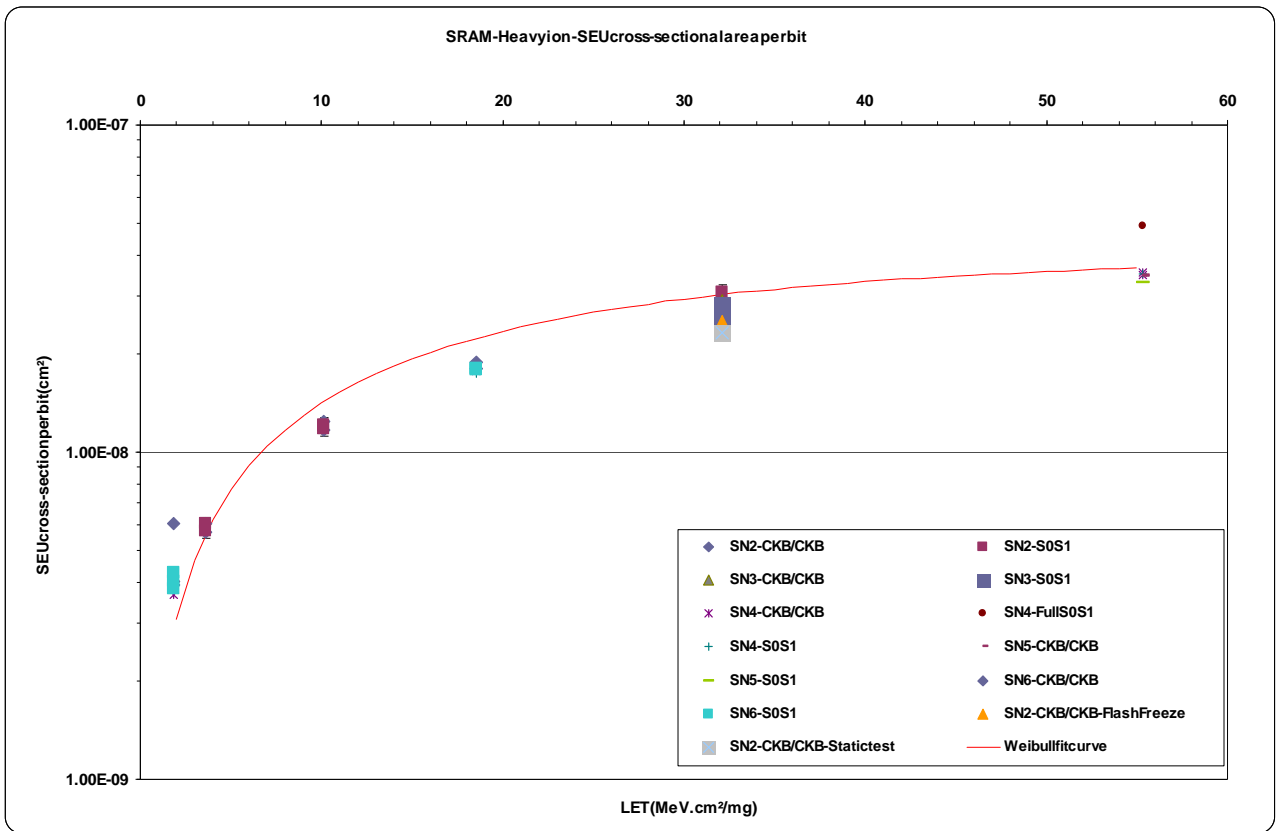


Figure 58: SRAM-SEU cross-sectional area per bit

As highlighted on the Figure 59 all SRAM errors are SBU. The Table 10 summarizes the available error types (see paragraph 8.3 for further details). The Figure 60 shows the very large majority of errors are SBU. The SEUs, the erroneous bit position inside the word.

SEUs (checking type 2 - upset while checking process). The Figure 60 displays the very well balanced distribution of SEUs. By averaging the data of all bits it can be stated that:

- ✓ 47% of SEU errors are reset bit while 53% are reset bit (clear bit) (see Figure 62).
- ✓ 47% of SEU errors are located on the north side while 53% are on the south side (see Figure 63).

The north side and south side error counts are close to each other. The small difference between the counts can also be originated from the variation of the homogeneity of the beam on the large distance between the opposite sides of the die.

The small difference between the counts can also be originated from the variation of the homogeneity of the beam on the large distance between the opposite sides of the die.

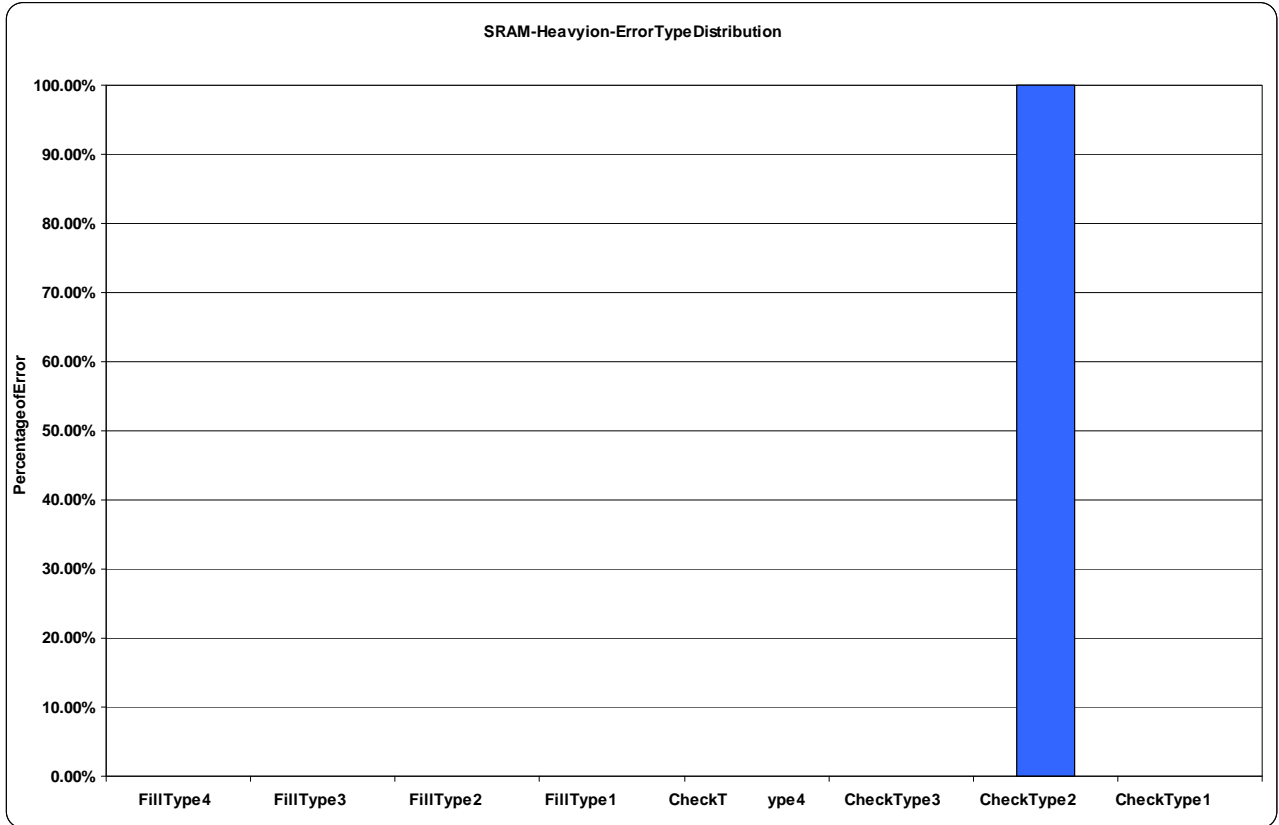


Figure59:SRAM-Errortypedistribution

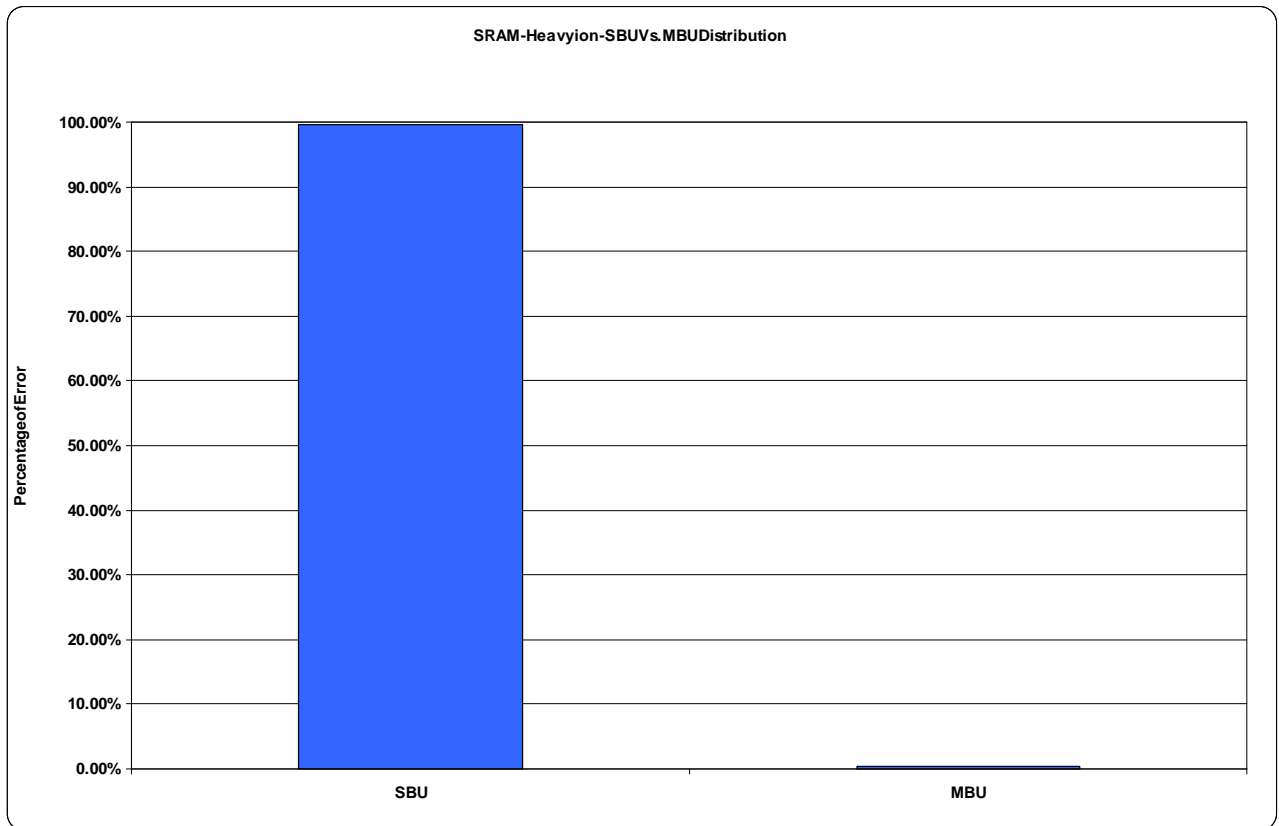


Figure60:SRAM-SBUvs.MBUDistribution

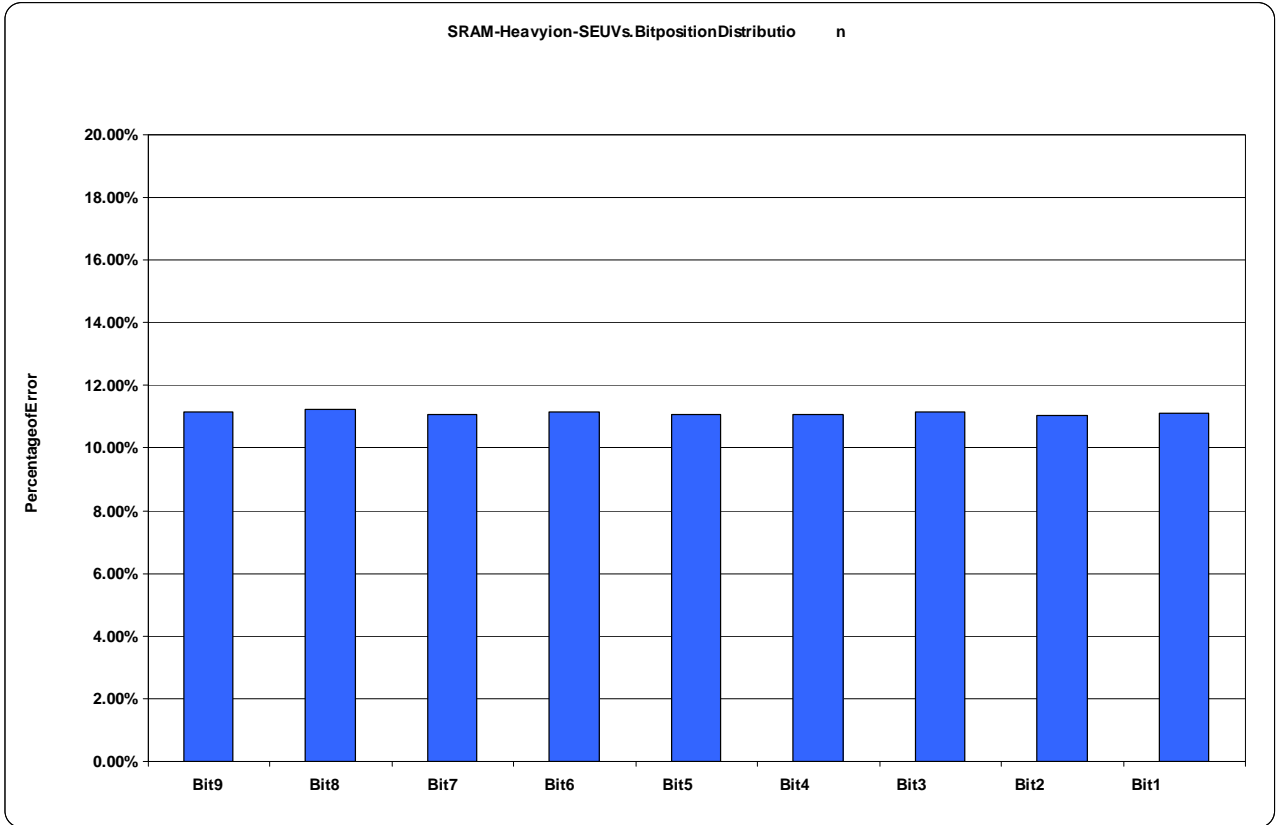


Figure61:SRAM-SEUvs.Bitpositiondistribution

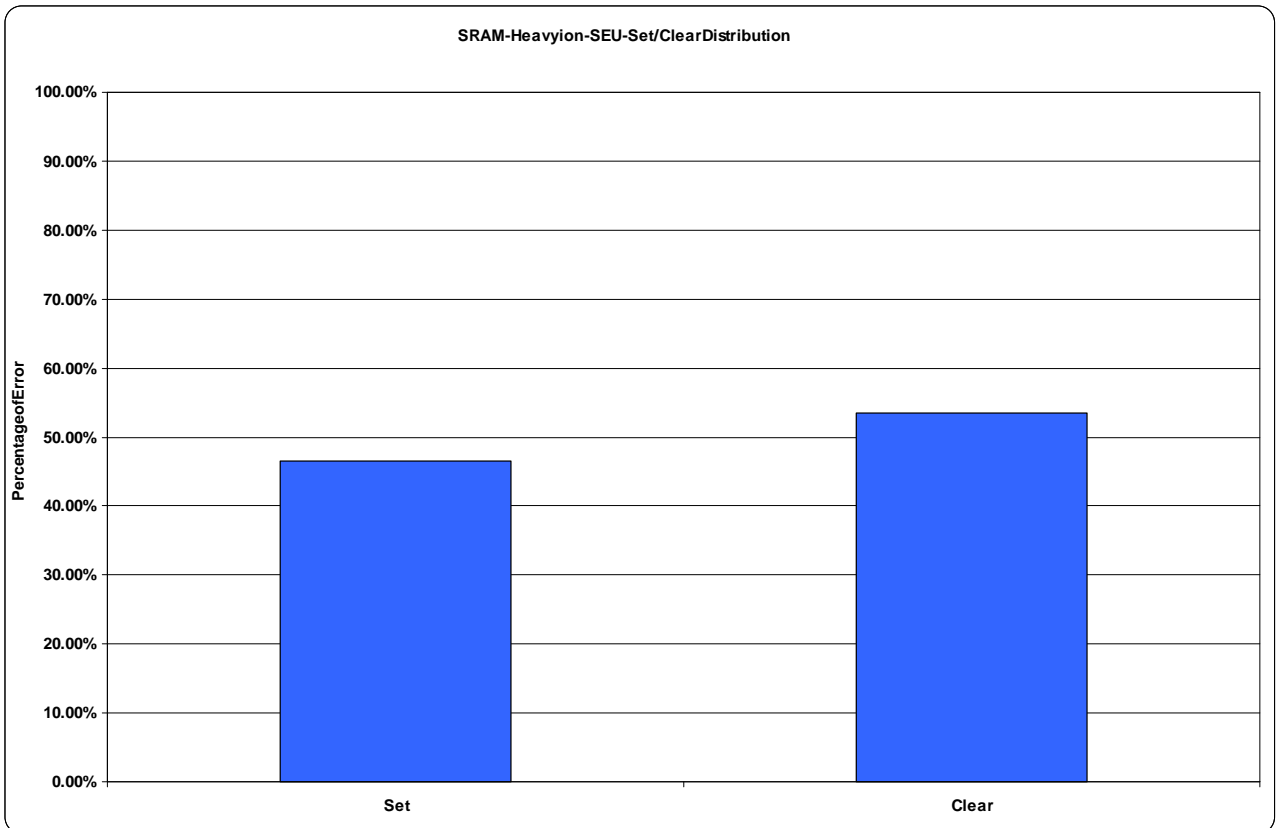


Figure62:SRAM-SEU-Set/Cleardistribution

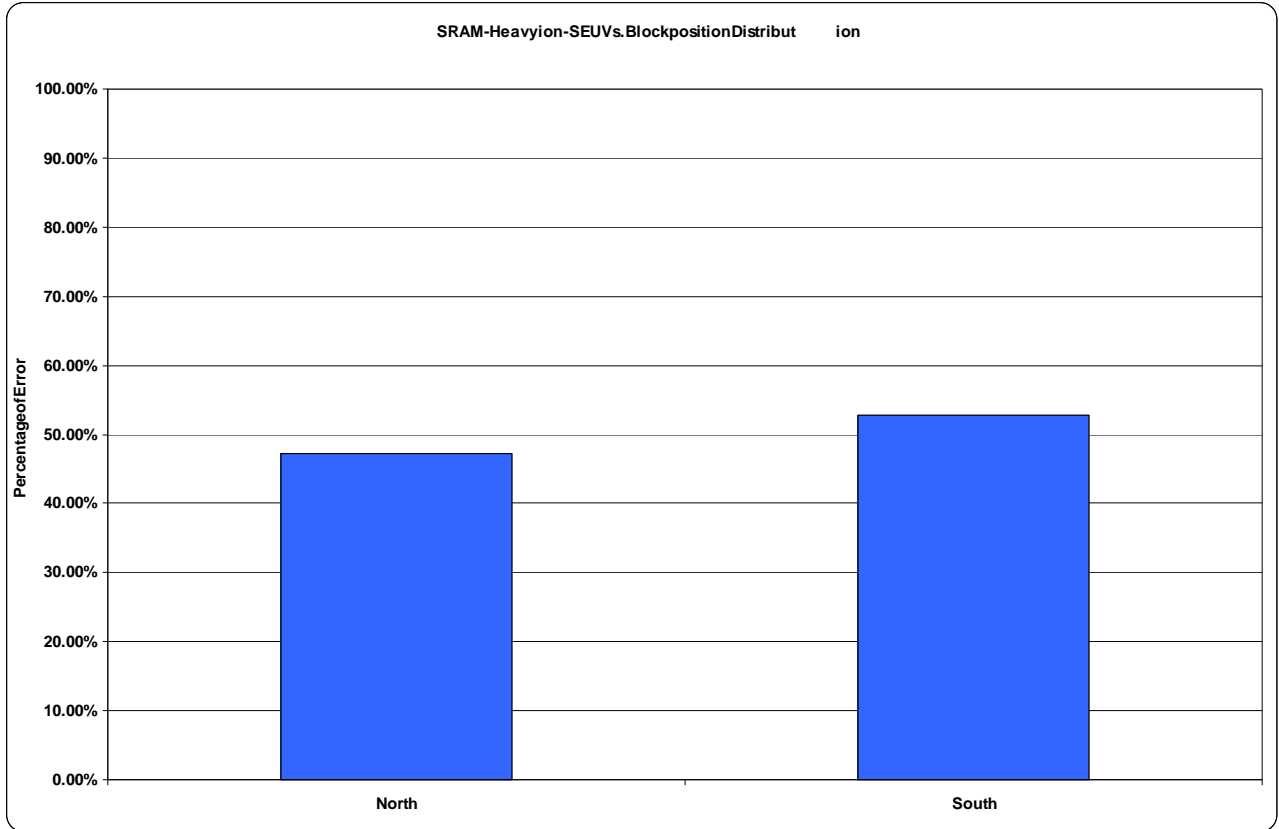


Figure63:SRAM-SEUvs.Blockpositiondistribution

9.5 **UFROM**

No error was observed (neither recorded) on the UFR OM upto a LET of 55 MeV.cm²/mg (¹³¹Xe³⁵⁺) and a total cumulated fluence of 1.36E7 p/cm².

9.6 **CCC/PLL**

Like the reference channel, most SEUs on the shift register channels clocked by the PLL output clock are SBUs with more than half coming from clear transition. MBUs signatures are the same as the reference channel. It was not seen a total flip or stuck bit of the channels' outputs that could lead to a total or partial stop of the PLL output clock: the PLL output clock never stopped.

The PLL lock signal however is sensitive to Large Error (here below called PLL lock signal SEFI) and to SET. One PLL lock signal SEFI event was counted each time an error appeared on the PLL lock signal and the PLL did not recover by itself. The recovering process was made using a power cycle. On the other way, the error was counted as a SET each time the PLL recovered by itself.

4 PLL lock signal SEFIs were recorded on the PLL lock signal under the following conditions:

SEFI#	1	2	3	4
Frequency (MHz)	100	150	150	100
LET (MeV.cm ² /mg)	32.1	32.1	18.5	18.5
Conditions	RADEF-June 2010-RUN22	RADEF-June 2010-RUN66	RADEF-June 2010-RUN101	RADEF-June 2010-RUN121
Fluence (p/cm ²)	5E5	1E6	1E6	1E6

Table13:CCC/PLL-PLL lock signal SEFI conditions

No PLL lock signal SET was recorded under the nominal condition.

The PLL lock signal SET cross-sectional area is plotted on the Figure 64. This SET cross-section is based on a poor statistic attended to the small number of errors. Three Weibull fit curves from 3 different input frequencies (200, 150 and 100 MHz) were more or less added to the graph. It can be seen that the frequency influence the SET sensitivity. Because the PLL was sensitive to a static mode to a nominal frequency of 200 MHz, increasing the gap between the nominal frequency and the working frequency increased the SET sensitivity. In nominal condition, the CCC/PLL lock signal SET cross-section is characterized with an asymptotic cross-section below $1E-5 \text{ cm}^2$ and a LET threshold around $1.8 \text{ MeV.cm}^2/\text{mg}$. The nominal Weibull fit curve has the following parameters values:

$K=1$
 $\lambda=160$
 $X_0=1.8 \text{ MeV.cm}^2/\text{mg}$
 $CS_{\text{sat}}=1E-5 \text{ cm}^2$

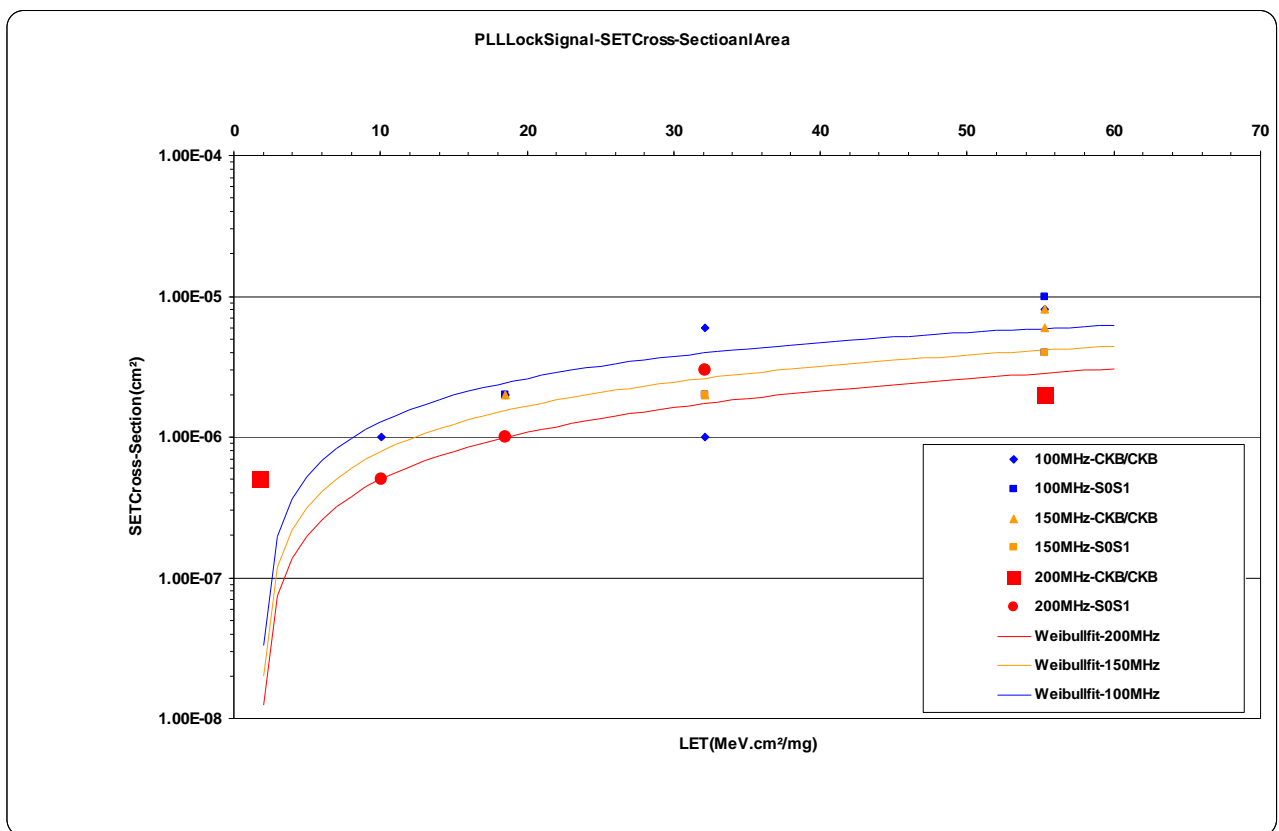


Figure 64: PLL Lock signal-SET cross-sectional area

9.7 CONFIGURATION FLASH, CHARGE PUMP & IN SYSTEM PROGRAMMING

The configuration flash is not sensitive to SEE. However the programming part of the configuration flash is sensitive to SEU, SHE and to the cumulated dose deposited by the cumulated fluence.

The following processes of the device configuration were run under beam exposition to check the sensitivity and can be stated to be sensitive to SEE.

- ✓ Erasing
- ✓ Programming
- ✓ Verifying

The processes were tested all together and separately on the beam. The success of the process, the functionality of the design and the re-configurability of such configured devices was then verified (once or twice) off beam.

The following Table 14 summarizes the status of the samples.

Few remarks have to be made on the Table 14:

- i. All status are stated from functionality of the design and the re-configurability of the sample. The failing of the re-configuration was generally verified by repeating the operation.
- ii. The dose (the status) after configuration test is the dose (the status) of the sample at the end of the last configuration test run performed under the beam. Additional runs (to test other parts of the device) can be performed on the same sample after the last configuration test run.
- iii. The status after SEE test is the status of the sample at the end of the test campaign.
- iv. The final dose is the total dose received by the sample.
- v. The final status is the status of the sample stated at the end of all tests. All samples were checked in August 2011 (5 months after the last campaign).

From this Table 14, it can be seen that:

- Over the 6 samples tested in configuration mode:
 - ✓ All were the source of SEUs inducing failures in the programming process. An off beam re-configuration was then successfully completed and the functionality of the design successfully verified.
 - ✓ 2 samples (SN3 and SN16) were the source of SHE during the configuration of the sample and were so destroyed.
 - ✓ 1 sample (SN5) was stated as fail (not configurable anymore) at the end of the heavy ion test (November 2010). It received a cumulated dose of 21 KRad. The same sample was then stated as pass (fully functional and re-configurable) at the end of all tests (August 2011).
- The influence of the cumulated dose deposited by the cumulated fluence can also be seen on the sample SN4. This sample was not used to test the configuration process, but the cumulated dose of this sample (29 KRad) at the end of the heavy ion test (November 2010) damaged its configuration system. The sample did not recover and was still failing (design functional but sample not re-configurable) at the end of all tests (August 2011).
- 3 samples (SN 8, 10 and 11) failed the re-configuration verification right after the heavy ion test. However they all passed (fully functional and re-configurable) the day after.

SN	Beam Nature	Configuration test			Dose (after configuration test) (Rad)	Status (after configuration test)	Status (after SEE test)	Status (after SEE test + 1 day)	Final Dose (Rad)	Final status
		SEU	SHE							
1	Heavy Ions				na	na	Pass	Pass	0.00E+00	Pass
2	Heavy Ions	X	X		1.43E+04	Pass	Pass	Pass	1.43E+04	Pass
3	Heavy Ions	X	X	X	6.57E+03	Fail	Fail	Fail	6.57E+03	Fail
4	Heavy Ions				na	na	not verified	Fail	2.89E+04	Fail
5	Heavy Ions	X	X		1.21E+04	Pass	Fail	Fail	2.09E+04	Pass
6	Heavy Ions	X	X		5.00E+03	Pass	Pass	Pass	5.00E+03	Pass
7	Heavy Ions				na	na	Pass	Pass	0.00E+00	Pass
8	Heavy Ions				na	na	Fail	Pass	2.84E+03	Pass
9	Heavy Ions				na	na	Pass	Pass	1.61E+02	Pass
10	Heavy Ions				na	na	Fail	Pass	1.92E+03	Pass
11	Heavy Ions				na	na	Fail	Pass	1.00E+04	Pass
12	Heavy Ions				na	na	Pass	Pass	0.00E+00	Pass
13	Heavy Ions				na	na	Pass	Pass	0.00E+00	Pass
14	Heavy Ions				na	na	Pass	Pass	0.00E+00	Pass
15	Heavy Ions				na	na	Pass	Pass	0.00E+00	Pass
16	Heavy Ions	X	X	X	3.20E+03	Fail	Fail	Fail	3.20E+03	Fail
17	Heavy Ions	X	X		1.05E+03	Pass	Pass	Pass	1.05E+03	Pass
18	Heavy Ions				na	na	Pass	Pass	0.00E+00	Pass
19	Proton				na	na	Pass	Pass	2.94E+04	Pass
20	Proton				na	na	Pass	Pass	1.65E+04	Pass
21	Proton				na	na	Pass	Pass	4.41E+03	Pass
22	Proton				na	na	Pass	Pass	0.00E+00	Pass
23	Proton				na	na	Pass	Pass	0.00E+00	Pass
24	Proton				na	na	Pass	Pass	0.00E+00	Pass

Table14:Samplesstatus

10 PROTON-TESTRESULTS

10.1 POWERSUPPLY

No SEL has been observed up to an energy of 230 MeV, a cumulative fluence of 6.36×10^{11} p/cm², a room temperature, a bias voltage of 1.5V for the core voltage and 3.3V for the input/output voltage.

10.2 TV1-SHIFTREGISTER

10.2.1 TV1-SR1

Due to the low proton sensitivity of the Dcore flip-flop (register) a large fluence was needed and a large dose was deposited on the samples at each run: this limiting the characterization. As a consequence, only 230 MeV energy was used. The SEU cross-section per bit plotted on the Figure 65 is below 1×10^{-13} cm² at 230 MeV.

In the purpose to increase the proton SEU cross-section statistics, the total number of register composing the shift registers on the design could be increased. However this would have requested the usage of another design including a higher number of register inside each shift register or the modification of the requirements of the original test vehicle.

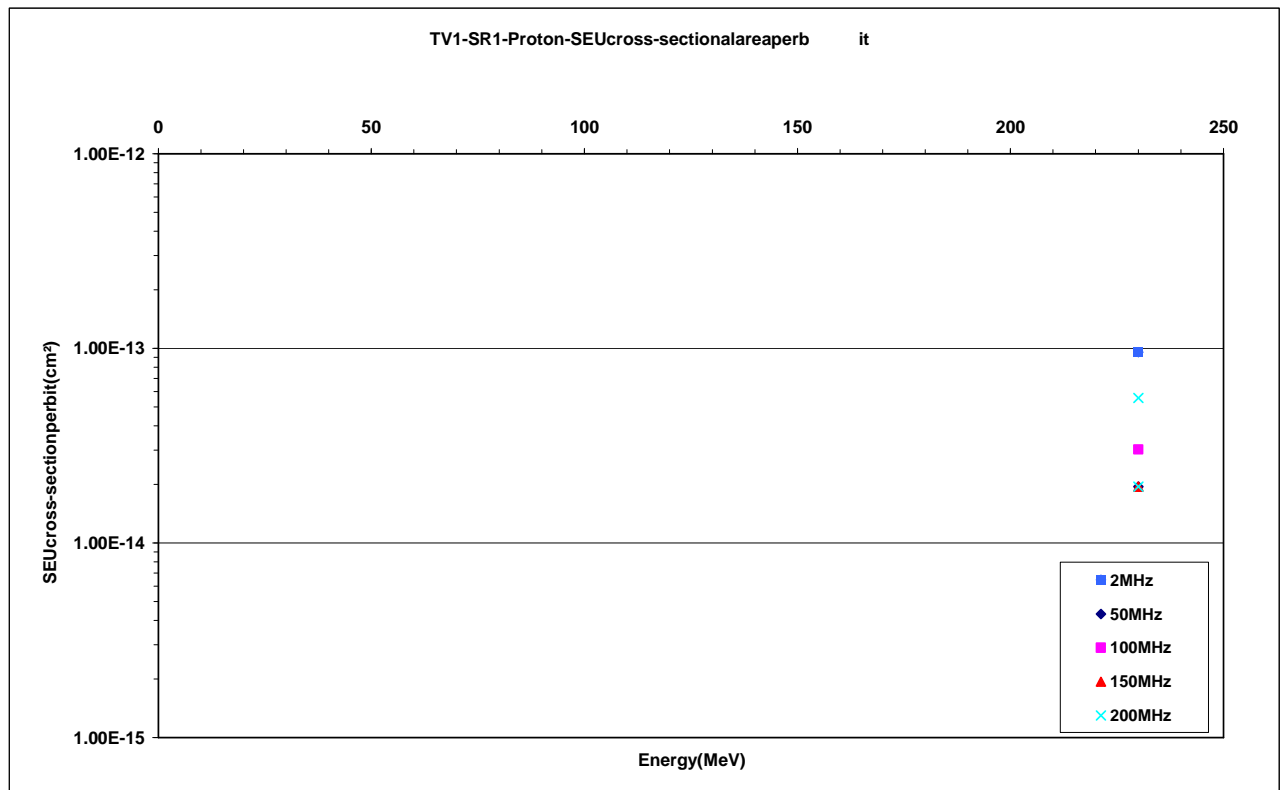


Figure 65: TV1-SR1-SEU cross-sectional area per bit

10.2.2 TV1-SR2

The SEU cross-section per bit plotted on the Figure 66 is the same as the reference below 1×10^{-13} cm² at 230 MeV.

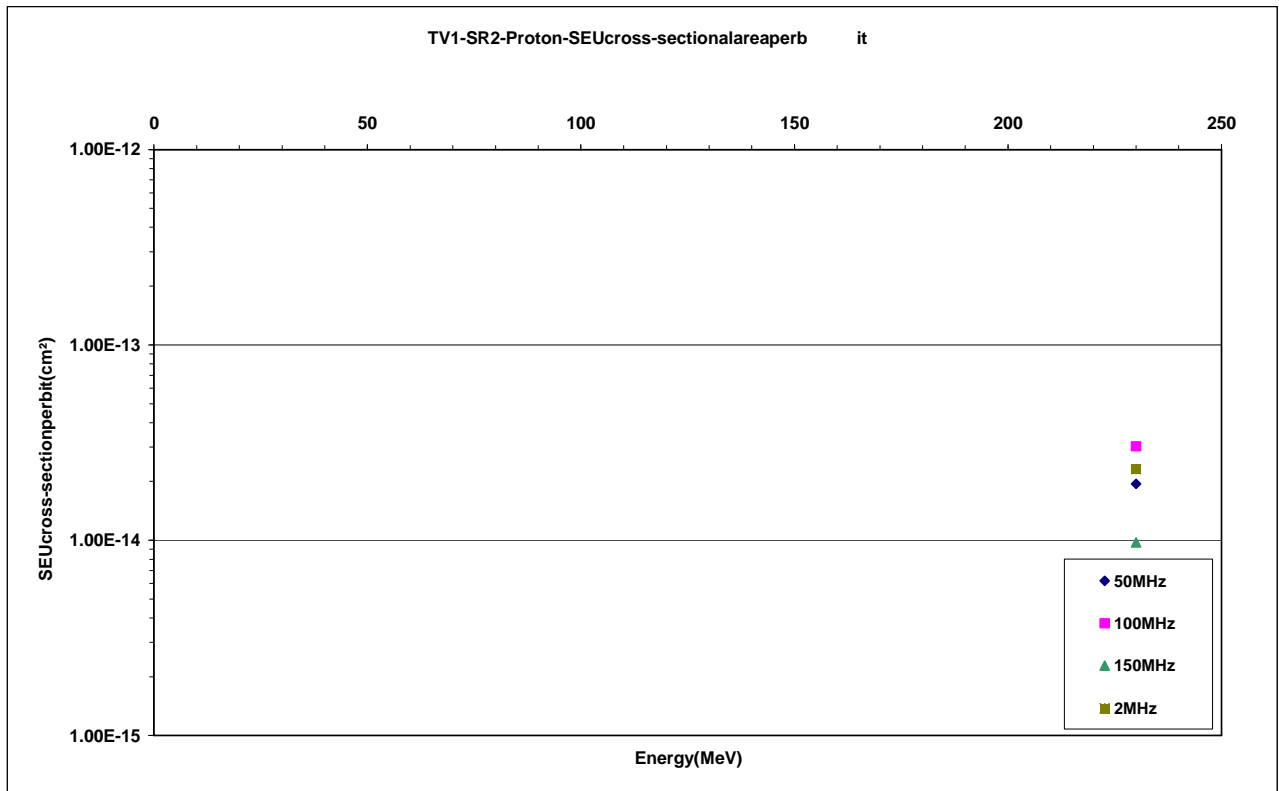


Figure66:TV1-SR2-SEUcross-sectionalareaper bit

10.2.3 TV1-SR3

TheSEUcross-sectionperbitplottedontheFigure 67issimilartothereferencechannelbelow1E-13 cm²at 230MeV.

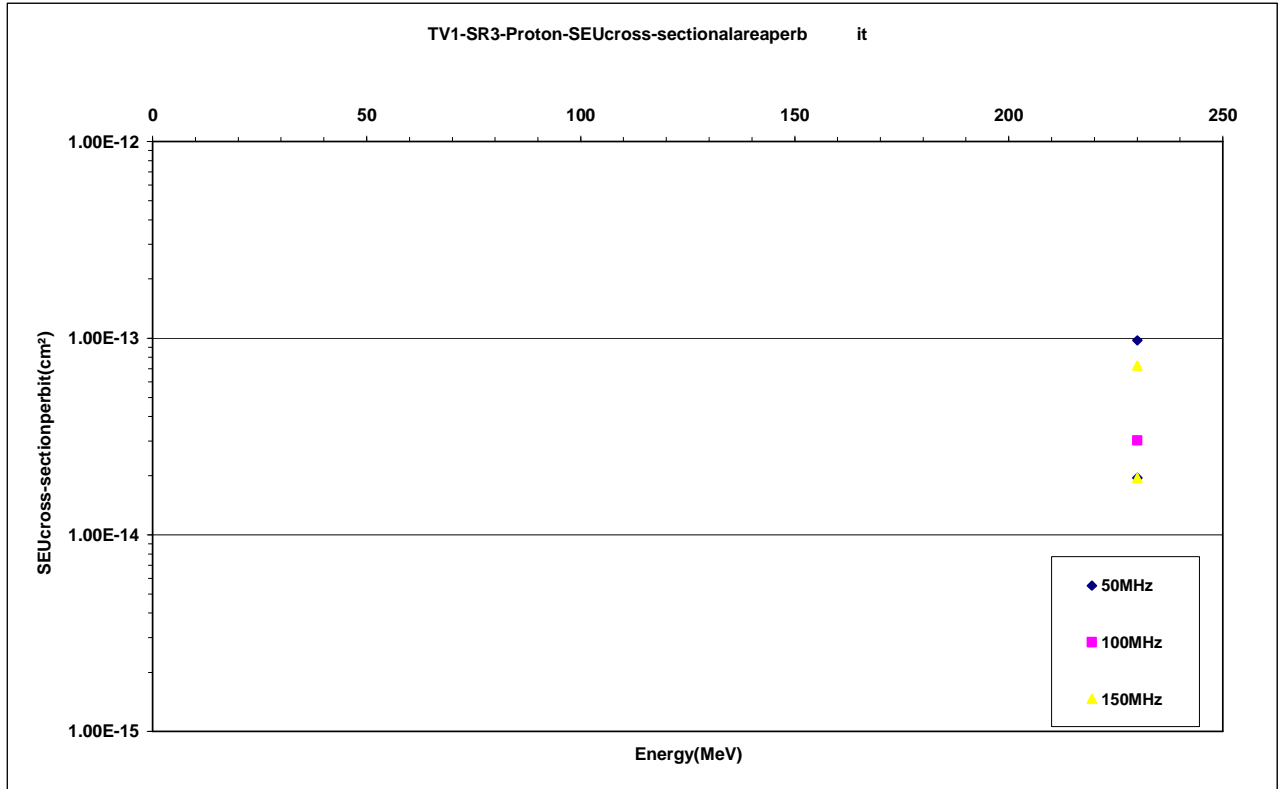


Figure67:TV1-SR3-SEUcross-sectionalareaper bit

10.2.4 TV1-SR4

TheSEUcross-sectionperbitplottedontheFigure 68issimilartothereferencechannelbelow1E-13 cm²at 230MeV.

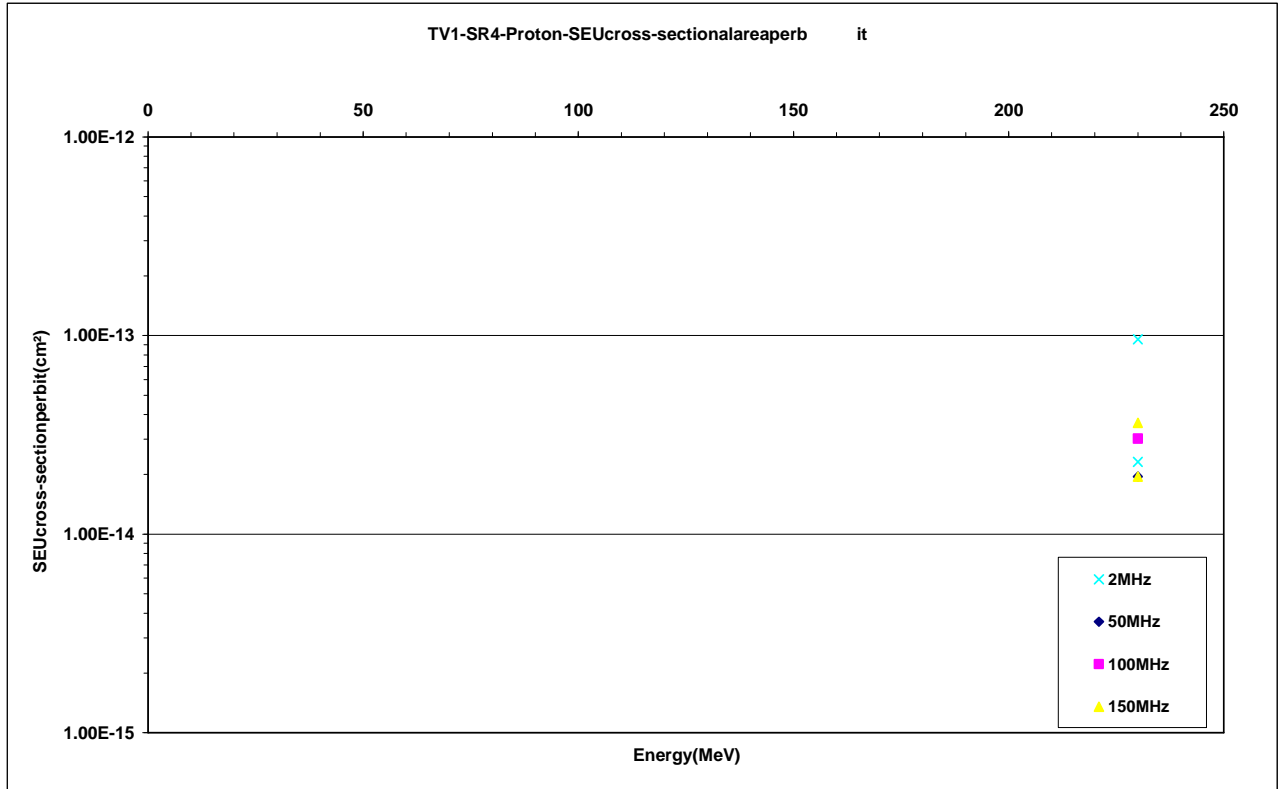


Figure68:TV1-SR4-SEUcross-sectionalareaper bit

10.2.5 TV1-SR5,6,7and8

TheSEUcross-sectionperbitplottedontheFigure 69issimilartothereferencechannelbelow1E-13 cm²at 230MeV.

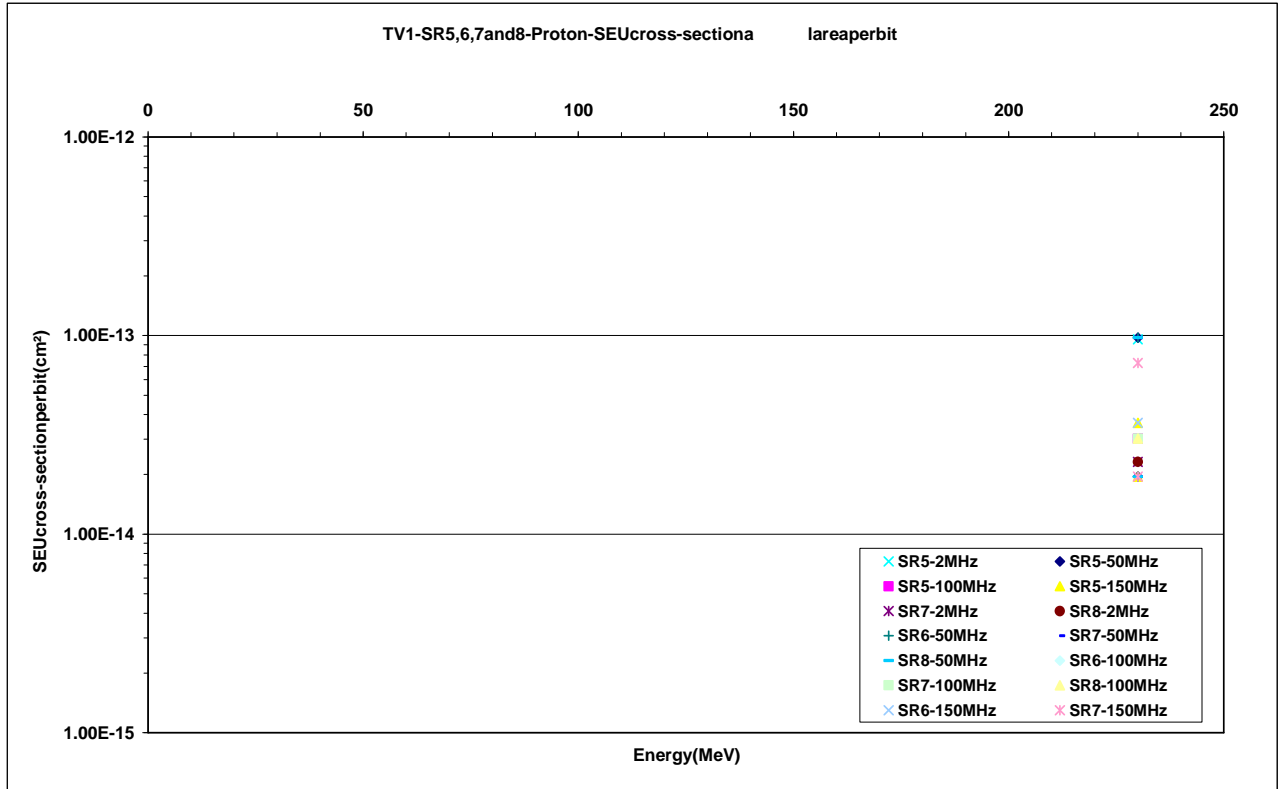


Figure69:TV1-SR5,6,7and8-SEUcross-sectiona lareaperbit

10.2.6 TV1-SR9and10

TheSEUcross-sectionperbitplottedontheFigure 70issimilartothereferencechannelbelow1E-13 cm²at 230MeV.

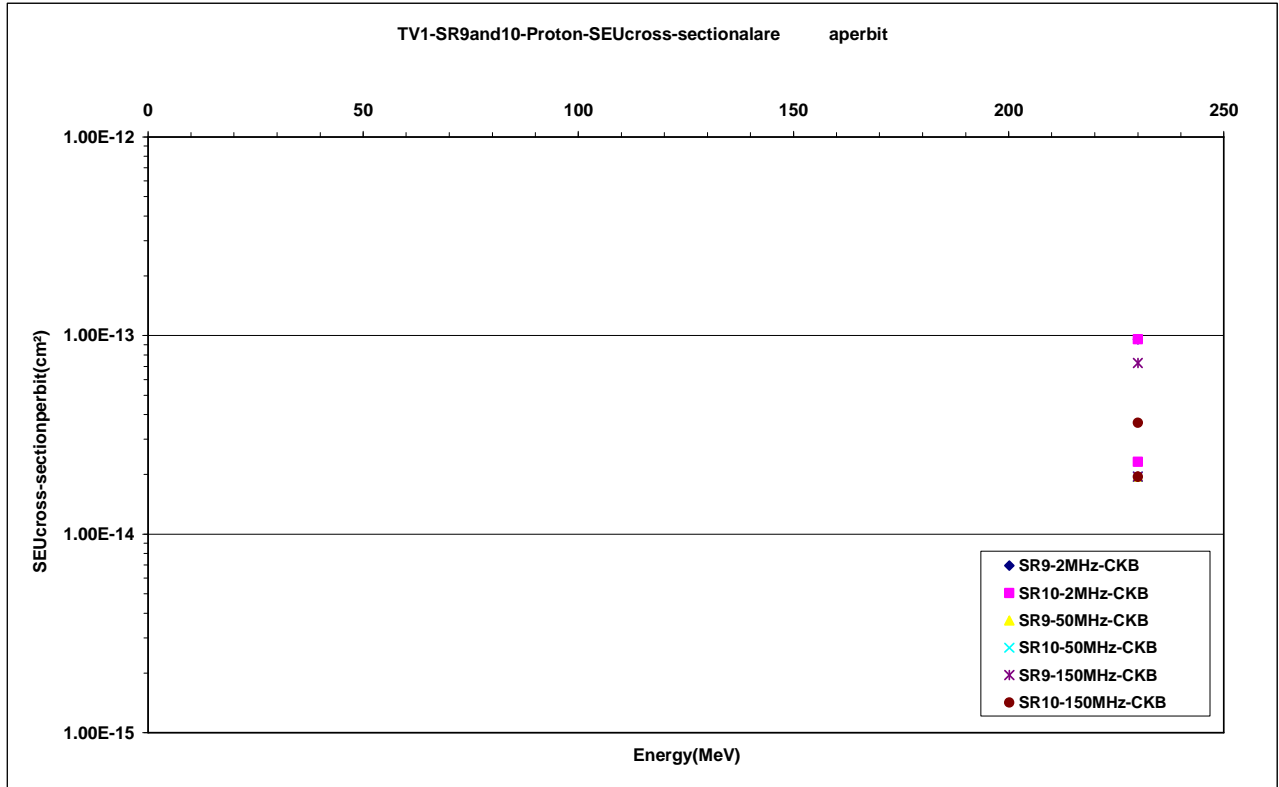


Figure 70: TV1-SR9 and 10-SEU cross-sectional area per bit

10.2.7 TV1-SR11,12,13 and 14

Those channels were not tested to proton.

10.3 TV2-SHIFT REGISTER

Due to the poor number of SEE recorded on the TV2 during heavy ion tests and the low proton sensitivity of registers of the TV1, the TV2 was not tested to proton.

10.4 SRAM

The SRAM SEU cross-sectional area per bit is plotted on the Figure 71. It is characterized with an asymptotic cross-section below 1E-13 cm² per bit and an energy threshold below 23.5 MeV.

One sample was used to fully characterize the SRAM at several energies while a second sample was used on 2 energies to verify. The 2 sample points are very likely.

Only the dynamic mode was used as test condition.

As highlighted on the Figure 72 all SRAM errors are SEUs (checking type 2-upset while checking process). The Table 10 summarizes the available error types (see paragraph 8.3 for further details). The Figure 73 shows that the very large majority of errors are SBUs. The Figure 74 displays the well balanced distribution of SEUs. By averaging data of all bits it can be stated that:

- ✓ 58% of SEUs are reset bit while 42% are clear bit (reset bit) (see Figure 75).
- ✓ 50% of SEUs are relocated on the north side while 50% are on the south side (see Figure 76).

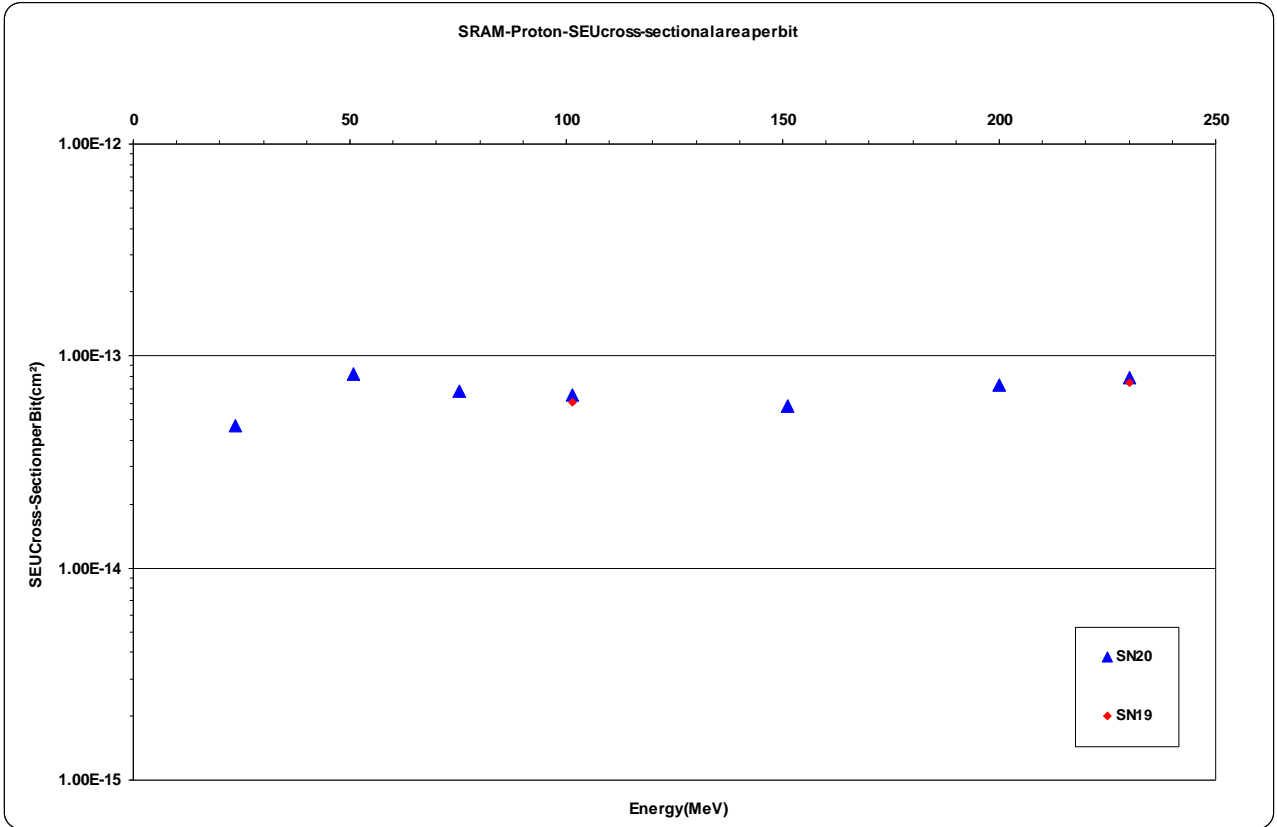


Figure71:SRAM-SEUcross-sectionalareaperbit

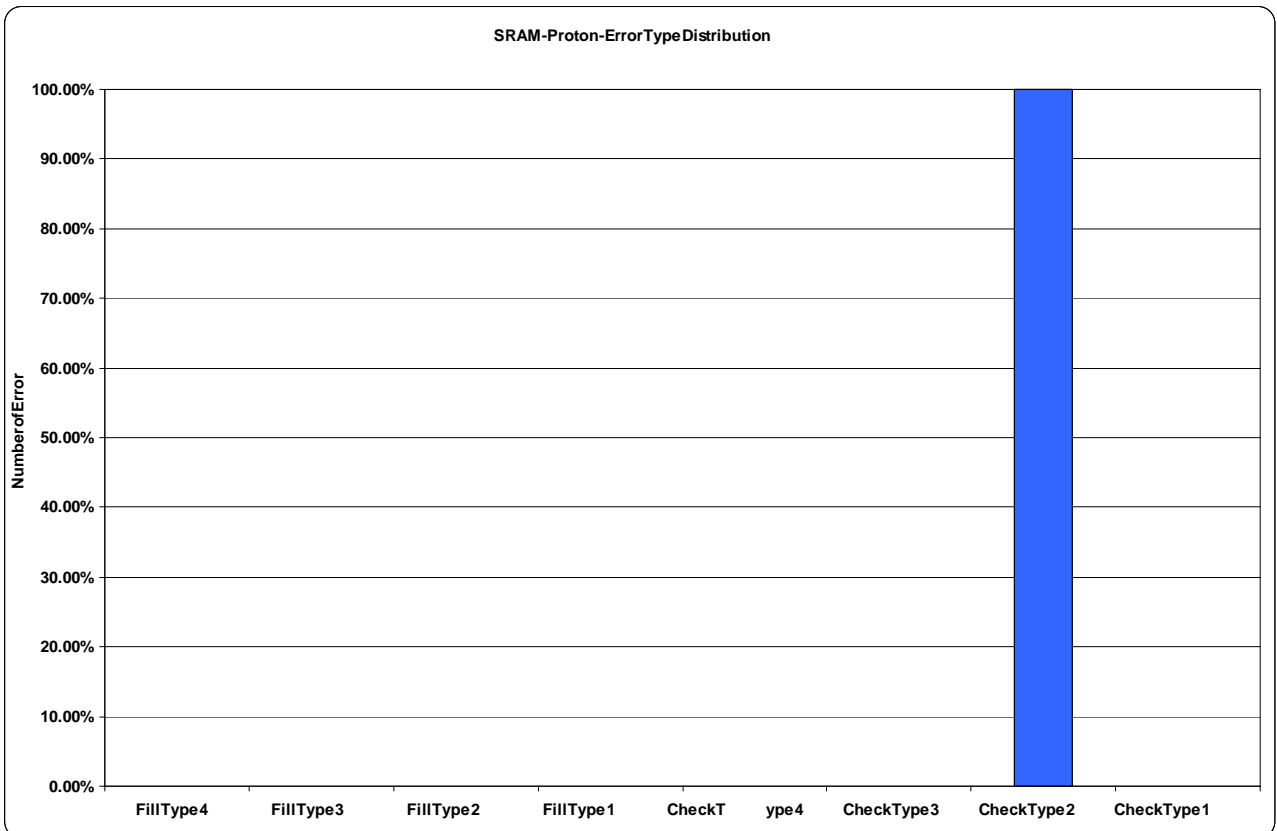


Figure72:SRAM-Errortypedistribution

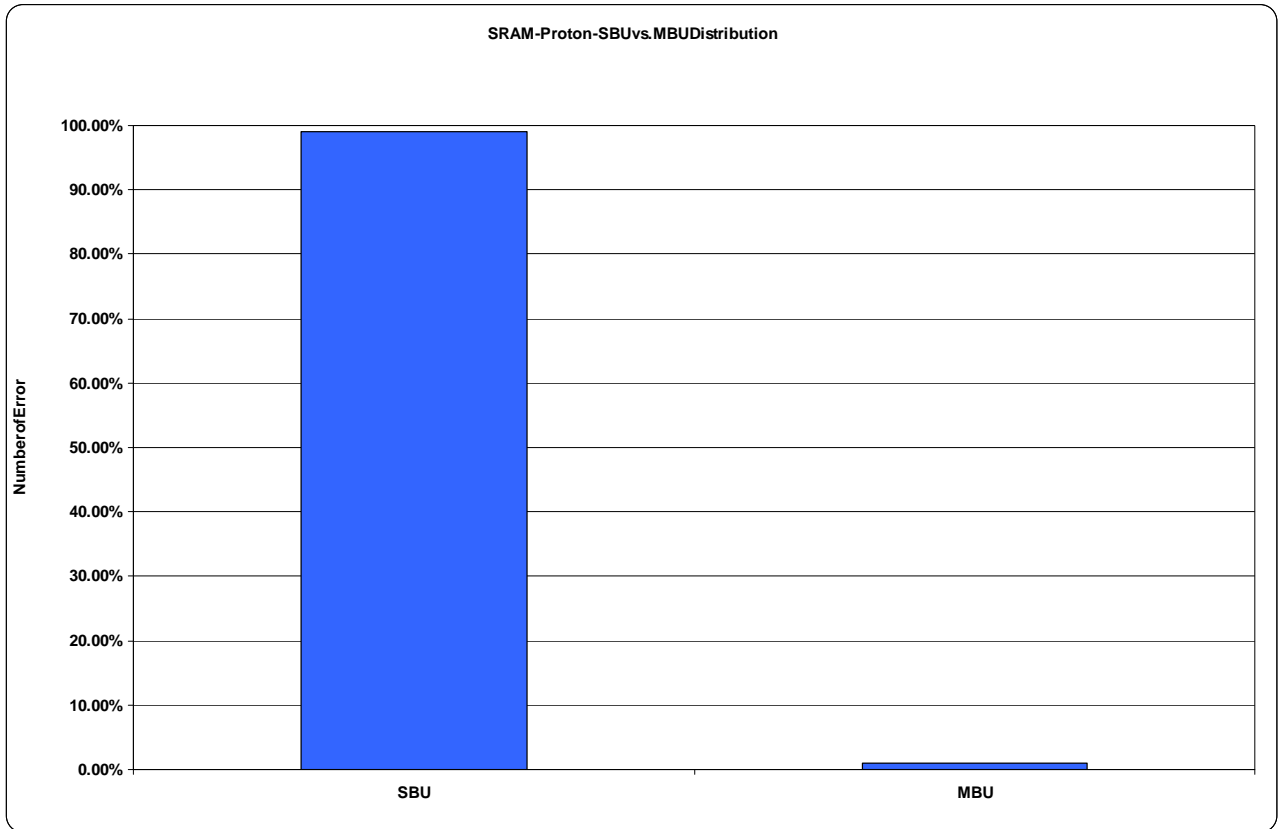


Figure73:SRAM-SBUvs.MBUDistribution

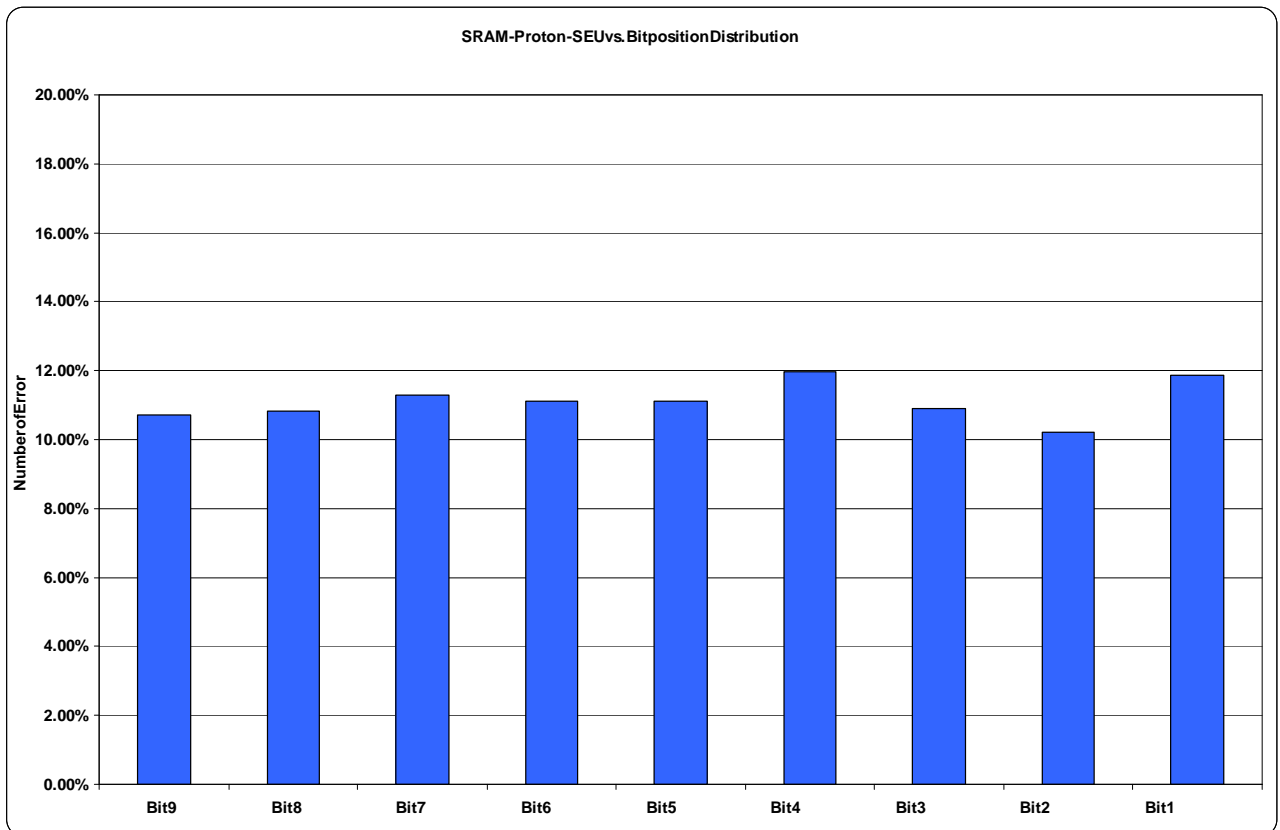


Figure74:SRAM-SEUvs.Bitpositiondistribution

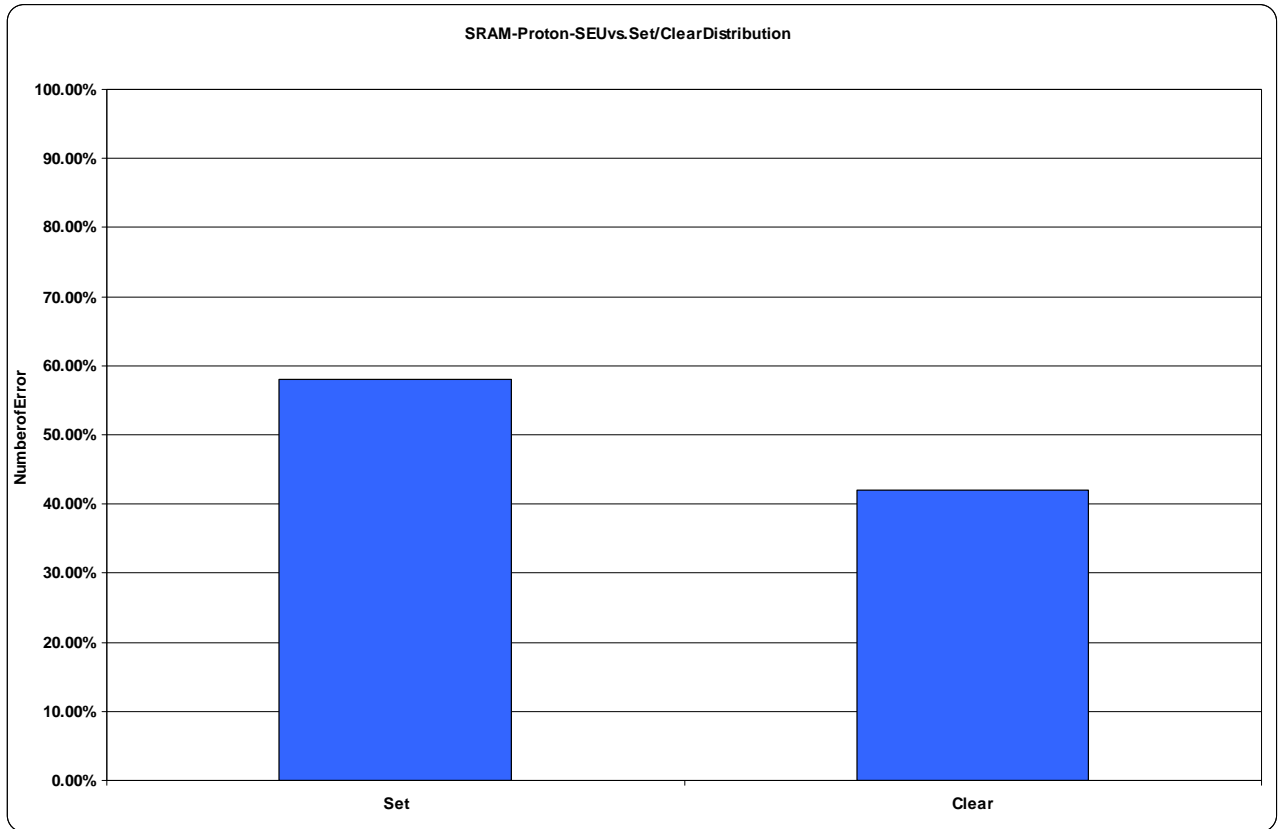


Figure75:SRAM-SEU-Set/Cleardistribution

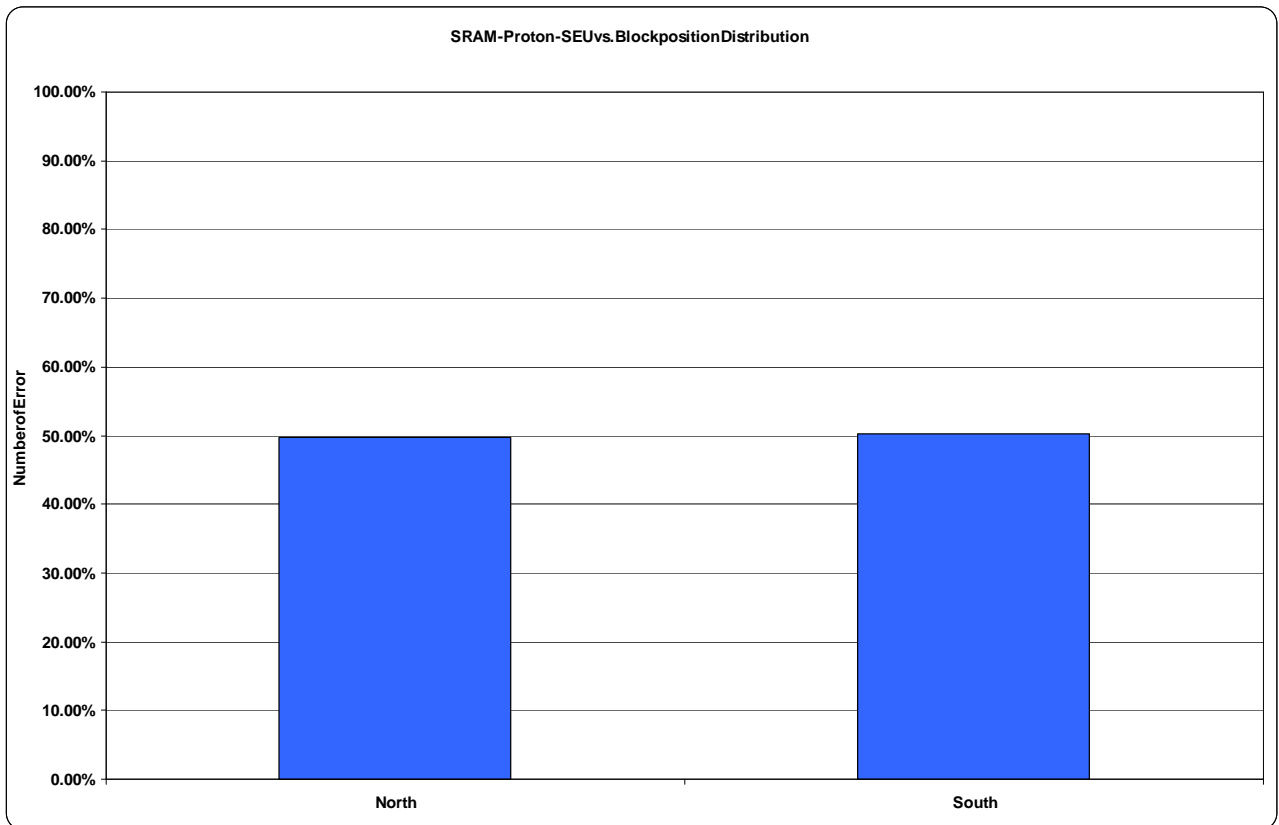


Figure76:SRAM-SEUsvs.Blockpositiondistributi on

10.5 UFROM

No error was observed (neither recorded) on the UFR OM up to an energy of 230 MeV and a total cumulated fluence of 2.03×10^{10} p/cm².

10.6 CCC/PLL

The channels clocked by the PLL output clock were not tested to proton. Neither was the CCC/PLL block.

10.7 CONFIGURATION FLASH, CHARGE PUMP & IN SYSTEM PROGRAMMING

The configuration flash is not sensitive to SEE. No additional run was performed with proton to evaluate the sensitivity of the programming part of the configuration flash.

11 CONCLUSION

The A3PE3000L flash FPGA from the ProASIC3L family from ACTEL manufacturer was SEE characterized at the following facilities under ESA ESTEC contract number 22327/09/NL/SFE:

- ✓ RADEF, University of Jyväskylä, Jyväskylä, Finland in June and November 2010.
- ✓ PIF, PSI, Villigen, Switzerland in March 2011.

SEE mitigation methods applied on the same die were also characterized and their SEE sensitivities evaluated. 2 test vehicles (TV) were designed and tested. The first TV implemented 14 shift registers, one clock conditioning circuit with phase-locked loop and 100 % of the SRAM and UFROM memories. The second TV implemented SEU and SET mitigation on 6 shift registers. All shift registers of both TVs were made of 1024 registers made of D core flip-flop with clear and enable active high.

No SEL was observed up to a LET of 55 MeV.cm²/mg, a cumulative fluence of 1 E7 p/cm², a temperature up to 125° Celsius and a bias voltage of 1.65 Volts for the core voltage and 3.6 Volts for the input/output voltage.

The flash (configuration and user) was not seen sensitive to SEE up to a LET of 55 MeV.cm²/mg. It remained intact. However, the programming part of the flash was stated sensitive to SEU, SHE and to the cumulative dose deposited by the cumulative fluence.

One SEFI was detected and recorded during the campaign at RADEF on November 2010 on the RUN112 with an effective LET of 55 MeV.cm²/mg. The device was configured with the TV2 and all shift registers were tested with a working frequency of 2 MHz. From the iteration N° 257 (a fluence of 3.69 E5 p/cm²) up to the end of the run (a fluence of 5 E5 p/cm²) all the data from the device were read at the low state ("0"). The device did not recover from the SEFI state by itself. The recovery took place after a power cycle of the device allowing the next run with the exact same condition to be performed without any more SEFI detected.

Concerning the shift registers:

- ✓ The reference and standard shift register (TV1 - SR1) SEU cross-section is characterized with an asymptotic cross-section below 3E-7 cm² per bit and a LET threshold below 1.8 MeV.cm²/mg. An extremely light influence of the working frequency can be seen on the SEU cross-section. Most errors are SBUs where almost 2/3 is due to clear transition. Some MBUs largely made of arbitrary numbers of consecutive reset bits (clear bit) were counted as well.
- ✓ The channel implementing combinational cells on the enable signal path (TV1 - SR2) results in an SEU cross-sectional area per bit similar to the reference. The frequency does not appear to influence the SEU cross-section or so lightly that it is not visible on the cross-section curve. Most errors are SBUs with more than half due to clear transition. MBUs are made of errors with the same signatures than the reference channel. However, another signature shows sun-shifted quartets caused by a SET on the enable signal caught at the active edge of the clock: data are held from shifting. Very few SETs on the enable signal were caught that way.
- ✓ The channel implementing combinational cells on the reset signal path (TV1 - SR3) results in a SEU cross-sectional area per bit characterized with an asymptotic cross-section below 1E-6 cm² and a LET threshold around 1.8 MeV.cm²/mg. This SEU cross-section per bit is higher than the reference. Almost 80% of SEUs are SBUs and 70% of those are due to clear transition. There is a high count of MBUs compared to the reference channel and almost all of those are due to arbitrary numbers of reset bits.
- ✓ The channel implementing combinational cells in-between each register (TV1 - SR4) results in an SEU cross-sectional area per bit similar to the reference. A very light influence of the working frequency can be seen on the SEU cross-section. Most errors are SBUs and 2/3 of those are due to clear transition. Comparing SEU cross-section and error signatures, this channel seems very similar to the reference one.
- ✓ The channels implementing the DDR I/O registers (TV1 - SR5 to 8) and the channels implementing LVDS buffers (TV1 - SR9 and 10) show a SEU cross-sectional area per bit very similar to the reference. SEE signatures are also like the reference ones.
- ✓ The channels clocked by the PLL output clock (TV1 - SR11 to 14) have a SEU cross-sectional area per bit identical to the reference. Most SEUs are SBUs with more than half due to clear transition. MBUs are largely attended to reset bits and flipped bits: it was not seen a total flip or stuck bit of the channel that could lead to a total or partial stop of the PLL output clock.

- ✓ The channel implementing sequential cell triplication (TV2 - SR1) results in a SEU cross-sectional area per bit characterized with an asymptotic cross-section below $2E-9 \text{ cm}^2$. There is a large difference (around 2 decades) on its SEU cross-section and the reference one. It is based on a poor statistic attended to the small number of errors. More than 70% of SEUs are SBUs and all of those are due to clear transition. The high percentage of MBU (almost 30%) compared to the reference channel is made of arbitrary numbers of reset bits. The sequential cell triplication SEU mitigation decreases the total amount of SEU and changes the SBU vs. MBU ratio. All events appearing on the channel only as asynchronous global (or local) reset signal should be considered between all registers induced all recorded SEU without any available correction from the voter.
- ✓ The channel implementing sequential cell triplication and I/O block triplication (TV2 - SR2) has a SEU cross-sectional area per bit characterized with an asymptotic cross-section below $2E-7 \text{ cm}^2$ and a LET threshold below $10 \text{ MeV.cm}^2/\text{mg}$, lower than the reference but still higher than the channel implementing only sequential cell triplication. This result seems unrealistic compared to the other channels implementing only the sequential cell triplication (TV2 SR1). Because both channels use the same sequential cell triplication as SEU mitigation, a smaller (or in the worst case an equivalent) cross-section was expected on the SR2 channel. No explanation has been found yet to explain the result on this channel.
- ✓ The channel implementing the SET filtering method with a delay of 2 ns (TV2 - SR3) has a SEU cross-sectional area per bit similar to the reference. Its SEEs signatures are also very like the reference channel.
- ✓ The channel implementing sequential cell triplication, I/O block triplication and SET filtering with a delay of 3 ns (TV2 - SR4) did not show any event up to a LET of $55 \text{ MeV.cm}^2/\text{mg}$ and accumulated fluence of $2E6 \text{ p/cm}^2$.
- ✓ The channel implementing sequential cell triplication, I/O block triplication and logic duplication (TV2 - SR5) did not show any event up to a LET of $55 \text{ MeV.cm}^2/\text{mg}$ and accumulated fluence of $2E6 \text{ p/cm}^2$.
- ✓ The channel made of full TMR mitigation (TV2 - SR6) was the source of only 2 SBUs (single bit cleared). Based on an extremely poor statistic this channel look close to the result of the channel implementing only sequential cell triplication (TV2 - SR1).
- ✓ All the channels of the TV1, expected the channels clocked with the PLL output clock were tested to proton. They all have the same proton SEU cross-section per bit measured from a low sensitivity (with a low number of errors) below $1E-13 \text{ cm}^2$ at 230 MeV .

The SRAM heavy ion SEU cross-sectional area per bit is characterized with an asymptotic cross-section around $4E-8 \text{ cm}^2$ per bit and a LET threshold below $1.8 \text{ MeV.cm}^2/\text{mg}$. The SRAM proton SEU cross-sectional area per bit is characterized with an asymptotic cross-section below $1E-13 \text{ cm}^2$ and an energy threshold below 23.5 MeV . All SEEs are upsets with a very large majority of SBUs very well balanced on bit position, on set/clear transitions and on RAM block position.

The PLL output clock never stopped. However the PLL lock signal is sensitive to PLL lock signal SEFI and those sensitivities. Because the PLL was set on a static mode to a nominal frequency of 200 MHz, increasing the gap between the nominal frequency and the working frequency increased those sensitivities. In nominal condition no any PLL lock signal SEFI was recorded on the PLL lock signal while its SET cross-sectional area based on a poor statistic attended to the small number of errors is characterized with an asymptotic cross-section below $1E-5 \text{ cm}^2$ and a LET threshold around $1.8 \text{ MeV.cm}^2/\text{mg}$.

Few remarks have to be made:

- ✓ The sequential cell and I/O block triplication mitigation methods were used on the channels 2, 4, 5 and 6 of the TV2. The yet unexplained phenomenon that influences the 2nd channel does not influence the channel 4, 5 and 6.
- ✓ TMR shift registers have a higher percentage of MBU compared to SBU than the non-mitigated shift registers.
- ✓ In the purpose to increase the SEU cross-section statistics, the total number of D core flip-flop (register) on the TV1 design could be increased. However this would have requested the usage of another TV1 design (including a higher number of register inside each shift register) or the modification of the requirements of the original test vehicle.
- ✓ The performance of the SET filtering method can only be evaluated if the SET sensitivity is evaluated (measured).
- ✓ The clock synchronization of global signals (seen on enable signal) highly reduces the probability to catch SETs appearing on the same global signals. Synchronizing the reset (clear) signal should so very probably decrease the sensitivity of SEUs induced by the SET on the global reset (clear) signal.

- ✓ The test of I/O blocks (I/O buffers and registers) would be characterized to SEE sensitivity with higher accuracy by being tested alone instead of mixed with other parts.
- ✓ The usage of SERDES module would have been of great help during the design of the shift register test system. However, requiring the output and the acquisition of the 4 last registers' output for all shift registers made it impossible. The high working frequency of SERDES system and the single data line would have greatly eased the high frequency access and the data line compensation.

12.2 SHIFTREGISTERCONDITIONSANDSEU-TABLES

Line #	SR conditions				SR - Total SEU																
	F (MHz)	Channel Mask (Hex)	Pattern	Valide	SR 1	SR 2	SR 3	SR 4	SR 5	SR 6	SR 7	SR 8	SR 9	SR 10	SR 11	SR 12	SR 13	SR 14	SR 15	SR 16	
6
7
8
9
10
11
20	100	3FFF	CKB /CKB	0	43	43	34	30	1					26	19	1	4				
21	100	3FFF	S0/S1	0	66	48	21	19					1	28	3	1	1				
22	100	3FFF	S0/S1	1	48	42	65	65	54	42	72	44	45	42	35	42	21	46			
23	100	3FFF	CKB /CKB	1	65	75	76	105	71	83	47	54	63	69	59	51	45	52			
25	150	351	CKB /CKB	1	65				27		23			56	68						
26	150	351	S0/S1	1	69				64		46			57	50						
28	200	3FF1	CKB /CKB	1	141				123	85	140	74	118	121	271	297	252	278			
29	200	3FF1	S0/S1	1	106				143	948	163	965	115	131	98	122	77	124			
33	50	3FF	CKB /CKB	1	103	113	174	123	102	122	106	97	95	102							
34	50	3FF	S0/S1	1	108	92	110	108	94	98	82	109	101	86							
35	2	3FF	CKB /CKB	1	76	79	142	58	72	92	88	79	82	91							
36
37	2	3FF	S0/S1	1	91	83	104	85	67	71	91	94	84	98							
38
40	2	3FF	CKB /CKB	1	91	93	136	168	78	92	88	79	89	72							
44	2	FFC7	CKB /CKB	1	15	15	15							103							
45	2	FFC7	S0/S1	1	5	5	5							87							
46	37.5	FFC7	CKB /CKB	1	1	1	1							88							
47	37.5	FFC7	S0/S1	1	3	3	3							105							
50	2	FFC7	CKB /CKB	1	21	21	21							101							
51	2	FFC7	CKB /CKB	1	13	13	13							92							
52	2	FFC7	S0/S1	1	2	2	2							80							
54	37.5	FFC7	CKB /CKB	1	1	1	1							127							
55	37.5	FFC7	S0/S1	1	2	2	2							96							
60	100	3BFF	CKB /CKB	0																2	
62	100	3BFF	CKB /CKB	1	95	118	195	126	90	118	97	94	89	100		85	93	91			
64	100	3FFF	S0/S1	1	115	95	142	124	84	99	101	107	81	72	119	74	76	100			
66	150	351	S0/S1	1	100				85		106			110	116						
67	150	351	CKB /CKB	1	114				51		72			120	101						
68	200	3F51	CKB /CKB	-1	81				11		2		49	71	33	27	26	31			
70	200	3F51	S0/S1	1	135				174		156		130	138	109	104	101	121			
71
72
73
74
75
78
82	100	3FFF	CKB /CKB	1											34	1	3				
83	100	3FFF	S0/S1	1																	
84	150	351	CKB /CKB	1		1														1	
85	150	351	S0/S1	1																	
86	200	??	CKB /CKB	1																	
87	200	3FF1	S0/S1	1						231		231							1		
90	100	3FFF	CKB /CKB	1											148				10		
91	100	3FFF	S0/S1	1									1								
92	150	351	CKB /CKB	1																	
93	150	351	S0/S1	1																	
94	200	3FF1	CKB /CKB	1	7				6	6	9	7	7	12	9	14	9	11			
95	200	3FF1	S0/S1	1	1					196	1	197									
96
97	2	3FF	CKB /CKB	1	59	50	116	45	57	46	58	57	62	49							
98	2	3FF	S0/S1	1	55	59	64	52	44	49	56	49	59	59							
99	50	3FF	CKB /CKB	1	57	59	83	58	51	52	51	56	63	49							
100	50	3FF	S0/S1	1	51	60	66	46	64	53	64	48	64	45							
101	100	3FFF	CKB /CKB	1	81	55	132	60	66	56	59	62	58	78	95	57	58	55			
102	100	3FFF	S0/S1	1	62	59	70	59	56	67	59	71	54	46	51	63	36	61			
104	150	351	CKB /CKB	1	73				12		24		59	75							
105	150	351	S0/S1	1	56				64		66		62	55							
106	200	3FF1	CKB /CKB	1	5				6	10	3	1	19	13	1	1	1	21			
107	200	3FF1	S0/S1	1	80				114	330	82	314	57	80	60	61	30	58			
109	2	FFC7	CKB /CKB	1																	
110	2	FFC7	S0/S1	1																	
111	37.5	FFC7	CKB /CKB	1																	
112	37.5	FFC7	S0/S1	1																	
113
114
119	2	3FF	CKB /CKB	1	46	41	69	52	64	46	52	55	53	54							
120	2	3FF	S0/S1	1	49	46	70	50	56	50	56	59	45	58							
121	50	3FF	CKB /CKB	1	58	50	80	66	56	50	65	58	58	63							
122	50	3FF	S0/S1	1	56	66	67	62	45	52	65	68	60	55							
123	100	3FFF	CKB /CKB	1	58	59	94	62	75	62	64	53	74	59	86	59	68	52			
124	100	3FFF	S0/S1	1	69	44	62	51	56	60	50	58	67	57	59	60	24	64			
125	150	351	CKB /CKB	1	71				5		29		73	64							

Line #	SR conditions				SR - Total SEU																
	F (MHz)	Channel Mask (Hex)	Pattern	Valide	SR 1	SR 2	SR 3	SR 4	SR 5	SR 6	SR 7	SR 8	SR 9	SR 10	SR 11	SR 12	SR 13	SR 14	SR 15	SR 16	
126	150	351	S0/S1	1	63				73		60		43	51							
127	200	3FF1	CKB /CKB	-1	27				1	5	1		14	33		1	3	10			
128	200	3FF1	SD/S1	1	60				113	275	81	256	65	63	67	59	39	62			
131	2	FFC7	CKB /CKB	1	9	9	9														
132	2	FFC7	SD/S1	1																	
133	37.5	FFC7	CKB /CKB	1	1	1	1														
134	37.5	FFC7	SD/S1	1																	
135	-	-	-	-																	
136	2	FFC7	CKB /CKB	1	10	10	10														
137	2	FFC7	SD/S1	1	6	6	6														
138	37.5	FFC7	CKB /CKB	1	16	16	16														
139	37.5	FFC7	SD/S1	1	9	9	9														
142	2	3FF	CKB /CKB	1	70	73	224	97	57	67	70	88	59	76							
143	2	3FF	SD/S1	1	77	76	108	69	74	60	57	66	73	57							
144	50	3FF	CKB /CKB	1	93	71	141	89	65	80	78	68	57	83							
146	50	3FF	SD/S1	1	66	90	138	70	72	71	78	64	73	79							
147	100	3FFF	CKB /CKB	1	78	76	172	99	84	71	90	91	108	81	106	95	87	117			
148	100	3FFF	SD/S1	1	83	88	141	76	80	83	81	74	77	94	60	70	60	76			
149	150	351	CKB /CKB	1	82				17		39		88	95							
150	150	351	SD/S1	1	80				92		83		77	80							
151	200	3FF1	CKB /CKB	-1	13				5	2	1		7	30	2		1	8			
152	200	3FF1	SD/S1	1	58				122	264	71	251	71	78	68	72	34	67			
153	200	3FF1	CKB /CKB	1	19				37	32	10	10	16	22	1		2	7			
154	200	3FF1	CKB /CKB	-1	224				28	28	51	5	82	234	22	18	10	72			
155	200	3FF1	CKB /CKB	-1	295				26	49	14		99	325	52	50	47	114			
156	200	3FF1	CKB /CKB	-1	666				29	11	7	3	86	553	27	25	31	88			
159	50	3FF	CKB /CKB	0	227	290	630	391	255	266	249	260	225	265							
160	50	3FF	CKB /CKB	0	586	568	1371	722	546	534	559	571	542	587							
162	50	3FF	CKB /CKB	1	79	89	189	129	164	167	235	242	81	84							
164	50	3FF	CKB /CKB	1	68	83	168	100	63	59	67	73	71	74							
165	50	3FF	CKB /CKB	1	93	80	179	131	72	65	76	61	70	73							
166	50	3FF	SD/S1	1	64	61	127	68	68	65	70	64	57	73							
167	100	3FFF	CKB /CKB	1	60	76	207	86	89	56	83	74	70	71	92	80	73	93			
168	100	3FFF	SD/S1	1	79	76	132	72	69	71	82	84	76	72	52	74	58	68			
169	150	351	CKB /CKB	1	64				9		62		92	141							
170	150	351	SD/S1	1	62				82		97		82	69							
171	200	3FF1	CKB /CKB	0	1				20	10	16		39	1	10	10	10	21			
173	200	3FF1	CKB /CKB	1	73				76	49	116	46	79	99	96	97	112	84			
174	200	3FF1	SD/S1	1	92				101	312	103	293	89	86	50	91	70	80			
178	2	FFC7	CKB /CKB	1	17	17	17														
179	2	FFC7	SD/S1	1	4	4	4														
180	37.5	FFC7	CKB /CKB	1	229	229	229														
181	37.5	FFC7	SD/S1	1																	
182	-	-	-	-																	
183	2	FFC7	CKB /CKB	1																	
184	2	FFC7	SD/S1	1																	
185	37.5	FFC7	CKB /CKB	0	3131	3131	3131														
189	2	FFC7	CKB /CKB	1																	
190	2	FFC7	SD/S1	1																	
191	37.5	FFC7	CKB /CKB	1																	
192	37.5	FFC7	SD/S1	1																	
194	2	3FF	CKB /CKB	1	60	49	74	69	59	67	52	52	54	44							
195	2	3FF	SD/S1	1	70	67	56	46	47	57	60	51	58	60							
196	50	3FF	CKB /CKB	1	54	59	79	51	53	54	60	51	55	49							
197	50	3FF	SD/S1	1	50	49	79	53	64	58	60	56	47	60							
198	100	3FFF	CKB /CKB	1	62	61	58	64	59	70	61	70	56	64	66	65	64	52			
199	100	3FFF	SD/S1	1	44	34	38	31	35	35	44	57	35	38	42	28	32	39			
201	150	351	CKB /CKB	1	74				13		25		54	75							
202	150	351	SD/S1	1	66				70		75		50	65							
203	200	3FF1	CKB /CKB	1	69				93	46	47	43	67	61	99	96	80	96			
204	200	3FF1	SD/S1	1	71				66	287	101	305	72	46	68	64	20	60			
205	-	-	-	-																	
207	-	-	-	-																	
208	2	3FF	CKB /CKB	1	7	8	11	7	12	10	8	9	10	8							
209	2	3FF	SD/S1	1	10	5	5	13	3	6	8	7	9	3							
210	50	3FF	CKB /CKB	1	9	11	11	12	11	18	8	10	9	7							
211	50	3FF	SD/S1	1	9	7	9	14	6	6	11	14	8	4							
212	100	3FFF	CKB /CKB	1	13	13	13	17	11	13	6	9	13	17	14	20	14	16			
213	100	3FFF	SD/S1	1	9	8	15	9	11	7	10	9	13	17	11	10	8	13			
214	150	351	CKB /CKB	1	15				2		8		7	12							
215	150	351	SD/S1	1	17				14		8		10	18							
216	200	3FF1	CKB /CKB	1	15				13	7	18	11	10	16	34	36	33	36			
217	200	3FF1	SD/S1	1	18				10	182	15	180	7	7	8	13	4	9			
219	2	FFC7	CKB /CKB	1																	
220	2	FFC7	SD/S1	1																	
221	37.5	FFC7	CKB /CKB	1																	
222	37.5	FFC7	SD/S1	1																	
223	-	-	-	-																	

12.3 SHIFTRREGISTERCROSS-SECTIONPERBIT-TABLE

Line #	SR - Cross-Section / Bit															
	SR 1	SR 2	SR 3	SR 4	SR 5	SR 6	SR 7	SR 8	SR 9	SR 10	SR 11	SR 12	SR 13	SR 14	SR 15	SR 16
6																
7																
8																
9																
10																
11																
20	8.398E-08	8.398E-08	6.641E-08	5.859E-08	1.953E-09					5.078E-08	3.711E-08	1.953E-09	7.813E-09			
21	1.337E-07	9.725E-08	4.255E-08	3.85E-08						5.673E-08	6.078E-09	2.026E-09	2.026E-09			
22	9.375E-08	8.203E-08	1.27E-07	1.27E-07	1.055E-07	8.203E-08	1.406E-07	8.594E-08	2.026E-09	8.789E-08	8.203E-08	6.836E-08	8.203E-08	4.102E-08	8.984E-08	
23	1.27E-07	1.465E-07	1.484E-07	2.051E-07	1.387E-07	1.621E-07	9.18E-08	1.055E-07	1.23E-07	1.348E-07	1.152E-07	9.961E-08	8.789E-08	1.016E-07		
25	1.27E-07				5.273E-08		4.492E-08			1.094E-07		1.328E-07				
26	1.15E-07				1.248E-07		8.966E-08			1.111E-07		9.746E-08				
28	1.377E-07				1.201E-07	8.301E-08	1.367E-07	7.227E-08	1.152E-07	1.182E-07	2.646E-07	2.9E-07	2.461E-07	2.715E-07		
29	1.035E-07				1.396E-07	9.258E-07	1.592E-07	9.424E-07	1.123E-07	1.279E-07	9.57E-08	1.191E-07	7.52E-08	1.211E-07		
33	1.006E-07	1.104E-07	1.699E-07	1.201E-07	9.961E-08	1.191E-07	1.035E-07	9.473E-08	9.277E-08	9.961E-08						
34	1.055E-07	8.984E-08	1.074E-07	1.055E-07	9.18E-08	9.57E-08	8.008E-08	1.064E-07	9.863E-08	8.398E-08						
35	7.422E-08	7.715E-08	1.387E-07	5.664E-08	7.031E-08	8.984E-08	8.594E-08	7.715E-08	8.008E-08	8.887E-08						
36																
37	8.887E-08	8.105E-08	1.016E-07	8.301E-08	6.543E-08	6.934E-08	8.887E-08	9.18E-08	8.203E-08	9.57E-08						
38																
40	8.887E-08	9.082E-08	1.328E-07	1.641E-07	7.617E-08	8.984E-08	8.594E-08	7.715E-08	8.691E-08	7.031E-08						
44	4.883E-09	4.883E-09	4.883E-09				3.353E-08									
45	1.628E-09	1.628E-09	1.628E-09				2.832E-08									
46	3.255E-10	3.255E-10	3.255E-10				2.865E-08									
47	9.766E-10	9.766E-10	9.766E-10				3.418E-08									
50	6.836E-09	6.836E-09	6.836E-09				3.288E-08									
51	4.232E-09	4.232E-09	4.232E-09				2.995E-08									
52	6.51E-10	6.51E-10	6.51E-10				2.604E-08									
54	3.255E-10	3.255E-10	3.255E-10				4.134E-08									
55	6.51E-10	6.51E-10	6.51E-10				3.125E-08									
60														1.713E-06		
62	9.277E-08	1.152E-07	1.904E-07	1.23E-07	8.789E-08	1.152E-07	9.473E-08	9.18E-08	8.691E-08	9.766E-08		8.301E-08	9.082E-08	8.887E-08		
64	1.123E-07	9.277E-08	1.387E-07	1.211E-07	8.203E-08	9.668E-08	9.863E-08	1.045E-07	7.91E-08	7.031E-08	1.162E-07	7.227E-08	7.422E-08	9.766E-08		
66	9.766E-08				8.301E-08		1.035E-07		1.074E-07	1.133E-07						
67	1.113E-07				4.98E-08		7.031E-08		1.172E-07	9.863E-08						
69	7.91E-08				1.074E-08		1.953E-09		4.785E-08	6.934E-08	3.223E-08	2.637E-08	2.539E-08	3.027E-08		
70	1.318E-07				1.699E-07		1.523E-07		1.27E-07	1.348E-07	1.064E-07	1.016E-07	9.863E-08	1.182E-07		
71																
72																
73																
74																
75																
78																
82											1.652E-08	4.859E-10	1.458E-09			
83		4.859E-10											4.859E-10			
84																
85																
86																
87						1.128E-07		1.128E-07					4.883E-10			
90											7.191E-08		4.859E-09			
91									4.883E-10							
92																
93																
94	3.401E-09				2.915E-09	2.915E-09	4.373E-09	3.401E-09	3.401E-09	5.63E-09	4.373E-09	6.802E-09	4.373E-09	5.344E-09		
95	4.883E-10					9.57E-08	4.883E-10	9.619E-08								
96																
97	5.762E-08	4.883E-08	1.133E-07	4.395E-08	5.566E-08	4.492E-08	5.664E-08	5.566E-08	6.055E-08	4.785E-08						
98	5.371E-08	5.762E-08	6.25E-08	5.078E-08	4.297E-08	4.785E-08	5.469E-08	4.785E-08	5.762E-08	5.762E-08						
99	5.566E-08	5.762E-08	8.105E-08	5.664E-08	4.98E-08	5.078E-08	4.98E-08	5.469E-08	6.152E-08	4.785E-08						
100	4.98E-08	5.859E-08	6.445E-08	4.492E-08	6.25E-08	5.176E-08	6.25E-08	4.888E-08	6.25E-08	4.395E-08						
101	7.91E-08	5.371E-08	1.289E-07	5.859E-08	6.445E-08	5.469E-08	5.762E-08	6.055E-08	5.664E-08	7.617E-08	9.277E-08	5.566E-08	5.664E-08	5.371E-08		
102	6.055E-08	5.762E-08	6.836E-08	5.762E-08	5.469E-08	6.543E-08	5.762E-08	6.934E-08	5.273E-08	4.492E-08	4.98E-08	6.152E-08	3.516E-08	5.957E-08		
104	7.129E-08				1.172E-08		2.344E-08		5.762E-08	7.324E-08						
105	5.469E-08				6.25E-08		6.445E-08		6.055E-08	5.371E-08						
106	4.883E-08				5.859E-09	9.766E-09	2.93E-09	9.766E-10	1.855E-08	1.27E-08	9.766E-10	9.766E-10	9.766E-10	2.051E-08		
107	7.813E-08				1.113E-07	3.223E-07	8.008E-08	3.066E-07	5.566E-08	7.813E-08	5.859E-08	5.957E-08	2.93E-08	5.664E-08		
109							1.66E-08									
110							1.693E-08									
111							1.595E-08									
112							1.66E-08									
113																
114																
119	4.492E-08	4.004E-08	6.738E-08	5.078E-08	6.25E-08	4.492E-08	5.078E-08	5.371E-08	5.176E-08	5.273E-08						
120	4.785E-08	4.492E-08	6.836E-08	4.883E-08	5.469E-08	4.883E-08	5.469E-08	5.762E-08	4.395E-08	5.664E-08						
121	5.664E-08	4.883E-08	7.813E-08	6.445E-08	5.469E-08	4.883E-08	6.348E-08	5.664E-08	5.664E-08	6.152E-08						
122	5.469E-08	6.445E-08	6.543E-08	6.055E-08	4.395E-08	5.078E-08	6.348E-08	6.641E-08	5.859E-08	5.371E-08						
123	5.664E-08	5.762E-08	9.18E-08	6.055E-08	7.324E-08	6.055E-08	6.25E-08	5.176E-08	7.227E-08	5.762E-08	8.398E-08	5.762E-08	6.641E-08	5.078E-08		
124	6.738E-08	4.297E-08	6.055E-08	4.98E-08	5.469E-08	5.859E-08	4.883E-08	5.664E-08	6.543E-08	5.566E-08	5.762E-08	5.859E-08	2.344E-08	6.25E-08		
125	6.934E-08				4.883E-09		2.632E-08		7.129E-08	6.25E-08						

12.4 SRAMCONDITIONSANDSEU-TABLES

Line #	SRAM conditions						Fill Error Type				Check Error Type				SEU	Cross-Section (Bit)			
	F (MHz)	Start Address	Stop Address	Mask (Hex)	# Bit Eff	Pattern	Valide	4	3	2	1	4	3	2			1	SCU	MCU
6	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
7	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
8	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
9	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
10	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
11	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
20	20	0	16383	1FF	294912	CKB /CKB	0	0	0	0	0	0	0	360	0	355	5	360	2.44E-09
21	20	0	16383	1FF	294912	S0 S1	0	0	0	0	0	0	0	426	0	425	1	426	3.00E-09
22	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	3902	0	3896	6	3902	2.65E-08
23	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	4004	0	3995	9	4004	2.72E-08
25	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
26	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
28	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	8650	0	8633	17	8650	2.93E-08
29	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	9082	0	8914	168	9082	3.08E-08
33	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	7771	0	7769	2	7771	2.64E-08
34	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	7679	0	7678	1	7679	2.60E-08
35	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	7236	0	7221	15	7236	2.45E-08
36	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
37	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	7220	0	7218	2	7220	2.45E-08
38	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	7372	0	7366	6	7372	2.50E-08
40	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	6851	0	6796	55	6851	2.32E-08
44	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
45	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
46	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
47	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
50	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
51	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
52	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
54	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
55	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
60	20	0	16383	1FF	294912	CKB /CKB	0	0	0	0	0	0	0	0	0	0	0	0	0.00E+00
62	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	7725	0	7698	27	7725	2.62E-08
64	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	7670	0	7644	26	7670	2.60E-08
66	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	7908	0	7881	27	7908	2.68E-08
67	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	8542	0	8311	231	8542	2.90E-08
69	20	0	16383	1FF	294912	CKB /CKB	0	0	0	0	0	0	0	475	0	472	3	475	1.61E-09
70	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	8299	0	8275	24	8299	2.81E-08
71	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
72	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
73	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
74	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
75	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
78	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
82	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	2181	0	2179	2	2181	3.68E-09
83	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	2240	0	2239	1	2240	3.78E-09
84	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	2253	0	2251	2	2253	3.82E-09
85	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	2334	0	2331	3	2334	3.94E-09
86	20	??	??	??	??	??	0	-	-	-	-	-	-	-	-	-	-	0	-
87	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	2353	0	2351	2	2353	3.99E-09
90	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	2319	0	2318	1	2319	3.91E-09
91	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	2265	0	2263	2	2265	3.84E-09
92	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	2384	0	2384	0	2384	4.02E-09
93	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	2396	0	2389	7	2396	4.04E-09
94	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	3585	0	3578	7	3585	6.05E-09
95	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	2535	0	2531	4	2535	4.30E-09
96	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
97	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	5299	0	5298	1	5299	1.80E-08
98	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	5297	0	5296	1	5297	1.80E-08
99	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	5528	0	5525	3	5528	1.87E-08
100	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	5258	0	5256	2	5258	1.78E-08
101	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
102	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
104	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
105	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
106	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
107	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
109	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
110	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
111	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
112	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
113	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
114	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
119	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	5215	0	5212	3	5215	1.77E-08
120	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	5146	0	5139	7	5146	1.74E-08
121	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	5396	0	5386	10	5396	1.83E-08
122	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	5321	0	5318	3	5321	1.80E-08
123	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
124	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
125	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-

Line #	SRAM conditions					# Bit Eff	Pattern	Valide	Fill Error Type				Check Error Type				SCU	MCU	SEU	Cross-Section (Bit)
	F (MHz)	Start Address	Stop Address	Mask (Hex)					4	3	2	1	4	3	2	1				
126	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
127	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
128	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
131	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
132	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
133	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
134	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
135	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
136	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
137	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
138	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
139	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
142	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	5113	0	5101	12	5113	3.47E-08	
143	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	5162	0	5159	3	5162	3.50E-08	
144	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	5196	0	5182	14	5196	3.52E-08	
146	20	0	16383	1FF	294912	FS0 FS1	1	0	0	0	0	0	0	7255	0	7244	11	7255	4.92E-08	
147	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
148	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
149	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
150	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
151	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
152	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
153	-	-	-	-	0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
154	-	-	-	-	0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
155	-	-	-	-	0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
156	-	-	-	-	0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
159	20	-	-	-	0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
160	20	-	-	-	0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
162	20	-	-	-	0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
164	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	5094	0	5002	92	5094	3.45E-08	
165	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	5117	0	5099	18	5117	3.47E-08	
166	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	4856	0	4848	8	4856	3.29E-08	
167	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
168	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
169	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
170	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
171	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
173	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
174	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
178	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
179	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
180	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
181	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
182	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
183	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
184	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
185	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
189	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
190	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
191	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
192	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
194	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	6909	0	6905	4	6909	1.17E-08	
195	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	6943	0	6941	2	6943	1.18E-08	
196	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	7300	0	7293	7	7300	1.24E-08	
197	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	7141	0	7139	2	7141	1.21E-08	
198	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
199	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
201	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
202	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
203	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
204	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
205	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
207	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
208	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	3355	0	3350	5	3355	5.69E-09	
209	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	3378	0	3362	16	3378	5.73E-09	
210	20	0	16383	1FF	294912	CKB /CKB	1	0	0	0	0	0	0	3584	0	3584	0	3584	6.08E-09	
211	20	0	16383	1FF	294912	S0 S1	1	0	0	0	0	0	0	3556	0	3553	3	3556	6.03E-09	
212	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
213	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
214	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
215	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
216	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
217	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
219	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
220	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
221	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
222	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
223	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	

12.5 UFROM/PLL-TABLES

Line #	UFROM		PLL			
	F (MHz)	SEU	SET	SEFI	Cross-Section	
					SET	SEFI
6	-	-	-	-	-	-
7	-	-	-	-	-	-
8	-	-	-	-	-	-
9	-	-	-	-	-	-
10	-	-	-	-	-	-
11	-	-	-	-	-	-
20	10	0	0	0	0	0
21	10	0	0	0	0	0
22	10	0	0	1	0	2E-06
23	10	0	3	0	6E-06	0
25	-	-	0	0	0	0
26	-	-	0	0	0	0
28	10	0	0	0	0	0
29	10	0	0	0	0	0
33	10	0	-	-	-	-
34	10	0	-	-	-	-
35	10	0	-	-	-	-
36	-	-	-	-	-	-
37	10	0	-	-	-	-
38	10	0	-	-	-	-
40	10	0	-	-	-	-
44	-	-	-	-	-	-
45	-	-	-	-	-	-
46	-	-	-	-	-	-
47	-	-	-	-	-	-
50	-	-	-	-	-	-
51	-	-	-	-	-	-
52	-	-	-	-	-	-
54	-	-	-	-	-	-
55	-	-	-	-	-	-
60	10	0	0	0	0	0
62	10	0	1	0	1E-06	0
64	10	0	2	0	2E-06	0
66	10	0	2	0	2E-06	0
67	10	0	2	1	2E-06	1E-06
69	10	0	0	0	0	0
70	10	0	3	0	3E-06	0
71	-	-	-	-	-	-
72	-	-	-	-	-	-
73	-	-	-	-	-	-
74	-	-	-	-	-	-
75	-	-	-	-	-	-
78	-	-	-	-	-	-
82	10	0	0	0	0	0
83	10	0	0	0	0	0
84	10	0	0	0	0	0
85	10	0	0	0	0	0
86	10	0	??	??	??	??
87	10	0	0	0	0	0
90	10	0	0	0	0	0
91	10	0	0	0	0	0
92	10	0	0	0	0	0
93	10	0	0	0	0	0
94	10	0	1	0	5E-07	0
95	10	0	0	0	0	0
96	-	-	-	-	-	-
97	10	0	-	-	-	-
98	10	0	-	-	-	-
99	10	0	-	-	-	-
100	10	0	-	-	-	-
101	-	-	1	0	1E-06	0
102	-	-	1	0	1E-06	0
104	-	-	2	1	2E-06	1E-06
105	-	-	1	0	1E-06	0
106	-	-	0	0	0	0
107	-	-	1	0	1E-06	0
109	-	-	-	-	-	-
110	-	-	-	-	-	-
111	-	-	-	-	-	-
112	-	-	-	-	-	-
113	-	-	-	-	-	-
114	-	-	-	-	-	-
119	10	0	-	-	-	-
120	10	0	-	-	-	-
121	10	0	-	-	-	-
122	10	0	-	-	-	-
123	-	-	2	0	2E-06	0
124	-	-	2	1	2E-06	1E-06
125	-	-	1	0	1E-06	0

Line #	UFROM		PLL			
	F (MHz)	SEU	SET	SEFI	Cross-Section	
					SET	SEFI
126	-	-	1	0	1E-06	0
127	-	-	0	0	0	0
128	-	-	0	0	0	0
131	-	-	-	-	-	-
132	-	-	-	-	-	-
133	-	-	-	-	-	-
134	-	-	-	-	-	-
135	-	-	-	-	-	-
136	-	-	-	-	-	-
137	-	-	-	-	-	-
138	-	-	-	-	-	-
139	-	-	-	-	-	-
142	10	0	-	-	-	-
143	10	0	-	-	-	-
144	10	0	-	-	-	-
146	10	0	-	-	-	-
147	-	-	1	0	2E-06	0
148	-	-	5	0	1.00E-05	0
149	-	-	3	0	6E-06	0
150	-	-	2	0	4E-06	0
151	-	-	0	0	0	0
152	-	-	0	0	0	0
153	-	-	0	0	0	0
154	-	-	1	0	2E-07	0
155	-	-	0	0	0	0
156	-	-	0	0	0	0
159	10	0	-	-	-	-
160	10	0	-	-	-	-
162	10	0	-	-	-	-
164	10	0	-	-	-	-
165	10	0	-	-	-	-
166	10	0	-	-	-	-
167	-	-	4	0	8E-06	0
168	-	-	2	0	4E-06	0
169	-	-	4	0	8E-06	0
170	-	-	0	0	0	0
171	-	-	0	0	0	0
173	-	-	1	0	2E-06	0
174	-	-	0	0	0	0
178	-	-	-	-	-	-
179	-	-	-	-	-	-
180	-	-	-	-	-	-
181	-	-	-	-	-	-
182	-	-	-	-	-	-
183	-	-	-	-	-	-
184	-	-	-	-	-	-
185	-	-	-	-	-	-
189	-	-	-	-	-	-
190	-	-	-	-	-	-
191	-	-	-	-	-	-
192	-	-	-	-	-	-
194	10	0	-	-	-	-
195	10	0	-	-	-	-
196	10	0	-	-	-	-
197	10	0	-	-	-	-
198	-	-	2	0	1E-06	0
199	-	-	1	0	5E-07	0
201	-	-	0	0	0	0
202	-	-	0	0	0	0
203	-	-	0	0	0	0
204	-	-	1	0	5E-07	0
205	-	-	-	-	-	-
207	-	-	-	-	-	-
208	10	0	-	-	-	-
209	10	0	-	-	-	-
210	10	0	-	-	-	-
211	10	0	-	-	-	-
212	-	-	0	0	0	0
213	-	-	0	0	0	0
214	-	-	0	0	0	0
215	-	-	0	0	0	0
216	-	-	0	0	0	0
217	-	-	0	0	0	0
219	-	-	-	-	-	-
220	-	-	-	-	-	-
221	-	-	-	-	-	-
222	-	-	-	-	-	-
223	-	-	-	-	-	-

12.6 **CONFIGURATION-TABLE**

CONFIGURATION			
Line #	Configuration step	Result	Details
7	All	Failed	Exit 11 - Verify 0 failed at row 7419
8	All	Failed	Exit 11 - Verify 1 failed at row 3173
9	Erasing	Passed	
10	Programming	Failed	Exit 11 - Verify 0 failed at row 6166
11	Verifying	Failed	Exit 11 - Verify 0 failed at row 7246
71	All	Failed	Exit 11 - Verify 0 failed at row 7033
72	Erasing	Failed	Exit -24 - Failed to program UROW
73	Programming	Failed	Exit 11 - Failed to verify FlashROM at row 7
75	Verifying	Failed	Exit 11 - Verify 0 failed at row 7534
113	All	Failed	Exit 11 - Verify 0 failed at row 7843
114	Erasing	Failed	Exit -24 - Failed to program UROW
205	All	Failed	Exit 8 - Failed Erase Operation
223	All	Failed	Exit 8 - Failed Erase Operation

13.2 **SHIFTREGISTERCONDITIONSANDSEU-TABLES**

Line #	SR conditions					SR - Total SEU															
	F (MHz)	Channel Mask (Hex)	Reading ratio	Pattern	Valide	SR 1	SR 2	SR 3	SR 4	SR 5	SR 6	SR 7	SR 8	SR 9	SR 10	SR 11	SR 12	SR 13	SR 14	SR 15	SR 16
28	2	3FF	4/4	A-5	1	44	46	56	41	51	48	51	34	48	39	0	0	0	0	0	0
30	50	3FF	4/4	A-5	1	53	32	43	39	47	42	42	37	35	55	0	0	0	0	0	0
33	100	3FF	4/4, 1/4	A-5	1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
34	100	3FF	4/4	A-5	1	112	106	120	122	93	87	104	103	72	75	0	0	0	0	0	0
37	150	3FF	4/4	A-5	1	92	101	126	117	103	103	103	116	105	0	0	0	0	0	0	0
38	150	3FF	4/4	A	1	98	118	129	105	95	98	85	87	88	95	0	0	0	0	0	0
39	150	3FF	4/4	A	1	112	112	170	112	125	144	105	106	131	142	0	0	0	0	0	0
40	150	3FF	4/4	A	1	61	65	75	54	64	64	71	70	64	71	0	0	0	0	0	0
49	200	3B9	4/4	A	1	69	0	0	52	56	34	0	43	46	62	0	0	0	0	0	0
50	200	3B9	1/4	A	1	108	0	0	115	99	82	0	66	129	109	0	0	0	0	0	0
65	2	FFFF	4/4	A	1	2	2	2	50	50	50	60	0	0	0	0	0	0	0	0	0
66	50	FFFF	4/4	A	1	0	0	0	75	75	75	59	0	0	0	0	0	0	1	1	1
67	50	FFFF	1/4	A	1	1	1	1	109	109	109	84	0	0	0	0	0	0	0	0	0
68	70	FC7F	1/4	A	1	2	2	2	46	46	46	62	0	0	0	0	0	0	0	0	0
70	70	FC7F	1/4	A	1	0	0	0	49	49	49	56	0	0	0	0	0	0	0	0	0
71	50	FFFF	1/4	A	1	0	0	0	50	50	50	53	0	0	0	0	0	0	0	0	0
72	2	FFFF	1/4	A	1	0	0	0	49	49	49	40	0	0	0	0	0	0	0	0	0
73	70	FC7F	1/4	A	1	0	0	0	48	48	48	64	0	0	0	0	0	0	0	0	0
75	2	3FF	1/4	A	1	58	63	59	52	58	55	57	59	50	44	0	0	0	0	0	0
76	50	3FF	1/4	A	1	63	51	68	63	55	45	44	40	54	55	0	0	0	0	0	0
77	100	3FF	1/4	A	1	57	48	72	68	52	57	65	54	72	60	0	0	0	0	0	0
78	150	3FF	1/4	A	1	68	61	63	77	68	68	68	68	50	63	0	0	0	0	0	0
80	200	3B9	1/4	A	1	73	0	0	86	53	41	0	29	62	59	0	0	0	0	0	0
84	200	3B9	1/4	A	1	81	0	0	112	91	81	0	59	105	71	0	0	0	0	0	0
86	150	3FF	1/4	A	1	84	83	166	88	97	98	87	87	94	70	0	0	0	0	0	0
87	100	3FF	1/4	A	1	87	87	178	88	59	77	64	72	79	73	0	0	0	0	0	0
88	50	3FF	1/4	A	1	82	74	114	89	71	66	86	73	81	88	0	0	0	0	0	0
92	50	3FF	1/4	A	1	77	81	182	84	68	70	73	75	89	95	0	0	0	0	0	0
93	2	3FF	1/4	A	1	63	84	106	83	66	77	71	80	75	64	0	0	0	0	0	0
115	2	FFFF	1/4	A	-1	1	1	1	19	19	19	11	0	0	0	0	0	0	0	0	0
116	2	FFFF	1/4	A	1	0	0	0	89	89	89	76	0	0	0	0	0	0	0	0	0
117	50	FFFF	1/4	A	1	2	2	2	158	158	158	100	0	0	0	0	0	0	1	1	1
118	70	FC7F	1/4	A	1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
128	70	FC7F	1/4	A	1	0	0	0	48	48	48	53	0	0	0	0	0	0	0	0	0
130	50	FFFF	1/4	A	1	0	0	0	62	62	62	74	0	0	0	0	0	0	0	0	0
131	2	FFFF	1/4	A	1	0	0	0	51	51	51	46	0	0	0	0	0	0	0	0	0
135	-	-	-	-	0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
136	2	3FF	1/4	A	1	55	58	59	53	76	71	53	52	56	57	0	0	0	0	0	0
137	50	3FF	1/4	A	1	48	59	54	57	73	69	58	53	48	67	0	0	0	0	0	0
138	100	3FF	1/4	A	1	62	60	64	70	68	68	68	47	50	69	0	0	0	0	0	0
139	150	3FF	1/4	A	1	67	58	67	67	78	79	63	63	67	72	0	0	0	0	0	0
147	200	3A1	1/4	A	1	68	0	0	447	220	64	0	66	75	66	0	0	0	0	0	0
148	-	-	-	-	1	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
155	2	3FF	1/4	A	1	9	8	10	8	11	9	5	9	6	13	0	0	0	0	0	0
156	50	3FF	1/4	A	1	12	5	10	8	14	12	6	8	10	9	0	0	0	0	0	0
157	150	3FF	1/4	A	1	9	7	6	20	14	14	12	12	9	13	0	0	0	0	0	0
158	150	3FF	1/4	A	1	16	9	7	13	15	15	21	21	12	9	0	0	0	0	0	0
159	200	1B1	1/4	A	1	0	0	0	6	0	0	0	0	0	12	0	0	0	0	0	0
163	2	FFC7	1/4	A	1	0	0	0	0	0	0	8	0	0	0	0	0	0	0	0	0
164	50	FFC7	1/4	A	1	0	0	0	0	0	0	11	0	0	0	0	0	0	0	0	0
166	70	E047	1/4	A	1	0	0	0	0	0	0	15	0	0	0	0	0	0	0	0	0
167	-	-	-	-	1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0

13.3 SHIFTREGISTERCROSS-SECTIONPERBIT-TABLE

Line #	SR - Cross-Section / Bit															
	SR 1	SR 2	SR 3	SR 4	SR 5	SR 6	SR 7	SR 8	SR 9	SR 10	SR 11	SR 12	SR 13	SR 14	SR 15	SR 16
28	6.54E-08	8.93E-08	1.09E-07	7.96E-08	9.90E-08	9.32E-08	9.90E-08	6.60E-08	9.32E-08	7.57E-08	-	-	-	-	-	-
30	1.01E-07	6.13E-08	8.23E-08	7.47E-08	9.00E-08	8.04E-08	8.04E-08	7.08E-08	6.70E-08	1.05E-07	-	-	-	-	-	-
33	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
34	1.09E-07	1.03E-07	1.17E-07	1.19E-07	9.06E-08	8.48E-08	1.01E-07	1.00E-07	7.02E-08	7.31E-08	-	-	-	-	-	-
37	8.97E-08	9.84E-08	1.23E-07	1.14E-07	1.00E-07	1.00E-07	1.00E-07	1.00E-07	1.13E-07	1.02E-07	-	-	-	-	-	-
38	9.55E-08	1.15E-07	1.26E-07	1.02E-07	9.26E-08	9.55E-08	8.28E-08	8.48E-08	8.58E-08	9.26E-08	-	-	-	-	-	-
39	1.09E-07	1.09E-07	1.66E-07	1.09E-07	1.22E-07	1.40E-07	1.02E-07	1.03E-07	1.28E-07	1.38E-07	-	-	-	-	-	-
40	8.77E-08	9.34E-08	1.08E-07	7.76E-08	9.20E-08	9.20E-08	1.02E-07	1.01E-07	9.20E-08	1.02E-07	-	-	-	-	-	-
49	1.12E-07	-	-	8.45E-08	9.10E-08	5.52E-08	-	6.99E-08	7.47E-08	1.01E-07	-	-	-	-	-	-
50	1.05E-07	-	-	1.12E-07	9.65E-08	7.99E-08	-	6.43E-08	1.26E-07	1.06E-07	-	-	-	-	-	-
65	9.95E-10	9.95E-10	9.95E-10	2.49E-08	2.49E-08	2.49E-08	8.94E-08	-	-	-	-	-	-	-	-	-
66	-	-	-	3.74E-08	3.74E-08	3.74E-08	8.82E-08	-	-	-	-	-	-	4.99E-10	4.99E-10	4.99E-10
67	5.00E-10	5.00E-10	5.00E-10	5.45E-08	5.45E-08	5.45E-08	1.26E-07	-	-	-	-	-	-	-	-	-
68	1.01E-09	1.01E-09	1.01E-09	2.32E-08	2.32E-08	2.32E-08	9.37E-08	-	-	-	-	-	-	-	-	-
70	-	-	-	1.88E-08	1.88E-08	1.88E-08	6.43E-08	-	-	-	-	-	-	-	-	-
71	-	-	-	1.45E-08	1.45E-08	1.45E-08	4.61E-08	-	-	-	-	-	-	-	-	-
72	-	-	-	1.59E-08	1.59E-08	1.59E-08	3.90E-08	-	-	-	-	-	-	-	-	-
73	-	-	-	1.56E-08	1.56E-08	1.56E-08	6.24E-08	-	-	-	-	-	-	-	-	-
75	5.65E-08	6.14E-08	5.75E-08	5.07E-08	5.65E-08	5.36E-08	5.56E-08	5.75E-08	4.87E-08	4.29E-08	-	-	-	-	-	-
76	6.14E-08	4.97E-08	6.63E-08	6.14E-08	5.36E-08	4.39E-08	4.29E-08	3.90E-08	5.26E-08	5.36E-08	-	-	-	-	-	-
77	5.56E-08	4.88E-08	7.02E-08	6.63E-08	5.07E-08	5.56E-08	6.34E-08	5.26E-08	7.02E-08	5.85E-08	-	-	-	-	-	-
78	6.63E-08	5.95E-08	6.14E-08	7.50E-08	6.63E-08	6.63E-08	6.63E-08	6.63E-08	4.87E-08	6.14E-08	-	-	-	-	-	-
80	7.12E-08	-	-	8.38E-08	5.17E-08	4.00E-08	-	2.83E-08	6.04E-08	5.75E-08	-	-	-	-	-	-
84	1.58E-07	-	-	2.18E-07	1.77E-07	1.58E-07	-	1.15E-07	2.05E-07	1.38E-07	-	-	-	-	-	-
86	1.63E-07	1.61E-07	3.23E-07	1.71E-07	1.89E-07	1.91E-07	1.69E-07	1.69E-07	1.83E-07	1.36E-07	-	-	-	-	-	-
87	1.70E-07	1.70E-07	3.47E-07	1.72E-07	1.15E-07	1.50E-07	1.25E-07	1.40E-07	1.54E-07	1.42E-07	-	-	-	-	-	-
88	1.60E-07	1.44E-07	2.22E-07	1.73E-07	1.38E-07	1.29E-07	1.68E-07	1.42E-07	1.58E-07	1.72E-07	-	-	-	-	-	-
92	1.50E-07	1.58E-07	3.54E-07	1.63E-07	1.32E-07	1.36E-07	1.42E-07	1.46E-07	1.73E-07	1.85E-07	-	-	-	-	-	-
93	1.23E-07	1.64E-07	2.07E-07	1.62E-07	1.29E-07	1.50E-07	1.38E-07	1.56E-07	1.46E-07	1.25E-07	-	-	-	-	-	-
115	6.51E-10	6.51E-10	6.51E-10	1.24E-08	1.24E-08	1.24E-08	2.14E-08	-	-	-	-	-	-	-	-	-
116	-	-	-	5.78E-08	5.78E-08	5.78E-08	1.48E-07	-	-	-	-	-	-	-	-	-
117	1.30E-09	1.30E-09	1.30E-09	1.03E-07	1.03E-07	1.03E-07	1.95E-07	-	-	-	-	-	-	6.49E-10	6.49E-10	6.49E-10
118	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
128	-	-	-	7.81E-09	7.81E-09	7.81E-09	2.58E-08	-	-	-	-	-	-	-	-	-
130	-	-	-	1.01E-08	1.01E-08	1.01E-08	3.61E-08	-	-	-	-	-	-	-	-	-
131	-	-	-	8.30E-09	8.30E-09	8.30E-09	2.24E-08	-	-	-	-	-	-	-	-	-
135	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
136	2.68E-08	2.83E-08	2.88E-08	2.58E-08	3.70E-08	3.46E-08	2.58E-08	2.53E-08	2.73E-08	2.78E-08	-	-	-	-	-	-
137	2.33E-08	2.86E-08	2.62E-08	2.76E-08	3.54E-08	3.35E-08	2.81E-08	2.57E-08	2.33E-08	3.25E-08	-	-	-	-	-	-
138	3.01E-08	2.91E-08	3.10E-08	3.39E-08	3.30E-08	3.30E-08	3.30E-08	2.28E-08	2.42E-08	3.35E-08	-	-	-	-	-	-
139	3.25E-08	2.81E-08	3.25E-08	3.25E-08	3.78E-08	3.83E-08	3.05E-08	3.05E-08	3.25E-08	3.49E-08	-	-	-	-	-	-
147	3.31E-08	-	-	2.18E-07	1.07E-07	3.12E-08	-	3.22E-08	3.65E-08	3.22E-08	-	-	-	-	-	-
148	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
155	4.36E-09	3.88E-09	4.85E-09	3.88E-09	5.33E-09	4.36E-09	2.42E-09	4.36E-09	2.91E-09	6.30E-09	-	-	-	-	-	-
156	5.82E-09	2.42E-09	4.85E-09	3.88E-09	6.79E-09	5.82E-09	2.91E-09	3.88E-09	4.85E-09	4.36E-09	-	-	-	-	-	-
157	4.39E-09	3.41E-09	2.92E-09	9.75E-09	6.82E-09	6.82E-09	5.85E-09	5.85E-09	4.39E-09	6.34E-09	-	-	-	-	-	-
158	7.80E-09	4.39E-09	3.41E-09	6.34E-09	7.31E-09	7.31E-09	1.02E-08	1.02E-08	5.85E-09	4.39E-09	-	-	-	-	-	-
159	-	-	-	2.92E-09	-	-	-	-	5.85E-09	-	-	-	-	-	-	-
163	-	-	-	-	-	-	3.90E-09	-	-	-	-	-	-	-	-	-
164	-	-	-	-	-	-	5.33E-09	-	-	-	-	-	-	-	-	-
166	-	-	-	-	-	-	7.27E-09	-	-	-	-	-	-	-	-	-
167	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-

13.4 **CONFIGURATION-TABLE**

Configuration		
Line #	Configuration step	Result
148	All	Failed Erase Operation
167	All	Verify 0 failed at row 6355

14 PIF-MARCH2011-RUNTABLES**14.1 RUN/BEAM/DUT/SEL-TABLES**

Line #	RUN						BEAM				DUT									
	Date	Run #	Start Time	PSI Run #	PSI Start time	Energy (MeV)	Fluence (p/cm ²)	Run Duration (s)	Mean Flux (p/(cm ² .s))	Run Dose (Rad)	SN	Total Dose (Rad)	TV Design	TV Design Version	Temperature (°C)	Vcore (V)	Vto (V)	Mode	Exposition Time (s)	SEL
40	05/03/2011	40	19:30	1	19:23	230	1.02E+10	46	2.22E+08	5.46E+02	20	5.46E+02	1.3	1	Room	1.5	3.3	Dyn	-	0
41	05/03/2011	41	19:34	2	19:30	200	2.01E+10	101	1.99E+08	1.17E+03	20	1.72E+03	1.3	1	Room	1.5	3.3	Dyn	-	0
42	05/03/2011	42	19:40	3	19:34	151	2.01E+10	156	1.29E+08	1.40E+03	20	3.12E+03	1.3	1	Room	1.5	3.3	Dyn	-	0
43	05/03/2011	43	19:45	4	19:39	101	2.00E+10	266	7.52E+07	1.85E+03	20	4.97E+03	1.3	1	Room	1.5	3.3	Dyn	-	0
44	05/03/2011	44	19:51	5	19:45	75.3	2.00E+10	387	5.18E+07	2.31E+03	20	7.29E+03	1.3	1	Room	1.5	3.3	Dyn	-	0
45	05/03/2011	45	20:14	6	20:07	50.9	2.00E+10	525	3.81E+07	3.12E+03	20	1.04E+04	1.3	1	Room	1.5	3.3	Dyn	-	0
46	05/03/2011	46	20:25	7	20:19	75.3	2.01E+10	388	5.17E+07	2.32E+03	20	1.27E+04	1.3	1	Room	1.5	3.3	Dyn	-	0
47	05/03/2011	47	20:35	8	20:28	23.5	2.82E+09	174	1.62E+07	8.04E+02	20	1.35E+04	1.3	1	Room	1.5	3.3	Dyn	-	0
48	05/03/2011	48	20:45	9	20:39	23.5	5.76E+09	355	1.62E+07	1.64E+03	20	1.52E+04	1.3	1	Room	1.5	3.3	Dyn	-	0
49	05/03/2011	49	20:57	10	20:51	23.5	4.85E+09	300	1.62E+07	1.38E+03	20	1.65E+04	1.3	1	Room	1.5	3.3	Dyn	-	0
51	05/03/2011	51	21:12	11	21:07	230	1.00E+10	45	2.23E+08	5.36E+02	19	0.00E+00	1.3	1	Room	1.5	3.3	Dyn	-	0
52	05/03/2011	52	21:16	12	21:09	101	1.00E+10	134	7.47E+07	9.27E+02	19	5.36E+02	1.3	1	Room	1.5	3.3	Dyn	-	0
55	05/03/2011	55	21:40	13	21:35	230	1.02E+10	45	2.26E+08	5.43E+02	19	2.01E+03	1.1	1	Room	1.5	3.3	Dyn	-	0
56	05/03/2011	56	21:45	14	21:38	230	1.00E+10	45	2.22E+08	5.34E+02	19	2.54E+03	1.1	1	Room	1.5	3.3	Dyn	-	0
58	05/03/2011	58	21:51	15	21:44	230	6.45E+10	288	2.24E+08	3.44E+03	19	5.98E+03	1.1	1	Room	1.5	3.3	Dyn	-	0
60	05/03/2011	60	22:05	16	21:58	230	1.75E+10	78	2.25E+08	9.36E+02	19	6.92E+03	1.1	1	Room	1.5	3.3	Dyn	-	0
61	05/03/2011	61	22:16	17	22:09	230	1.00E+11	447	2.24E+08	5.35E+03	19	1.23E+04	1.1	1	Room	1.5	3.3	Dyn	-	0
63	05/03/2011	63	22:26	18	22:19	230	2.68E+10	119	2.25E+08	1.43E+03	19	1.37E+04	1.1	1	Room	1.5	3.3	Dyn	-	0
65	05/03/2011	65	22:44	19	22:37	230	1.00E+11	450	2.22E+08	5.34E+03	19	1.90E+04	1.1	1	Room	1.5	3.3	Dyn	-	0
66	05/03/2011	66	22:54	20	22:47	230	3.76E+10	168	2.24E+08	2.01E+03	19	2.10E+04	1.1	1	Room	1.5	3.3	Dyn	-	0
68	05/03/2011	68	23:03	21	22:56	230	1.00E+11	444	2.26E+08	5.35E+03	19	2.64E+04	1.1	1	Room	1.5	3.3	Dyn	-	0
69	05/03/2011	69	23:12	22	23:05	230	1.50E+10	66	2.27E+08	7.98E+02	19	2.72E+04	1.1	1	Room	1.5	3.3	Dyn	-	0
71	05/03/2011	71	23:25	23	23:18	230	8.92E+09	39	2.29E+08	4.76E+02	19	2.77E+04	1.1	1	Room	1.5	3.3	Dyn	-	0
73	05/03/2011	73	23:31	24	23:24	230	4.21E+10	187	2.25E+08	2.25E+03	19	2.99E+04	1.1	1	Room	1.5	3.3	Dyn	-	0
76	06/03/2011	76	00:06	25	00:04	230	3.71E+10	166	2.24E+08	1.98E+03	21	1.98E+03	1.1	1	Room	1.5	3.3	Dyn	-	0
85	06/03/2011	85	00:36	26	00:29	230	1.95E+10	87	2.24E+08	1.04E+03	21	3.02E+03	1.2	1	Room	1.5	3.3	Dyn	-	0
86	06/03/2011	86	00:43	27	00:36	230	1.38E+10	62	2.22E+08	7.36E+02	21	3.76E+03	1.2	1	Room	1.5	3.3	Dyn	-	0
87	06/03/2011	87	00:45	28	00:38	230	8.86E+09	39	2.27E+08	4.73E+02	21	4.23E+03	1.2	1	Room	1.5	3.3	Dyn	-	0
88	06/03/2011	88	00:46	29	00:48	230	3.33E+09	15	2.22E+08	1.78E+02	21	4.41E+03	1.2	1	Room	1.5	3.3	Dyn	-	0

14.2 **SHIFTREGISTERCONDITIONSANDSEU-TABLES**

Line #	SR conditions					SR - Total SEU																
	F (MHz)	Channel Mask (Hex)	Reading ratio	Pattern	Valide	SR 1	SR 2	SR 3	SR 4	SR 5	SR 6	SR 7	SR 8	SR 9	SR 10	SR 11	SR 12	SR 13	SR 14	SR 15	SR 16	
40	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
41	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
42	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
43	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
44	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
45	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
46	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
47	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
48	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
49	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
51	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
52	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
55	2	3FF	4/4	A		1	0	0	1	1	0	0	0	1	1	0	0	0	0	0	0	0
56	50	3FF	4/4	A		0	0	1	0	1	1	1	1	0	0	0	0	0	0	0	0	0
58	100	FF	4/4	A		2	2	2	2	2	2	2	2	0	0	0	0	0	0	0	0	0
60	200	1	4/4	A		1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
61	200	1	4/4	A		2	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
63	150	35F	4/4	A		0	0	2	1	1	1	2	0	2	1	0	0	0	0	0	0	0
65	150	35F	4/4	A		2	1	2	2	2	0	2	0	2	2	0	0	0	0	0	0	0
66	50	3FF	4/4	A		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
68	50	3FF	4/4	A		2	2	2	2	2	2	2	2	2	2	0	0	0	0	0	0	0
69	2	3FF	4/4	A		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
71	2	3FF	4/4	A		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
73	2	3FF	4/4	A		0	1	0	1	0	0	1	1	0	1	0	0	0	0	0	0	0
76	100	3FF	4/4	A		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
85	190	3C00	4/4	A		0	0	0	0	0	0	0	0	0	0	0	1	0	1	0	0	0
86	190	3C00	4/4	A		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
87	190	3C00	4/4	A		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
88	190	3C00	4/4	A		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0

14.3 SHIFTREGISTERCROSS-SECTIONPERBIT-TABLES

Line#	SR - Cross-Section / Bit															
	SR 1	SR 2	SR 3	SR 4	SR 5	SR 6	SR 7	SR 8	SR 9	SR 10	SR 11	SR 12	SR 13	SR 14	SR 15	SR 16
40
41
42
43
44
45
46
47
48
49
51
52
55	9.57E-14	.	.	9.57E-14	9.57E-14	.	.	.	9.57E-14	9.57E-14
56	.	.	9.75E-14	.	9.75E-14	9.75E-14	9.75E-14	9.75E-14
58	3.02E-14	3.02E-14	3.02E-14	3.02E-14	3.02E-14	3.02E-14	3.02E-14	3.02E-14
60	5.56E-14
61	1.95E-14
63	.	.	7.27E-14	3.64E-14	3.64E-14	3.64E-14	7.27E-14	.	7.27E-14	3.64E-14
65	1.95E-14	9.74E-15	1.95E-14	1.95E-14	1.95E-14	.	1.95E-14	.	1.95E-14	1.95E-14
66
68	1.95E-14	1.95E-14	1.95E-14	1.95E-14	1.95E-14	1.95E-14	1.95E-14	1.95E-14	1.95E-14	1.95E-14
69
71
73	.	2.31E-14	.	2.31E-14	.	.	2.31E-14	2.31E-14	.	2.31E-14
76
85	4.98E-14	.	4.98E-14	.	.
86
87
88

14.4 **SRAM/UFROM-TABLES**

Line #	SRAM										UFROM											
	SRAM conditions					Fill Error Type				Check Error Type			Cross-Section/Bit (cm ²)	F (MHz)	SEU							
	F (MHz)	Start Address	Stop Address	Mask (Dec)	#Bit Effic	Pattern	Valide	4	3	2	1	4				3	2	1	SCU	MCU	SEU	
40	20	0	6FFF	511	516096	CKB /CKB	1	0	0	0	0	0	0	409	0	408	8	416	7.887E-14	10	0	
41	20	0	6FFF	511	516096	CKB /CKB	1	0	0	0	0	0	0	737	0	727	34	761	7.32141E-14	10	0	
42	20	0	6FFF	511	516096	CKB /CKB	1	0	0	0	0	0	0	603	0	602	2	604	5.82541E-14	10	0	
43	20	0	6FFF	511	516096	CKB /CKB	1	0	0	0	0	0	0	676	0	676	0	676	6.54917E-14	10	0	
44	20	0	6FFF	511	516096	CKB /CKB	0	0	0	0	0	0	0	0	0	0	0	0	0	0	10	0
45	20	0	6FFF	511	516096	CKB /CKB	1	0	0	0	0	0	0	844	0	844	0	844	8.1686E-14	10	0	
46	20	0	6FFF	511	516096	CKB /CKB	1	0	0	0	0	0	0	707	0	707	0	707	6.83242E-14	10	0	
47	20	0	6FFF	511	516096	CKB /CKB	1	0	0	0	0	0	0	41	0	41	0	41	2.81512E-14	10	0	
48	20	0	6FFF	511	516096	CKB /CKB	1	0	0	0	0	0	0	144	0	144	0	144	4.84743E-14	10	0	
49	20	0	6FFF	511	516096	CKB /CKB	1	0	0	0	0	0	0	138	0	138	0	138	5.5121E-14	10	0	
					516096			0	0	0	0	0	0	323	0	323	0	323	4.66046E-14			
51	20	0	6FFF	511	516096	CKB /CKB	1	0	0	0	0	0	0	389	0	389	0	389	7.51481E-14	10	0	
52	20	0	6FFF	511	516096	CKB /CKB	1	0	0	0	0	0	0	312	0	312	0	312	6.03935E-14	10	0	
55	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
56	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
58	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
60	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
61	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
63	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
65	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
66	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
68	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
69	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
71	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
73	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
76	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
85	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
86	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
87	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
88	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	

15 AcronymsandAbbreviations

CCC:	ClockConditioningCircuit
CMOS:	ComplementaryMetal-Oxide-Semiconductor
DDR:	DoubleDataRate
DDR2SDRAM:	DoubleDataRate(version2)SynchronousDynamic RandomAccessMemory
DUT:	DeviceUnderTest
EDAC:	ErrorDetectionAndCorrection
FF:	FlashFreeze
FPGA:	FieldProgrammableGateArray
FROM:	FlashReadOnlyMemory
HI:	HeavyIon
ISP:	InSystemProgramming
LVC MOS:	LowVoltageCMOS
LVDS:	LowVoltageDifferentialSignaling.
MBU:	Multi-BitUpset
MCU:	Multi-CellUpset
UFROM:	UserFROM
PLL:	Phase-lockedLoop
ROM:	ReadOnlyMemory
SBU:	SingleBitUpset
SCU:	SingleCellUpset
SDR:	SingleDataRate
SEB:	Single-EventBurnout
SEE:	Single-EventEffect
SEFI:	Single-EventFunctionalInterrupt
SEGR:	Single-EventGateRupture
SEL:	Single-EventLatch-up
SET:	Single-EventTransient
SEU:	Single-EventUpset
SPI:	SerialProgrammingInterface
SRAM:	StaticRandomAccessMemory
TMR:	TripleModuleRedundancy